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PSP 102.5

The PSP model is a joint development of Delft University of Technology and NXP Semiconductors

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Unclassified Report

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Abstract: The PSP model is a compact MOSFET model intended for analog, RF, and digital design. It is jointly developed by NXP Semiconductors and Delft University of Technology. (Until 2011, it was jointly developed by NXP Semiconductors and Arizona State University. The roots of PSP lie in both *MOS Model 11* (developed by NXP Semiconductors) and *SP* (developed at the Pennsylvania State University and later at Arizona State University). PSP is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, STI stress, etc.) to model present-day and upcoming deep-submicron bulk CMOS technologies. The source/drain junction model, c.q. the JUNCAP2 model, is fully integrated in PSP. This report contains a full description of the PSP model, including parameter sets, scaling rules, model equations, and a description of the parameter extraction procedure.
In December 2005, the Compact Model Council (CMC) has elected PSP as the new industrial standard model for compact MOSFET modeling.
Since December 2012, Delft University of Technology replaces Arizona State University as the supporting institution.

Conclusions:

History of model and documentation

History of the model

April 2005 Release of PSP 100.0 (which includes JUNCAP2 200.0) as part of SiMKit 2.1. A Verilog-A implementation of the PSP-model is made available as well. The PSP-NQS model is released as Verilog-A code only.

August 2005 Release of PSP 100.1 (which includes JUNCAP2 200.1) as part of SiMKit 2.2. Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only. Focus of this release was mainly on the optimization of the evaluation speed of PSP. Moreover, the PSP implementation has been extended with operating point output (SiMKit-version only).

March 2006 Release of PSP 101.0 (which includes JUNCAP2 200.1) as part of SiMKit 2.3. PSP 101.0 is *not* backward compatible with PSP 100.1. Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only. Focus of this release was on the implementation of requirements for CMC standardization, especially those which could not preserve backward compatibility.

June 2006 Release of PSP 102.0 (which includes JUNCAP2 200.1) as part of SiMKit 2.3.2. PSP 102.0 is backward compatible with PSP 101.0 in all practical cases, provided a simple transformation to the parameter set is applied (see description below). Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only.

Global parameter sets for PSP 101.0 can be transformed to PSP 102.0 by replacing **DPHIBL** (in 102.0 parameter set) by **DPHIBO** · **DPHIBL** (from 101.0 parameter set). After this transformation, the simulation results of PSP 102.0 are identical to those of PSP 101.0 in all practical situations.

October 2006 Release of PSP 102.1 (which includes JUNCAP2 200.2) as part of SiMKit 2.4. PSP 102.1 is backward compatible with PSP 102.0. SiMKit 2.4 includes a preliminary implementation of the PSP-NQS model. Similar to the previous version, a Verilog-A implementation of the PSP-model is available as well.

October 2007 Release of PSP 102.2 (which includes JUNCAP2 200.3). PSP 102.2 is backward compatible with PSP 102.1.

April 2008 Release of PSP 102.3 (which includes JUNCAP2 200.3) as part of SiMKit 3.1. PSP 102.3 is backward compatible with PSP 102.2. The main changes are:

- Added asymmetric junction model for the drain-bulk junction. The new junction parameters have a suffix "D" added to their names. When **SWJUNASYM** $= 1$ the original parameters are used for the source-bulk junction and the new parameters are used for drain-bulk junction. When **SWJUNASYM** $= 0$ the original junction parameters are used for both source-bulk and drain-bulk junctions as in symmetric case, and the new junction parameters are neglected.
- Added asymmetric models for the overlap region of the drain side. These include
  - Added related model parameters **TOXOVDO**, **LOVD** and **NOVDO** to global, **TOXOVD** and **NOVD** to local and **POTOXOVD**, **PONOVD**, **PLNOVD**, **PWNOVD** and **PLWNOVD** to binning models.
  - Asymmetric GIDL/GISL model. Added related parameters **AGIDLDW**, **BGIDLDO**, **STBGIDLDO** and **CGIDLDO** to global, **AGIDLD**, **BGIDLD**, **STBGIDLD** and **CGIDLD** to local and **POAGIDLD**, **PLAGIDLD**, **PWAGIDLD**, **PLWAGIDLD**, **POBGIDLD**, **POSTBGIDLD** and **POCGIDLD** to binning models.

- Asymmetric overlap gate current model. Added related parameters **IGOVDW** to global, **IGOVD** to local and **POIGOVD**, **PLIGOVD**, **PWIGOVD** and **PLWIGOVD** to binning models.
- Asymmetric overlap capacitance model. Added related parameters **CGOVD** to local, **POCGOVD**, **PLCGOVD**, **PWCGOVD** and **PLWCGOVD** to binning models.
- Asymmetric outer fringe capacitance model. Added related parameters **CFRDW** to global, **CFRD** to local and **POCFRD**, **PLCFRD**, **PWCFRD** and **PLWCFRD** to binning models.

When **SWJUNASYM** $= 1$ the original parameters for the models listed above are used for the source side and the newly added parameters are used for the drain side. When **SWJUNASYM** $= 0$ the original parameters are used for both source and drain sides and the new parameters are ignored.

- Added **EF**(local), **EFO**(global) and **POEF**(binning) as flicker noise frequency exponent parameters.
- Added noise parameters **LINTNOI** and **ALPNOI** to global model to increase the flexibility of the length scaling of the flicker noise.
- Some minor bug-fixes and implementation changes.

December 2012 Release of PSP 102.4 as part of SiMKit 4.0.1. PSP 102.4 is backward compatible with the previous version, PSP 102.3. The main changes are:

- Several improvements in the noise-model implementation
  - Fixed sign of correlation coefficient (Verilog-A only).
  - Simplified implementation and better scaled noise amplitude at internal nodes (Verilog-A only).
  - Improved behavior when crossing $V_{\rm ds} = 0$ at high-frequency.
- Scaled local parameters were added to OP-output.
- Some minor implementation changes.
- New parameter **PARAMCHK** to set level of clip warnings (SiMKit only).
- More efficient model evaluation when **MULT** $= 0$ (SiMKit only).

December 2013 Release of PSP 102.5.0 (which includes JUNCAP 200.4) as part of SiMKit 4.2. The main changes are:

- Addition of excess noise, which is important for sub-100-nm channel lengths. This addition is backwards compatible with PSP 102.4. New parameters: **FNTEXC** (local model), **FNTEXCL** (global model), and **POFNTEXC**, **PLFNTEXC**, **PWFNTEXC**, **PLWFNTEXC** (binning model).
- Minor bugfixes.

History of the documentation

April 2005 First release of PSP (PSP 100.0) documentation.

August 2005 Documentation updated for PSP 100.1, errors corrected and new items added.

March 2006 Documentation adapted to PSP 101.0. Added more details on noise-model implementation and a full description of the NQS-model.

June 2006 Documentation adapted to PSP 102.0 and some errors corrected.

October 2006 Documentation adapted to PSP 102.1 and some errors corrected.

October 2007 Documentation adapted to PSP 102.2 and some errors corrected.

April 2008 Documentation adapted to PSP 102.3 and some errors corrected.

January 2011 Description of SiMKit noise implementation (Section 6.5) aligned with recent modifications.

April 2013 Documentation adapted to PSP 102.4.

December 2013 Documentation adapted to PSP 102.5 and some errors corrected.

Contents

Section 1

Introduction

1.1 Origin and purpose

The PSP model is a compact MOSFET model intended for analog, RF, and digital design. It is jointly developed by NXP Semiconductors and Delft University of Technology. (Until 2011, it was jointly developed by NXP Semiconductors and Arizona State University. The roots of PSP lie in both *MOS Model 11* (developed by NXP Semiconductors) and *SP* (developed at the Pennsylvania State University and later at Arizona State University). PSP is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, STI stress, etc.) to model present-day and upcoming deep-submicron bulk CMOS technologies. The source/drain junction model, c.q. the JUNCAP2 model, is fully integrated in PSP.

PSP not only gives an accurate description of currents, charges, and their first order derivatives (i.e. transconductance, conductance and capacitances), but also of the higher order derivatives, resulting in an accurate description of electrical distortion behavior. The latter is especially important for analog and RF circuit design. The model furthermore gives an accurate description of the noise behavior of MOSFETs. Finally, PSP has an option for simulation of non-quasi-static (NQS) effects.

The source code of PSP and the most recent version of this documentation are available on the PSP model web site: `psp.ewi.tudelft.nl` and the NXP Semiconductors web site: `www.nxp.com/models`.

1.2 Structure of PSP

The PSP model has a hierarchical structure, similar to that of MOS Model 11 and SP. This means that there is a strict separation of the geometry scaling in the global model and the model equations in the local model.

As a consequence, PSP can be used at either one of two levels.

- **Global level** One uses a global parameter set, which describes a whole geometry range. Combined with instance parameters (such as L and W), a local parameter set is internally generated and further processed at the local level in exactly the same way as a custom-made local parameter set.

- **Local level** One uses a custom-made local parameter set to simulate a transistor with a specific geometry. Temperature scaling is included at this level.

The set of parameters which occur in the equations for the various electrical quantities is called the *local* parameter set. In PSP, temperature scaling parameters are included in the local parameter set. An overview of the local parameters in PSP is given in Section 2.5.7. Each of these parameters can be determined by purely electrical measurements. As a consequence, a local parameter set gives a complete description of the electrical properties of a device of *one* particular geometry.

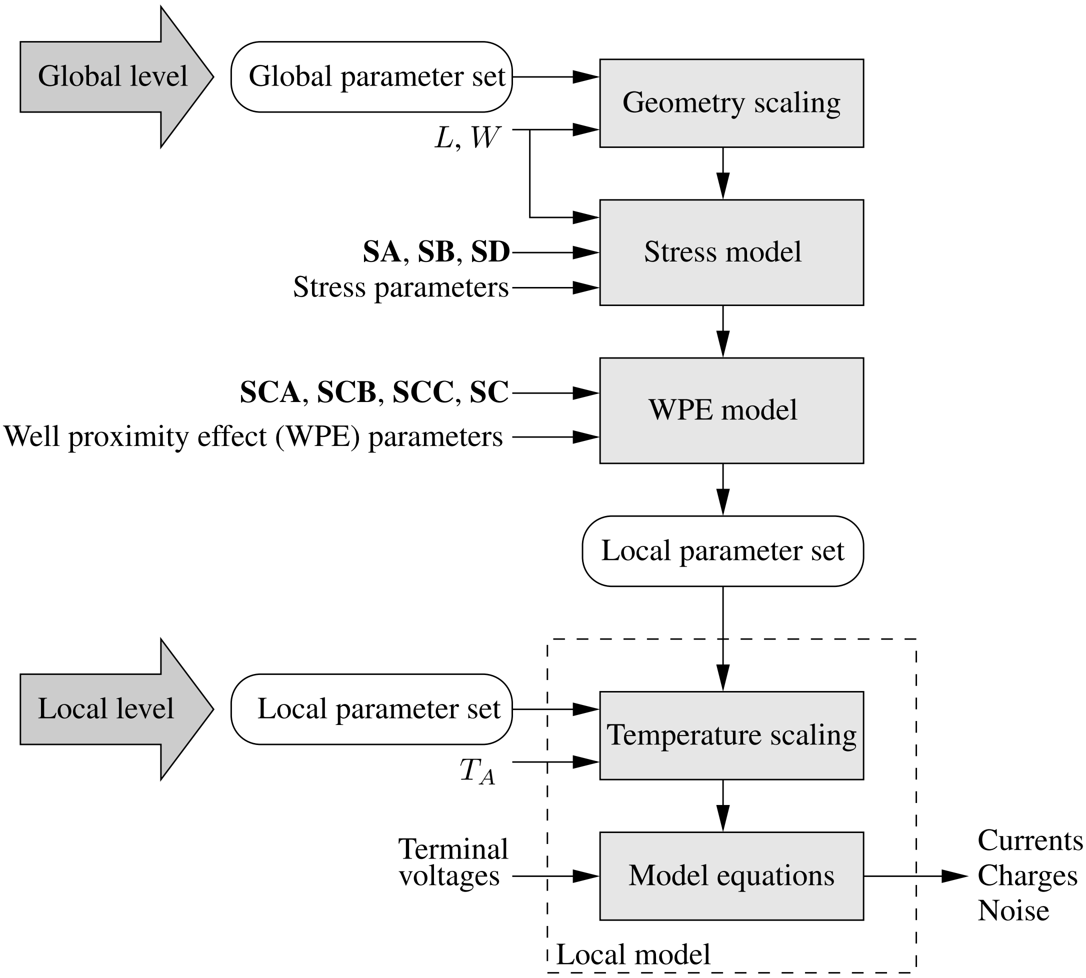

Figure 1.1: Simplified schematic overview of PSP's hierarchical structure.

Since most of these (local) parameters scale with geometry, all transistors of a particular process can be described by a (larger) set of parameters, called the *global* parameter set. An overview of the global parameters in PSP is given in Section 2.5.3. Roughly speaking, this set contains all local parameters for a long/wide device plus a number of sensitivity coefficients. From the global parameter set, one can obtain a local parameter set for a specific device by applying a set of scaling rules (see Section 3.2). The geometric properties of that specific device (such as its length and width) enter these scaling rules as *instance parameters*.

From PSP 101.0 onwards it is possible to use a set of binning rules (see Section 3.3) as an alternative to the geometrical (physics based) scaling rules. These binning rules come with their own set of parameters (see Section 2.5.4). Similar to the geometrical scaling rules, the binning rules yield a local parameter set which is used as input for the local model.

PSP is preferably used at global level when designing a circuit in a specific technology for which a global parameter set is available. On the other hand, using PSP at local level can be advantageous during parameter extraction.

As an option, it is possible to deal with the modifications of transistor properties due to stress and well proximity effect (WPE). In PSP, this is implemented by additional sets of transformation rules, which are optionally applied to the intermediate local parameter set generated at the global level. The parameters associated with the stress and WPE models are consequently part of the global parameter set (both geometrical and binning).

The model structure described above is schematically depicted in Fig. 1.1.

The JUNCAP2 model is implemented in such a way that the same set of JUNCAP2 parameters can be used at both the global and the local level. This is further explained in Section 6.4.

1.3 Availability

The PSP model developers (Delft University of Technology and NXP Semiconductors) distribute the PSP code in two formats:

1. Verilog-A code
2. C-code (as part of SiMKit-library)

The C-version is automatically generated from the Verilog-A version by the software package ADMS [1]. This procedure guarantees the two implementations to contain identical equations. Nevertheless—due to some specific limitations/capabilities of the two formats—there are a few minor differences, which are described in Section 6.5.

1.3.1 SiMKit

SiMKit is a simulator-independent compact transistor model library. Simulator-specific connections are handled through so-called adapters that provide the correct interfacing to the circuit simulator of choice. Currently, adapters to the following circuit simulators are provided:

1. Spectre (Cadence)
2. Pstar (NXP Semiconductors)
3. ADS (Agilent)

Some other circuit simulators vendors provide their own SiMKit adapter, such that simulations with models in SiMKit are possible.

Section 2

Constants and Parameters

2.1 Nomenclature

The nomenclature of the quantities listed in the following sections has been chosen to express their purpose and their relation to other quantities and to preclude ambiguity and inconsistency. Throughout this document, all PSP parameter names are printed in boldface capitals. Parameters which refer to the long transistor limit and/or the reference temperature have a name containing an '**O**', while the names of scaling parameters end with the letter '**L**' and/or '**W**' for length or width scaling, respectively. Parameters for temperature scaling start with '**ST**', followed by the name of the parameter to which the temperature scaling applies. Parameters used for the binning model start with '**PO**', '**PL**', '**PW**', or '**PLW**', followed by the name of the local parameter they refer to.

2.2 Parameter clipping

For most parameters, a maximum and/or minimum value is given in the tables below. In PSP, all parameters are limited (clipped) to this pre-specified range in order to prevent difficulties in the numerical evaluation of the model, such as division by zero.

N.B. After computation of the scaling rules (either physical or binning), stress and well proximity effect equations, the resulting local parameters are subjected to the clipping values as given in Section 2.5.7.

2.3 Circuit simulator variables

External electrical variables

The definitions of the external electrical variables are illustrated in Fig. 2.1. The relationship between these external variables and the internal variables used in Chapter 4 is given in Fig. 6.1.

Symbol	Unit	Description
V_{D}^{e}	V	Potential applied to drain node
V_{G}^{e}	V	Potential applied to gate node
V_{S}^{e}	V	Potential applied to source node
V_{B}^{e}	V	Potential applied to bulk node
I_{D}^{e}	A	DC current into drain node

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Symbol	Unit	Description
I^e_{G}	A	DC current into gate node
I^e_{S}	A	DC current into source node
I^e_{B}	A	DC current into bulk node
S^e_{fl}	A^{2}s	Spectral density of flicker noise current in the channel
S^e_{id}	A^{2}s	Spectral density of thermal noise current in the channel
$S^e_{\mathrm{ig,S}}$	A^{2}s	Spectral density of induced gate noise at source side
$S^e_{\mathrm{ig,D}}$	A^{2}s	Spectral density of induced gate noise at drain side
S^e_{igs}	A^{2}s	Spectral density of gate current shot noise at source side
S^e_{igd}	A^{2}s	Spectral density of gate current shot noise at drain side
$S^e_{\mathrm{j,S}}$	A^{2}s	Spectral density of source junction shot noise
$S^e_{\mathrm{j,D}}$	A^{2}s	Spectral density of drain junction shot noise
S^e_{igid}	A^{2}s	Cross spectral density between S^e_{id} and (S^e_{igS} or S^e_{igD})

Other circuit simulator variables

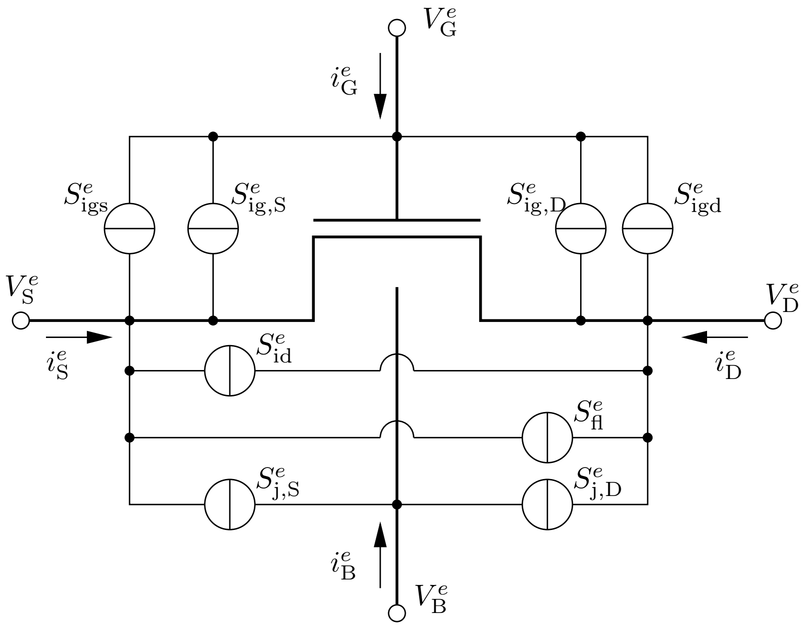
Next to the electrical variables described above, the quantities in the table below are also provided to the model by the circuit simulator.

Symbol	Unit	Description
T_{A}	°C	Ambient circuit temperature
f_{op}	Hz	Operation frequency

2.4 Model constants

In the following table the symbolic representation, the value and the description of the various physical constants used in the PSP model are given.

No.	Symbol	Unit	Value	Description
1	T_0	K	273.15	Offset between Celsius and Kelvin temperature scale
2	k_{B}	J/K	$1.3806505 \cdot 10^{-23}$	Boltzmann constant
3	$\hbar$	J s	$1.05457168 \cdot 10^{-34}$	Reduced Planck constant
4	q	C	$1.6021918 \cdot 10^{-19}$	Elementary unit charge
5	m_0	kg	$9.1093826 \cdot 10^{-31}$	Electron rest mass
6	ϵ_0	F/m	$8.85418782 \cdot 10^{-12}$	Permittivity of free space
7	$\epsilon_{\mathrm{r,Si}}$	–	11.8	Relative permittivity of silicon
8	QM_{N}	V m$^{\frac{4}{3}}$C$^{-\frac{2}{3}}$	5.951993	Constant of quantum-mechanical behavior of electrons
9	QM_{P}	V m$^{\frac{4}{3}}$C$^{-\frac{2}{3}}$	7.448711	Constant of quantum-mechanical behavior of holes



$$i_D^e = I_D^e + \frac{\mathrm{d}Q_D^e}{\mathrm{d}t}$$

$$i_G^e = I_G^e + \frac{\mathrm{d}Q_G^e}{\mathrm{d}t}$$

$$i_S^e = I_S^e + \frac{\mathrm{d}Q_S^e}{\mathrm{d}t}$$

$$i_B^e = I_B^e + \frac{\mathrm{d}Q_B^e}{\mathrm{d}t}$$

Figure 2.1: Definition of external electrical quantities.

2.5 Model parameters

In this section all parameters of the PSP-model are described. The parameters for the intrinsic MOS model, the stress and well proximity effect models and the junction model are given in separate tables. The complete parameter list for each of the model entry levels is composed of several parts, as indicated in the table below.

Entry level	**Sections**
Global (geometrical scaling)	2.5.1 (instance parameters)
	2.5.3 (intrinsic MOS)
	2.5.5 (stress)
	2.5.6 (well proximity effect)
	2.5.8 (junctions)
	2.5.9 (parasitic resistances)
Binning	2.5.1 (instance parameters)
	2.5.4 (intrinsic MOS)
	2.5.5 (stress)
	2.5.6 (well proximity effect)
	2.5.8 (junctions)
	2.5.9 (parasitic resistances)
Local	2.5.2 (instance parameters)
	2.5.7 (intrinsic MOS)
	2.5.8 (junctions)
	2.5.9 (parasitic resistances)

2.5.1 Instance parameters for global and binning model

No.	Name	Unit	Default	Min.	Max.	Description
0	L	m	10^{-6}	10^{-9}	–	Drawn channel length
1	W	m	10^{-6}	10^{-9}	–	Drawn channel width (total width)
2	**ABSOURCE**	m^2	10^{-12}	0	–	Source junction area
3	**LSSOURCE**	m	10^{-6}	0	–	STI-edge part of source junction perimeter
4	**LGSOURCE**	m	10^{-6}	0	–	Gate-edge part of source junction perimeter
5	**ABDRAIN**	m^2	10^{-12}	0	–	Drain junction area
6	**LSDRAIN**	m	10^{-6}	0	–	STI-edge part of drain junction perimeter
7	**LGDRAIN**	m	10^{-6}	0	–	Gate-edge part of drain junction perimeter
8	**AS**	m^2	10^{-12}	0	–	Source junction area (alternative spec.)
9	**PS**	m	10^{-6}	0	–	Source STI-edge perimeter (alternative spec.)
10	**AD**	m^2	10^{-12}	0	–	Drain junction area (alternative spec.)
11	**PD**	m	10^{-6}	0	–	Drain STI-edge perimeter (alternative spec.)
12	**DELVTO**	V	0	–	–	Threshold voltage shift parameter
13	**FACTUO**	–	1	0	–	Zero-field mobility pre-factor
14	**SA**	m	0	–	–	Distance between OD-edge and poly at source side
15	**SB**	m	0	–	–	Distance between OD-edge and poly at drain side
16	**SD**	m	0	–	–	Distance between neighboring fingers
17	**SCA**	–	0	0	–	Integral of the first distribution function for scattered well dopant
18	**SCB**	–	0	0	–	Integral of the second distribution function for scattered well dopant
19	**SCC**	–	0	0	–	Integral of the third distribution function for scattered well dopant
20	**SC**	m	0	–	–	Distance between OD edge and nearest well edge
21	**NGCON**	–	1	1	2	Number of gate contacts
22	**XGW**	m	10^{-7}	–	–	Distance from the gate contact to the channel edge
23	**NF**	–	1	1	–	Number of fingers; internally rounded to the nearest integer
24	**MULT**	–	1	0	–	Number of devices in parallel

Note that if both **SA** and **SB** are set to 0 the stress-equations are not computed. If **SCA**, **SCB**, **SCC** and **SC** are all set to 0 the well proximity effect equations are not computed.

The switching parameter **SWJUNCAP** is used to determine the meaning and usage of the junction instance parameters, where **AB** (junction area), **LS** (STI-edge part of junction perimeter), and **LG** (gate-edge part of junction perimeter) are the instance parameters of a single instance (source or drain) of the JUNCAP2 model.

	source			drain		
SWJUNCAP	**AB**	**LS**	**LG**	**AB**	**LS**	**LG**
0	0	0	0	0	0	0
1	**ABSOURCE**	**LSSOURCE**	**LGSOURCE**	**ABDRAIN**	**LSDRAIN**	**LGDRAIN**
2	**AS**	**PS**	W_{E}	**AD**	**PD**	W_{E}
3	**AS**	**PS** $- W_{\mathrm{E}}$	W_{E}	**AD**	**PD** $- W_{\mathrm{E}}$	W_{E}

2.5.2 Instance parameters for local model

As explained in Section 6.4, the instance parameters for the JUNCAP2 model are used at the local level as well.

No.	Name	Unit	Default	Min.	Max.	Description
0	**ABSOURCE**	m^2	$1 \cdot 10^{-12}$	0	–	Source junction area
1	**LSSOURCE**	m	$1 \cdot 10^{-6}$	0	–	STI-edge part of source junction perimeter
2	**LGSOURCE**	m	$1 \cdot 10^{-6}$	0	–	Gate-edge part of source junction perimeter
3	**ABDRAIN**	m^2	$1 \cdot 10^{-12}$	0	–	Drain junction area
4	**LSDRAIN**	m	$1 \cdot 10^{-6}$	0	–	STI-edge part of drain junction perimeter
5	**LGDRAIN**	m	$1 \cdot 10^{-6}$	0	–	Gate-edge part of drain junction perimeter
6	**AS**	m^2	$1 \cdot 10^{-12}$	0	–	Source junction area (alternative spec.)
7	**PS**	m	$1 \cdot 10^{-6}$	0	–	Source STI-edge perimeter (alternative spec.)
8	**AD**	m^2	$1 \cdot 10^{-12}$	0	–	Drain junction area (alternative spec.)
9	**PD**	m	$1 \cdot 10^{-6}$	0	–	Drain STI-edge perimeter (alternative spec.)
10	**JW**	m	$1 \cdot 10^{-6}$	0	–	Junction width
11	**DELVTO**	V	0	–	–	Threshold voltage shift parameter
12	**FACTUO**	–	1	0	–	Zero-field mobility pre-factor
13	**MULT**	–	1	0	–	Number of devices in parallel

Also at the local level, the switching parameter **SWJUNCAP** is used to determine the meaning and usage of the junction instance parameters, where **AB** (junction area), **LS** (STI-edge part of junction perimeter), and **LG** (gate-edge part of junction perimeter) are the instance parameters of a single instance (source or drain) of the JUNCAP2 model. Because the transistor width W is not available at the local level, an additional instance parameter **JW** (junction width) is required when **SWJUNCAP** $= 2$ or 3.

	source			drain		
SWJUNCAP	**AB**	**LS**	**LG**	**AB**	**LS**	**LG**
0	0	0	0	0	0	0
1	**ABSOURCE**	**LSSOURCE**	**LGSOURCE**	**ABDRAIN**	**LSDRAIN**	**LGDRAIN**
2	**AS**	**PS**	**JW**	**AD**	**PD**	**JW**
3	**AS**	**PS** – **JW**	**JW**	**AD**	**PD** – **JW**	**JW**

2.5.3 Parameters for global model (physical geometrical scaling rules)

The physical geometry scaling rules of PSP (see Section 3.2) have been developed to give a good description over the whole geometry range of CMOS technologies.

No.	Name	Unit	Default	Min.	Max.	Description
0	**LEVEL**	–	1020	–	–	Model selection parameter; see Sec. 6.1
1	**TYPE**	–	1	−1	1	Channel type parameter; 1 ↔ NMOS, −1 ↔ PMOS[1]
2	**TR**	°C	21	−273	–	Reference temperature
			Switch Parameters			
3	**PARAMCHK**	–	0	–	–	Level of clip-warning info[2]
4	**SWIGATE**	–	0	0	1	Flag for gate current (0 ↔ “off”)
5	**SWIMPACT**	–	0	0	1	Flag for impact ionization current (0 ↔ “off”)
6	**SWGIDL**	–	0	0	1	Flag for GIDL/GISL current (0 ↔ “off”)
7	**SWJUNCAP**	–	0	0	3	Flag for JUNCAP (0 ↔ “off”); see Sec. 2.5.1
8	**SWJUNASYM**	–	0	–	–	Flag for asymmetric junctions (0 ↔ “off”)[3]
9	**QMC**	–	1	0	–	Quantum-mechanical correction factor
			Process Parameters			
10	**LVARO**	m	0	–	–	Geometry independent difference between actual and programmed poly-silicon gate length
11	**LVARL**	–	0	–	–	Length dependence of ΔL_{PS}
12	**LVARW**	–	0	–	–	Width dependence of ΔL_{PS}
13	**LAP**	m	0	–	–	Effective channel length reduction per side due to lateral diffusion of source/drain dopant ions
14	**WVARO**	m	0	–	–	Geometry independent difference between actual and programmed field-oxide opening
15	**WVARL**	–	0	–	–	Length dependence of ΔW_{OD}
16	**WVARW**	–	0	–	–	Width dependence of ΔW_{OD}
17	**WOT**	m	0	–	–	Effective reduction of channel width per side due to lateral diffusion of channel-stop dopant ions
18	**DLQ**	m	0	–	–	Effective channel length offset for CV
19	**DWQ**	m	0	–	–	Effective channel width offset for CV
20	**VFBO**	V	−1	–	–	Geometry-independent flat-band voltage at **TR**
21	**VFBL**	–	0	–	–	Length dependence **VFB**
22	**VFBW**	–	0	–	–	Width dependence of **VFB**
23	**VFBLW**	–	0	–	–	Area dependence of **VFB**

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[1] See Section 6.3.1 for more information on usage of **TYPE** in various simulators.
[2] Only in SiMKit-version of PSP. See Section 6.5.4 for more information.
[3] See Section 3.7 for more information on usage of **SWJUNASYM**.

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No.	Name	Unit	Default	Min.	Max.	Description
24	**STVFBO**	V/K	$5 \cdot 10^{-4}$	–	–	Geometry-independent temperature dependence of **VFB**
25	**STVFBL**	–	0	–	–	Length dependence of **STVFB**
26	**STVFBW**	–	0	–	–	Width dependence of **STVFB**
27	**STVFBLW**	–	0	–	–	Area dependence of **STVFB**
28	**TOXO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Gate oxide thickness
29	**EPSROXO**	–	3.9	1	–	Relative permittivity of gate dielectric
30	**NSUBO**	m^{-3}	$3 \cdot 10^{23}$	10^{20}	–	Geometry independent substrate doping
31	**NSUBW**	–	0	–	–	Width dependence of substrate doping due to segregation
32	**WSEG**	m	10^{-8}	10^{-10}	–	Characteristic length for segregation of substrate doping
33	**NPCK**	m^{-3}	10^{24}	0	–	Pocket doping level
34	**NPCKW**	–	0	–	–	Width dependence of **NPCK** due to segregation
35	**WSEGP**	m	10^{-8}	10^{-10}	–	Characteristic length for segregation of pocket doping
36	**LPCK**	m	10^{-8}	10^{-10}	–	Characteristic length for lateral doping profile
37	**LPCKW**	–	0	–	–	Width dependence of **LPCK** due to segregation
38	**FOL1**	–	0	–	–	First order length dependence of short channel body-effect
39	**FOL2**	–	0	–	–	Second order length dependence of short channel body-effect
40	**VNSUBO**	V	0	–	–	Effective doping bias-dependence parameter
41	**NSLPO**	V	0.05	–	–	Effective doping bias-dependence parameter
42	**DNSUBO**	V^{-1}	0	–	–	Effective doping bias-dependence parameter
43	**DPHIBO**	V	0	–	–	Geometry independent offset of φ_B
44	**DPHIBL**	V	0	–	–	Length dependence of **DPHIB**
45	**DPHIBLEXP**	–	1	–	–	Exponent for length dependence of **DPHIB**
46	**DPHIBW**	–	0	–	–	Width dependence of **DPHIB**
47	**DPHIBLW**	–	0	–	–	Area dependence of **DPHIB**
48	**NPO**	m^{-3}	10^{26}	–	–	Geometry-independent gate poly-silicon doping
49	**NPL**	–	0	–	–	Length dependence of **NP**
50	**CTO**	–	0	–	–	Geometry-independent part of interface states factor **CT**
51	**CTL**	–	0	–	–	Length dependence of **CT**

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No.	Name	Unit	Default	Min.	Max.	Description
52	**CTLEXP**	–	1	–	–	Exponent describing length dependence of **CT**
53	**CTW**	–	0	–	–	Width dependence of **CT**
54	**CTLW**	–	0	–	–	Area dependence of **CT**
55	**TOXOVO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness
56	**TOXOVDO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness for drain side
57	**LOV**	m	0	0	–	Overlap length for overlap capacitance
58	**LOVD**	m	0	0	–	Overlap length for gate/drain overlap capacitance
59	**NOVO**	m^{-3}	$5 \cdot 10^{25}$	–	–	Effective doping of overlap region
60	**NOVDO**	m^{-3}	$5 \cdot 10^{25}$	–	–	Effective doping of overlap region for drain side
			DIBL-Parameters			
61	**CFL**	V^{-1}	0	–	–	Length dependence of DIBL-parameter
62	**CFLEXP**	–	2	–	–	Exponent for length dependence of **CF**
63	**CFW**	–	0	–	–	Width dependence of **CF**
64	**CFBO**	V^{-1}	0	–	–	Back-bias dependence of **CF**
			Mobility Parameters			
65	**UO**	m^2/V/s	$5 \cdot 10^{-2}$	–	–	Zero-field mobility at **TR**
66	**FBET1**	–	0	–	–	Relative mobility decrease due to first lateral profile
67	**FBET1W**	–	0	–	–	Width dependence of **FBET1**
68	**LP1**	m	10^{-8}	10^{-10}	–	Mobility-related characteristic length of first lateral profile
69	**LP1W**	–	0	–	–	Width dependence of **LP1**
70	**FBET2**	–	0	–	–	Relative mobility decrease due to second lateral profile
71	**LP2**	m	10^{-8}	10^{-10}	–	Mobility-related characteristic length of second lateral profile
72	**BETW1**	–	0	–	–	First higher-order width scaling coefficient of **BETN**
73	**BETW2**	–	0	–	–	Second higher-order width scaling coefficient of **BETN**
74	**WBET**	m	10^{-9}	10^{-10}	–	Characteristic width for width scaling of **BETN**
75	**STBETO**	–	1	–	–	Geometry independent temperature dependence of **BETN**
76	**STBETL**	–	0	–	–	Length dependence of **STBET**
77	**STBETW**	–	0	–	–	Width dependence of **STBET**
78	**STBETLW**	–	0	–	–	Area dependence of **STBET**
79	**MUEO**	m/V	0.5	–	–	Geometry independent mobility reduction coefficient at **TR**

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No.	Name	Unit	Default	Min.	Max.	Description
80	**MUEW**	–	0	–	–	Width dependence of **MUE**
81	**STMUEO**	–	0	–	–	Temperature dependence of **MUE**
82	**THEMUO**	–	1.5	0	–	Mobility reduction exponent at **TR**
83	**STTHEMUO**	–	1.5	–	–	Temperature dependence of **THEMU**
84	**CSO**	–	0	–	–	Geometry independent Coulomb scattering parameter at **TR**
85	**CSL**	–	0	–	–	Length dependence of **CS**
86	**CSLEXP**	–	0	–	–	Exponent for length dependence of **CS**
87	**CSW**	–	0	–	–	Width dependence of **CS**
88	**CSLW**	–	0	–	–	Area dependence of **CS**
89	**STCSO**	–	0	–	–	Temperature dependence of **CS**
90	**XCORO**	V^{-1}	0	–	–	Geometry independent non-universality parameter
91	**XCORL**	–	0	–	–	Length dependence of **XCOR**
92	**XCORW**	–	0	–	–	Width dependence of **XCOR**
93	**XCORLW**	–	0	–	–	Area dependence of **XCOR**
94	**STXCORO**	–	0	–	–	Temperature dependence of **XCOR**
95	**FETAO**	–	1	–	–	Effective field parameter
			Series Resistance Parameters			
96	**RSW1**	Ω	2500	–	–	Source/drain series resistance for channel width W_{EN} at **TR**
97	**RSW2**	–	0	–	–	Higher-order width scaling of source/drain series resistance
98	**STRSO**	–	1	–	–	Temperature dependence of **RS**
99	**RSBO**	V^{-1}	0	–	–	Back-bias dependence of **RS**
100	**RSGO**	V^{-1}	0	–	–	Gate-bias dependence of **RS**
			Velocity Saturation Parameters			
101	**THESATO**	V^{-1}	0	–	–	Geometry independent velocity saturation parameter at **TR**
102	**THESATL**	V^{-1}	0.05	–	–	Length dependence of **THESAT**
103	**THESATLEXP**	–	1	–	–	Exponent for length dependence of **THESAT**
104	**THESATW**	–	0	–	–	Width dependence of **THESAT**
105	**THESATLW**	–	0	–	–	Area dependence **THESAT**
106	**STTHESATO**	–	1	–	–	Geometry independent temperature dependence of **THESAT**
107	**STTHESATL**	–	0	–	–	Length dependence of **STTHESAT**
108	**STTHESATW**	–	0	–	–	Width dependence of **STTHESAT**
109	**STTHESATLW**	–	0	–	–	Area dependence of **STTHESAT**

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No.	Name	Unit	Default	Min.	Max.	Description
110	**THESATBO**	V^{-1}	0	–	–	Back-bias dependence of **THESAT**
111	**THESATGO**	V^{-1}	0	–	–	Gate-bias dependence of **THESAT**
			Saturation Voltage Parameters			
112	**AXO**	–	18	–	–	Geometry independent linear/saturation transition factor
113	**AXL**	–	0.4	0	–	Length dependence of **AX**
			Channel Length Modulation (CLM) Parameters			
114	**ALPL**	–	$5 \cdot 10^{-4}$	–	–	Length dependence of CLM pre-factor **ALP**
115	**ALPLEXP**	–	1	–	–	Exponent for length dependence of **ALP**
116	**ALPW**	–	0	–	–	Width dependence of **ALP**
117	**ALP1L1**	V	0	–	–	Length dependence of CLM enhancement factor above threshold
118	**ALP1LEXP**	–	0.5	–	–	Exponent describing the length dependence of **ALP1**
119	**ALP1L2**	–	0	0	–	Second order length dependence of **ALP1**
120	**ALP1W**	–	0	–	–	Width dependence of **ALP1**
121	**ALP2L1**	V	0	–	–	Length dependence of CLM enhancement factor below threshold
122	**ALP2LEXP**	–	0.5	–	–	Exponent describing the length dependence **ALP2**
123	**ALP2L2**	–	0	0	–	Second order length dependence of **ALP2**
124	**ALP2W**	–	0	–	–	Width dependence of **ALP2**
125	**VPO**	V	0.05	–	–	CLM logarithmic dependence parameter
			Impact Ionization (II) Parameters			
126	**A1O**	–	1	–	–	Geometry independent part of impact-ionization pre-factor **A1**
127	**A1L**	–	0	–	–	Length dependence of **A1**
128	**A1W**	–	0	–	–	Width dependence of **A1**
129	**A2O**	V	10	–	–	Impact-ionization exponent at **TR**
130	**STA2O**	V	0	–	–	Temperature dependence of **A2**
131	**A3O**	–	1.0	–	–	Geometry independent saturation-voltage dependence of II
132	**A3L**	–	0	–	–	Length dependence of **A3**
133	**A3W**	–	0	–	–	Width dependence of **A3**
134	**A4O**	$V^{-\frac{1}{2}}$	0	–	–	Geometry independent back-bias dependence of II
135	**A4L**	–	0	–	–	Length dependence of **A4**
136	**A4W**	–	0	–	–	Width dependence of **A4**

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No.	Name	Unit	Default	Min.	Max.	Description
			Gate Current Parameters			
137	**GCOO**	–	0	–	–	Gate tunneling energy adjustment
138	**IGINVLW**	A	0	–	–	Gate channel current pre-factor for a channel area of $W_{\rm EN} \cdot L_{\rm EN}$
139	**IGOVW**	A	0	–	–	Gate overlap current pre-factor for a channel width of $W_{\rm EN}$
140	**IGOVDW**	A	0	–	–	Gate overlap current pre-factor for a channel width of $W_{\rm EN}$ for drain side
141	**STIGO**	–	2	–	–	Temperature dependence of gate current
142	**GC2O**	–	0.375	–	–	Gate current slope factor
143	**GC3O**	–	0.063	–	–	Gate current curvature factor
144	**CHIBO**	V	3.1	–	–	Tunneling barrier height
			Gate-Induced Drain Leakage (GIDL) Parameters			
145	**AGIDLW**	$\rm A/V^3$	0	–	–	Width dependence of GIDL pre-factor
146	**AGIDLDW**	$\rm A/V^3$	0	–	–	Width dependence of GIDL pre-factor for drain side
147	**BGIDLO**	V	41	–	–	GIDL probability factor at **TR**
148	**BGIDLDO**	V	41	–	–	GIDL probability factor at **TR** for drain side
149	**STBGIDLO**	V/K	0	–	–	Temperature dependence of **BGIDL**
150	**STBGIDLDO**	V/K	0	–	–	Temperature dependence of **BGIDL** for drain side
151	**CGIDLO**	–	0	–	–	Back-bias dependence of GIDL
152	**CGIDLDO**	–	0	–	–	Back-bias dependence of GIDL for drain side
			Charge Model Parameters			
153	**CGBOVL**	F	0	–	–	Oxide capacitance for gate–bulk overlap for a channel length of $L_{\rm EN}$
154	**CFRW**	F	0	–	–	Outer fringe capacitance for a channel width of $W_{\rm EN}$
155	**CFRDW**	F	0	–	–	Outer fringe capacitance for a channel width of $W_{\rm EN}$ for drain side
			Noise Model Parameters			
156	**FNTO**	–	1.0	–	–	Thermal noise coefficient
157	**FNTEXCL**	–	0	0	–	Length dependence of excess noise
158	**NFALW**	$\rm V^{-1}/m^4$	$8 \cdot 10^{22}$	–	–	First coefficient of flicker noise for a channel area of $W_{\rm EN} \cdot L_{\rm EN}$
159	**NFBLW**	$\rm V^{-1}/m^2$	$3 \cdot 10^7$	–	–	Second coefficient of flicker noise for a channel area of $W_{\rm EN} \cdot L_{\rm EN}$
160	**NFCLW**	$\rm V^{-1}$	0	–	–	Third coefficient of flicker noise for a channel area of $W_{\rm EN} \cdot L_{\rm EN}$
161	**EFO**	–	1.0	–	–	Flicker noise frequency exponent
162	**LINTNOI**	m	0.0	–	–	Length offset for flicker noise

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No.	Name	Unit	Default	Min.	Max.	Description
163	**ALPNOI**	–	2.0	–	–	Exponent for length offset for flicker noise
			Other Parameters			
164	**DTA**	K	0	–	–	Temperature offset w.r.t. ambient circuit temperature

2.5.4 Parameters for binning model

The binning scaling rules of PSP (see Section 3.3) have been developed as a flexible but phenomenological alternative to the geometrical scaling rules.

No.	Name	Unit	Default	Min.	Max.	Description
0	**LEVEL**	–	1021	–	–	Model selection parameter; see Sec. 6.1
1	**TYPE**	–	1	−1	1	Channel type parameter; 1 ↔ NMOS, −1 ↔ PMOS[4]
2	**TR**	°C	21	−273	–	reference temperature
			Switch Parameters			
3	**PARAMCHK**	–	0	–	–	Level of clip-warning info[5]
4	**SWIGATE**	–	0	0	1	Flag for gate current (0 ↔ “off”)
5	**SWIMPACT**	–	0	0	1	Flag for impact ionization current (0 ↔ “off”)
6	**SWGIDL**	–	0	0	1	Flag for GIDL/GISL current (0 ↔ “off”)
7	**SWJUNCAP**	–	0	0	3	Flag for JUNCAP (0 ↔ “off”); see Sec. 2.5.2
8	**SWJUNASYM**	–	0	–	–	Flag for asymmetric junctions (0 ↔ “off”)[6]
9	**QMC**	–	1	0	–	Quantum-mechanical correction factor
			Labels for binning set			
10	**LMIN**	m	0	–	–	Dummy parameter to label binning set
11	**LMAX**	m	1	–	–	Dummy parameter to label binning set
12	**WMIN**	m	0	–	–	Dummy parameter to label binning set
13	**WMAX**	m	1	–	–	Dummy parameter to label binning set
			Process Parameters			
14	**LVARO**	m	0	–	–	Geometry independent difference between actual and programmed poly-silicon gate length
15	**LVARL**	–	0	–	–	Length dependence of difference between actual and programmed poly-silicon gate length
16	**LAP**	m	0	–	–	Effective channel length reduction per side due to lateral diffusion of source/drain dopant ions
17	**WVARO**	m	0	–	–	Geometry independent difference between actual and programmed field-oxide opening
18	**WVARW**	–	0	–	–	Width dependence of difference between actual and programmed field-oxide opening
19	**WOT**	m	0	–	–	Effective reduction of channel width per side due to lateral diffusion of channel-stop dopant ions
20	**DLQ**	m	0	–	–	Effective channel length reduction for CV
21	**DWQ**	m	0	–	–	Effective channel width reduction for CV

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[4] See Section 6.3.1 for more information on usage of **TYPE** in various simulators.
[5] Only in SiMKit-version of PSP. See Section 6.5.4 for more information.
[6] See Section 3.7 for more information on usage of **SWJUNASYM**.

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No.	Name	Unit	Default	Min.	Max.	Description
22	**POVFB**	V	-1	–	–	Coefficient for the geometry independent part of flat-band voltage at **TR**
23	**PLVFB**	V	0	–	–	Coefficient for the length dependence of flat-band voltage at **TR**
24	**PWVFB**	V	0	–	–	Coefficient for the width dependence of flat-band voltage at **TR**
25	**PLWVFB**	V	0	–	–	Coefficient for the length times width dependence of flat-band voltage at **TR**
26	**POSTVFB**	V/K	$5 \cdot 10^{-4}$	–	–	Coefficient for the geometry independent part of temperature dependence of **VFB**
27	**PLSTVFB**	V/K	0	–	–	Coefficient for the length dependence of temperature dependence of **VFB**
28	**PWSTVFB**	V/K	0	–	–	Coefficient for the width dependence of temperature dependence of **VFB**
29	**PLWSTVFB**	V/K	0	–	–	Coefficient for the length times width dependence of temperature dependence of **VFB**
30	**POTOX**	m	$2 \cdot 10^{-9}$	–	–	Coefficient for the geometry independent part of gate oxide thickness
31	**POEPSROX**	–	3.9	1	–	Coefficient for the geometry independent part of relative permittivity of gate dielectric
32	**PONEFF**	m^{-3}	$5 \cdot 10^{23}$	–	–	Coefficient for the geometry independent part of substrate doping
33	**PLNEFF**	m^{-3}	0	–	–	Coefficient for the length dependence of substrate doping
34	**PWNEFF**	m^{-3}	0	–	–	Coefficient for the width dependence of substrate doping
35	**PLWNEFF**	m^{-3}	0	–	–	Coefficient for the length times width dependence of substrate doping
36	**POVNSUB**	V	0	–	–	Coefficient for the geometry independent part of effective doping bias-dependence parameter
37	**PONSLP**	V	$5 \cdot 10^{-2}$	–	–	Coefficient for the geometry independent part of effective doping bias-dependence parameter
38	**PODNSUB**	V^{-1}	0	–	–	Coefficient for the geometry independent part of effective doping bias-dependence parameter
39	**PODPHIB**	V	0	–	–	Coefficient for the geometry independent part of offset of ϕ_{B}
40	**PLDPHIB**	V	0	–	–	Coefficient for the length dependence of offset of ϕ_{B}

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No.	Name	Unit	Default	Min.	Max.	Description
41	**PWDPHIB**	V	0	–	–	Coefficient for the width dependence of offset of ϕ_B
42	**PLWDPHIB**	V	0	–	–	Coefficient for the length times width dependence of offset of ϕ_B
43	**PONP**	m^{-3}	10^{26}	–	–	Coefficient for the geometry independent part of gate poly-silicon doping
44	**PLNP**	m^{-3}	0	–	–	Coefficient for the length dependence of gate poly-silicon doping
45	**PWNP**	m^{-3}	0	–	–	Coefficient for the width dependence of gate poly-silicon doping
46	**PLWNP**	m^{-3}	0	–	–	Coefficient for the length times width dependence of gate poly-silicon doping
47	**POCT**	–	0	–	–	Coefficient for the geometry independent part of interface states factor
48	**PLCT**	–	0	–	–	Coefficient for the length dependence of interface states factor
49	**PWCT**	–	0	–	–	Coefficient for the width dependence of interface states factor
50	**PLWCT**	–	0	–	–	Coefficient for the length times width dependence of interface states factor
51	**POTOXOV**	m	$2 \cdot 10^{-9}$	–	–	Coefficient for the geometry independent part of overlap oxide thickness
52	**POTOXOVD**	m	$2 \cdot 10^{-9}$	–	–	Coefficient for the geometry independent part of overlap oxide thickness for drain side
53	**PONOV**	m^{-3}	$5 \cdot 10^{25}$	–	–	Coefficient for the geometry independent part of effective doping of overlap region
54	**PLNOV**	m^{-3}	0	–	–	Coefficient for the length dependence of effective doping of overlap region
55	**PWNOV**	m^{-3}	0	–	–	Coefficient for the width dependence of effective doping of overlap region
56	**PLWNOV**	m^{-3}	0	–	–	Coefficient for the length times width dependence of effective doping of overlap region
57	**PONOVD**	m^{-3}	$5 \cdot 10^{25}$	–	–	Coefficient for the geometry independent part of effective doping of overlap region for drain side
58	**PLNOVD**	m^{-3}	0	–	–	Coefficient for the length dependence of effective doping of overlap region for drain side
59	**PWNOVD**	m^{-3}	0	–	–	Coefficient for the width dependence of effective doping of overlap region for drain side
60	**PLWNOVD**	m^{-3}	0	–	–	Coefficient for the length times width dependence of effective doping of overlap region for drain side

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No.	Name	Unit	Default	Min.	Max.	Description
			DIBL Parameters			
61	**POCF**	V^{-1}	0	–	–	Coefficient for the geometry independent part of DIBL parameter
62	**PLCF**	V^{-1}	0	–	–	Coefficient for the length dependence of DIBL parameter
63	**PWCF**	V^{-1}	0	–	–	Coefficient for the width dependence of DIBL parameter
64	**PLWCF**	V^{-1}	0	–	–	Coefficient for the length times width dependence of DIBL parameter
65	**POCFB**	V^{-1}	0	–	–	Coefficient for the geometry independent part of back-bias dependence of **CF**
			Mobility Parameters			
66	**POBETN**	$m^2/V/s$	$7 \cdot 10^{-2}$	–	–	Coefficient for the geometry independent part of product of channel aspect ratio and zero-field mobility at **TR**
67	**PLBETN**	$m^2/V/s$	0	–	–	Coefficient for the length dependence of product of channel aspect ratio and zero-field mobility at **TR**
68	**PWBETN**	$m^2/V/s$	0	–	–	Coefficient for the width dependence of product of channel aspect ratio and zero-field mobility at **TR**
69	**PLWBETN**	$m^2/V/s$	0	–	–	Coefficient for the length times width dependence of product of channel aspect ratio and zero-field mobility at **TR**
70	**POSTBET**	–	1	–	–	Coefficient for the geometry independent part of temperature dependence of **BETN**
71	**PLSTBET**	–	0	–	–	Coefficient for the length dependence of temperature dependence of **BETN**
72	**PWSTBET**	–	0	–	–	Coefficient for the width dependence of temperature dependence of **BETN**
73	**PLWSTBET**	–	0	–	–	Coefficient for the length times width dependence of temperature dependence of **BETN**
74	**POMUE**	m/V	$5 \cdot 10^{-1}$	–	–	Coefficient for the geometry independent part of mobility reduction coefficient at **TR**
75	**PLMUE**	m/V	0	–	–	Coefficient for the length dependence of mobility reduction coefficient at **TR**
76	**PWMUE**	m/V	0	–	–	Coefficient for the width dependence of mobility reduction coefficient at **TR**
77	**PLWMUE**	m/V	0	–	–	Coefficient for the length times width dependence of mobility reduction coefficient at **TR**
78	**POSTMUE**	–	0	–	–	Coefficient for the geometry independent part of temperature dependence of **MUE**

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No.	Name	Unit	Default	Min.	Max.	Description
79	**POTHEMU**	–	1.5	–	–	Coefficient for the geometry independent part of mobility reduction exponent at **TR**
80	**POSTTHEMU**	–	1.5	–	–	Coefficient for the geometry independent part of temperature dependence of **THEMU**
81	**POCS**	–	0	–	–	Coefficient for the geometry independent part of Coulomb scattering parameter at **TR**
82	**PLCS**	–	0	–	–	Coefficient for the length dependence of Coulomb scattering parameter at **TR**
83	**PWCS**	–	0	–	–	Coefficient for the width dependence of Coulomb scattering parameter at **TR**
84	**PLWCS**	–	0	–	–	Coefficient for the length times width dependence of Coulomb scattering parameter at **TR**
85	**POSTCS**	–	0	–	–	Coefficient for the geometry independent part of temperature dependence of **CS**
86	**POXCOR**	V^{-1}	0	–	–	Coefficient for the geometry independent part of non-universality parameter
87	**PLXCOR**	V^{-1}	0	–	–	Coefficient for the length dependence of non-universality parameter
88	**PWXCOR**	V^{-1}	0	–	–	Coefficient for the width dependence of non-universality parameter
89	**PLWXCOR**	V^{-1}	0	–	–	Coefficient for the length times width dependence of non-universality parameter
90	**POSTXCOR**	–	0	–	–	Coefficient for the geometry independent part of temperature dependence of **XCOR**
91	**POFETA**	–	1	–	–	Coefficient for the geometry independent part of effective field parameter
			Series Resistance Parameters			
92	**PORS**	Ω	30	–	–	Coefficient for the geometry independent part of source/drain series resistance at **TR**
93	**PLRS**	Ω	0	–	–	Coefficient for the length dependence of source/drain series resistance at **TR**
94	**PWRS**	Ω	0	–	–	Coefficient for the width dependence of source/drain series resistance at **TR**
95	**PLWRS**	Ω	0	–	–	Coefficient for the length times width dependence of source/drain series resistance at **TR**
96	**POSTRS**	–	1	–	–	Coefficient for the geometry independent part of temperature dependence of **RS**
97	**PORSB**	V^{-1}	0	–	–	Coefficient for the geometry independent part of back-bias dependence of **RS**

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No.	Name	Unit	Default	Min.	Max.	Description
98	**PORSG**	V^{-1}	0	–	–	Coefficient for the geometry independent part of gate-bias dependence of **RS**
			Velocity Saturation Parameters			
99	**POTHESAT**	V^{-1}	1	–	–	Coefficient for the geometry independent part of velocity saturation parameter at **TR**
100	**PLTHESAT**	V^{-1}	0	–	–	Coefficient for the length dependence of velocity saturation parameter at **TR**
101	**PWTHESAT**	V^{-1}	0	–	–	Coefficient for the width dependence of velocity saturation parameter at **TR**
102	**PLWTHESAT**	V^{-1}	0	–	–	Coefficient for the length times width dependence of velocity saturation parameter at **TR**
103	**POSTTHESAT**	–	1	–	–	Coefficient for the geometry independent part of temperature dependence of **THESAT**
104	**PLSTTHESAT**	–	0	–	–	Coefficient for the length dependence of temperature dependence of **THESAT**
105	**PWSTTHESAT**	–	0	–	–	Coefficient for the width dependence of temperature dependence of **THESAT**
106	**PLWSTTHESAT**	–	0	–	–	Coefficient for the length times width dependence of temperature dependence of **THESAT**
107	**POTHESATB**	V^{-1}	0	–	–	Coefficient for the geometry independent part of back-bias dependence of velocity saturation
108	**PLTHESATB**	V^{-1}	0	–	–	Coefficient for the length dependence of back-bias dependence of velocity saturation
109	**PWTHESATB**	V^{-1}	0	–	–	Coefficient for the width dependence of back-bias dependence of velocity saturation
110	**PLWTHESATB**	V^{-1}	0	–	–	Coefficient for the length times width dependence of back-bias dependence of velocity saturation
111	**POTHESATG**	V^{-1}	0	–	–	Coefficient for the geometry independent part of gate-bias dependence of velocity saturation
112	**PLTHESATG**	V^{-1}	0	–	–	Coefficient for the length dependence of gate-bias dependence of velocity saturation
113	**PWTHESATG**	V^{-1}	0	–	–	Coefficient for the width dependence of gate-bias dependence of velocity saturation
114	**PLWTHESATG**	V^{-1}	0	–	–	Coefficient for the length times width dependence of gate-bias dependence of velocity saturation
			Saturation Voltage Parameters			
115	**POAX**	–	3	–	–	Coefficient for the geometry independent part of linear/saturation transition factor

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No.	Name	Unit	Default	Min.	Max.	Description
116	**PLAX**	–	0	–	–	Coefficient for the length dependence of linear/saturation transition factor
117	**PWAX**	–	0	–	–	Coefficient for the width dependence of linear/saturation transition factor
118	**PLWAX**	–	0	–	–	Coefficient for the length times width dependence of linear/saturation transition factor
			Channel Length Modulation (CLM) Parameters			
119	**POALP**	–	10^{-2}	–	–	Coefficient for the geometry independent part of CLM pre-factor
120	**PLALP**	–	0	–	–	Coefficient for the length dependence of CLM pre-factor
121	**PWALP**	–	0	–	–	Coefficient for the width dependence of CLM pre-factor
122	**PLWALP**	–	0	–	–	Coefficient for the length times width dependence of CLM pre-factor
123	**POALP1**	V	0	–	–	Coefficient for the geometry independent part of CLM enhancement factor above threshold
124	**PLALP1**	V	0	–	–	Coefficient for the length dependence of CLM enhancement factor above threshold
125	**PWALP1**	V	0	–	–	Coefficient for the width dependence of CLM enhancement factor above threshold
126	**PLWALP1**	V	0	–	–	Coefficient for the length times width dependence of CLM enhancement factor above threshold
127	**POALP2**	V^{-1}	0	–	–	Coefficient for the geometry independent part of CLM enhancement factor below threshold
128	**PLALP2**	V^{-1}	0	–	–	Coefficient for the length dependence of CLM enhancement factor below threshold
129	**PWALP2**	V^{-1}	0	–	–	Coefficient for the width dependence of CLM enhancement factor below threshold
130	**PLWALP2**	V^{-1}	0	–	–	Coefficient for the length times width dependence of CLM enhancement factor below threshold
131	**POVP**	V	$5 \cdot 10^{-2}$	–	–	Coefficient for the geometry independent part of CLM logarithmic dependence parameter
			Impact Ionization (II) Parameters			
132	**POA1**	–	1	–	–	Coefficient for the geometry independent part of impact-ionization pre-factor
133	**PLA1**	–	0	–	–	Coefficient for the length dependence of impact-ionization pre-factor

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No.	Name	Unit	Default	Min.	Max.	Description
134	**PWA1**	–	0	–	–	Coefficient for the width dependence of impact-ionization pre-factor
135	**PLWA1**	–	0	–	–	Coefficient for the length times width dependence of impact-ionization pre-factor
136	**POA2**	V	10	–	–	Coefficient for the geometry independent part of impact-ionization exponent at **TR**
137	**POSTA2**	V	0	–	–	Coefficient for the geometry independent part of temperature dependence of **A2**
138	**POA3**	–	1	–	–	Coefficient for the geometry independent part of saturation-voltage dependence of II
139	**PLA3**	–	0	–	–	Coefficient for the length dependence of saturation-voltage dependence of II
140	**PWA3**	–	0	–	–	Coefficient for the width dependence of saturation-voltage dependence of II
141	**PLWA3**	–	0	–	–	Coefficient for the length times width dependence of saturation-voltage dependence of II
142	**POA4**	$\mathrm{V}^{-0.5}$	0	–	–	Coefficient for the geometry independent part of back-bias dependence of II
143	**PLA4**	$\mathrm{V}^{-0.5}$	0	–	–	Coefficient for the length dependence of back-bias dependence of II
144	**PWA4**	$\mathrm{V}^{-0.5}$	0	–	–	Coefficient for the width dependence of back-bias dependence of II
145	**PLWA4**	$\mathrm{V}^{-0.5}$	0	–	–	Coefficient for the length times width dependence of back-bias dependence of II
			Gate Current Parameters			
146	**POGCO**	–	0	–	–	Coefficient for the geometry independent part of gate tunneling energy adjustment
147	**POIGINV**	A	0	–	–	Coefficient for the geometry independent part of gate channel current pre-factor
148	**PLIGINV**	A	0	–	–	Coefficient for the length dependence of gate channel current pre-factor
149	**PWIGINV**	A	0	–	–	Coefficient for the width dependence of gate channel current pre-factor
150	**PLWIGINV**	A	0	–	–	Coefficient for the length times width dependence of gate channel current pre-factor
151	**POIGOV**	A	0	–	–	Coefficient for the geometry independent part of gate overlap current pre-factor
152	**PLIGOV**	A	0	–	–	Coefficient for the length dependence of gate overlap current pre-factor
153	**PWIGOV**	A	0	–	–	Coefficient for the width dependence of gate overlap current pre-factor
154	**PLWIGOV**	A	0	–	–	Coefficient for the length times width dependence of gate overlap current pre-factor

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No.	Name	Unit	Default	Min.	Max.	Description
155	**POSTIG**	–	2	–	–	Coefficient for the geometry independent part of temperature dependence of gate current
156	**POGC2**	–	$3.75 \cdot 10^{-1}$	–	–	Coefficient for the geometry independent part of gate current slope factor
157	**POGC3**	–	$6.3 \cdot 10^{-2}$	–	–	Coefficient for the geometry independent part of gate current curvature factor
158	**POCHIB**	V	3.1	–	–	Coefficient for the geometry independent part of tunneling barrier height
			Gate-Induced Drain Leakage (GIDL) Parameters			
159	**POAGIDL**	A/V^3	0	–	–	Coefficient for the geometry independent part of GIDL pre-factor
160	**PLAGIDL**	A/V^3	0	–	–	Coefficient for the length dependence of GIDL pre-factor
161	**PWAGIDL**	A/V^3	0	–	–	Coefficient for the width dependence of GIDL pre-factor
162	**PLWAGIDL**	A/V^3	0	–	–	Coefficient for the length times width dependence of GIDL pre-factor
163	**POAGIDLD**	A/V^3	0	–	–	Coefficient for the geometry independent part of GIDL pre-factor for drain side
164	**PLAGIDLD**	A/V^3	0	–	–	Coefficient for the length dependence of GIDL pre-factor for drain side
165	**PWAGIDLD**	A/V^3	0	–	–	Coefficient for the width dependence of GIDL pre-factor for drain side
166	**PLWAGIDLD**	A/V^3	0	–	–	Coefficient for the length times width dependence of GIDL pre-factor for drain side
167	**POBGIDL**	V	41	–	–	Coefficient for the geometry independent part of GIDL probability factor at **TR**
168	**POBGIDLD**	V	41	–	–	Coefficient for the geometry independent part of GIDL probability factor at **TR** for drain side
169	**POSTBGIDL**	V/K	0	–	–	Coefficient for the geometry independent part of temperature dependence of **BGIDL**
170	**POSTBGIDLD**	V/K	0	–	–	Coefficient for the geometry independent part of temperature dependence of **BGIDL** for drain side
171	**POCGIDL**	–	0	–	–	Coefficient for the geometry independent part of back-bias dependence of GIDL
172	**POCGIDLD**	–	0	–	–	Coefficient for the geometry independent part of back-bias dependence of GIDL for drain side
			Charge Model Parameters			

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No.	Name	Unit	Default	Min.	Max.	Description
173	**POCOX**	F	10^{-14}	–	–	Coefficient for the geometry independent part of oxide capacitance for intrinsic channel
174	**PLCOX**	F	0	–	–	Coefficient for the length dependence of oxide capacitance for intrinsic channel
175	**PWCOX**	F	0	–	–	Coefficient for the width dependence of oxide capacitance for intrinsic channel
176	**PLWCOX**	F	0	–	–	Coefficient for the length times width dependence of oxide capacitance for intrinsic channel
177	**POCGOV**	F	10^{-15}	–	–	Coefficient for the geometry independent part of oxide capacitance for gate-drain/source overlap
178	**PLCGOV**	F	0	–	–	Coefficient for the length dependence of oxide capacitance for gate-drain/source overlap
179	**PWCGOV**	F	0	–	–	Coefficient for the width dependence of oxide capacitance for gate-drain/source overlap
180	**PLWCGOV**	F	0	–	–	Coefficient for the length times width dependence of oxide capacitance for gate-drain/source overlap
181	**POCGOVD**	F	10^{-15}	–	–	Coefficient for the geometry independent part of oxide capacitance for gate-drain/source overlap for drain side
182	**PLCGOVD**	F	0	–	–	Coefficient for the length dependence of oxide capacitance for gate-drain/source overlap for drain side
183	**PWCGOVD**	F	0	–	–	Coefficient for the width dependence of oxide capacitance for gate-drain/source overlap for drain side
184	**PLWCGOVD**	F	0	–	–	Coefficient for the length times width dependence of oxide capacitance for gate-drain/source overlap for drain side
185	**POCGBOV**	F	0	–	–	Coefficient for the geometry independent part of oxide capacitance for gate-bulk overlap
186	**PLCGBOV**	F	0	–	–	Coefficient for the length dependence of oxide capacitance for gate-bulk overlap
187	**PWCGBOV**	F	0	–	–	Coefficient for the width dependence of oxide capacitance for gate-bulk overlap
188	**PLWCGBOV**	F	0	–	–	Coefficient for the length times width dependence of oxide capacitance for gate-bulk overlap
189	**POCFR**	F	0	–	–	Coefficient for the geometry independent part of outer fringe capacitance

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No.	Name	Unit	Default	Min.	Max.	Description
190	**PLCFR**	F	0	–	–	Coefficient for the length dependence of outer fringe capacitance
191	**PWCFR**	F	0	–	–	Coefficient for the width dependence of outer fringe capacitance
192	**PLWCFR**	F	0	–	–	Coefficient for the length times width dependence of outer fringe capacitance
193	**POCFRD**	F	0	–	–	Coefficient for the geometry independent part of outer fringe capacitance for drain side
194	**PLCFRD**	F	0	–	–	Coefficient for the length dependence of outer fringe capacitance for drain side
195	**PWCFRD**	F	0	–	–	Coefficient for the width dependence of outer fringe capacitance for drain side
196	**PLWCFRD**	F	0	–	–	Coefficient for the length times width dependence of outer fringe capacitance for drain side
			Noise Model Parameters			
197	**POFNT**	–	1	–	–	Coefficient for the geometry independent part of thermal noise coefficient
198	**POFNTEXC**	–	0	–	–	Coefficient for the geometry independent part of excess noise
199	**PLFNTEXC**	–	0	–	–	Coefficient for the length dependence of excess noise
200	**PWFNTEXC**	–	0	–	–	Coefficient for the width dependence of excess noise
201	**PLWFNTEXC**	–	0	–	–	Coefficient for the length times width dependence of excess noise
202	**PONFA**	$\mathrm{V^{-1}/m^4}$	$8 \cdot 10^{22}$	–	–	Coefficient for the geometry independent part of first coefficient of flicker noise
203	**PLNFA**	$\mathrm{V^{-1}/m^4}$	0	–	–	Coefficient for the length dependence of first coefficient of flicker noise
204	**PWNFA**	$\mathrm{V^{-1}/m^4}$	0	–	–	Coefficient for the width dependence of first coefficient of flicker noise
205	**PLWNFA**	$\mathrm{V^{-1}/m^4}$	0	–	–	Coefficient for the length times width dependence of first coefficient of flicker noise
206	**PONFB**	$\mathrm{V^{-1}/m^2}$	$3 \cdot 10^{7}$	–	–	Coefficient for the geometry independent part of second coefficient of flicker noise
207	**PLNFB**	$\mathrm{V^{-1}/m^2}$	0	–	–	Coefficient for the length dependence of second coefficient of flicker noise
208	**PWNFB**	$\mathrm{V^{-1}/m^2}$	0	–	–	Coefficient for the width dependence of second coefficient of flicker noise
209	**PLWNFB**	$\mathrm{V^{-1}/m^2}$	0	–	–	Coefficient for the length times width dependence of second coefficient of flicker noise

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No.	Name	Unit	Default	Min.	Max.	Description
210	**PONFC**	V^{-1}	0	–	–	Coefficient for the geometry independent part of third coefficient of flicker noise
211	**PLNFC**	V^{-1}	0	–	–	Coefficient for the length dependence of third coefficient of flicker noise
212	**PWNFC**	V^{-1}	0	–	–	Coefficient for the width dependence of third coefficient of flicker noise
213	**PLWNFC**	V^{-1}	0	–	–	Coefficient for the length times width dependence of third coefficient of flicker noise
214	**POEF**	–	1.0	–	–	Coefficient for the geometry independent part of flicker noise frequency exponent
			Other Parameters			
215	**DTA**	K	0	–	–	temperature offset w.r.t. ambient circuit temperature

2.5.5 Parameters for stress model

The stress model of BSIM4.4.0 has been adopted in PSP with as little modifications as possible. Parameter names have been copied, but they have been subjected to PSP conventions by replacing every zero by an '**O**'. Moreover, the parameters **STK2** and **LODK2** are not available in PSP. Except for these changes, stress parameters determined for BSIM can be directly applied in PSP. Some trivial conversion of parameters BSIM→PSP is still necessary, see [2].

The parameters in this section are part of PSP's global parameter set (both geometrical and binning).

No.	Name	Unit	Default	Min.	Max.	Description
0	**SAREF**	m	10^{-6}	10^{-9}	–	Reference distance between OD edge to Poly from one side
1	**SBREF**	m	10^{-6}	10^{-9}	–	Reference distance between OD edge to Poly from other side
2	**WLOD**	m	0	–	–	Width parameter
3	**KUO**	m	0	–	–	Mobility degradation/enhancement coefficient
4	**KVSAT**	m	0	-1	1	Saturation velocity degradation/enhancement parameter
5	**TKUO**	–	0	–	–	Temperature coefficient of **KUO**
6	**LKUO**	$\mathrm{m}^{\mathbf{LLODKUO}}$	0	–	–	Length dependence of **KUO**
7	**WKUO**	$\mathrm{m}^{\mathbf{WLODKUO}}$	0	–	–	Width dependence of **KUO**
8	**PKUO**	$\mathrm{m}^{\mathbf{LLODKUO}+\mathbf{WLODKUO}}$	0	–	–	Cross-term dependence of **KUO**
9	**LLODKUO**	–	0	0	–	Length parameter for mobility stress effect
10	**WLODKUO**	–	0	0	–	Width parameter for mobility stress effect
11	**KVTHO**	Vm	0	–	–	Threshold shift parameter
12	**LKVTHO**	$\mathrm{m}^{\mathbf{LLODVTH}}$	0	–	–	Length dependence of **KVTHO**
13	**WKVTHO**	$\mathrm{m}^{\mathbf{WLODVTH}}$	0	–	–	Width dependence of **KVTHO**
14	**PKVTHO**	$\mathrm{m}^{\mathbf{LLODVTH}+\mathbf{WLODVTH}}$	0	–	–	Cross-term dependence of **KVTHO**
15	**LLODVTH**	–	0	0	–	Length parameter for threshold voltage stress effect
16	**WLODVTH**	–	0	0	–	Width parameter for threshold voltage stress effect
17	**STETAO**	m	0	–	–	ETAO shift factor related to threshold voltage change
18	**LODETAO**	–	1	0	–	ETAO shift modification factor

2.5.6 Parameters for well proximity effect model

The WPE model of BSIM4.5.0 has been adopted in PSP with as little modifications as possible. Parameter names have been copied, but they have been subjected to PSP conventions by replacing every zero by an '**O**'. Moreover, the parameter **K2WE** is not available in PSP. Except for some trivial conversion of parameters BSIM→PSP [2], WPE parameters from BSIM can be used directly in PSP. The WPE parameters have both geometrical and binning rules included as explained in Section 3.6.2. Consequently one of the following parameter sets can be used depending on which scaling rule is selected.

The parameters in the following table are part of PSP's global parameter set.

No.	Name	Unit	Default	Min.	Max.	Description
0	**SCREF**	m	$1 \cdot 10^{-6}$	0	–	Distance between OD-edge and well edge of a reference device
1	**WEB**	–	0	–	–	Coefficient for **SCB**
2	**WEC**	–	0	–	–	Coefficient for **SCC**
3	**KVTHOWEO**	–	0	–	–	Geometry independent threshold shift parameter
4	**KVTHOWEL**	–	0	–	–	Length dependence of threshold shift parameter
5	**KVTHOWEW**	–	0	–	–	Width dependence of threshold shift parameter
6	**KVTHOWELW**	–	0	–	–	Area dependence of threshold shift parameter
7	**KUOWEO**	–	0	–	–	Geometry independent mobility degradation factor
8	**KUOWEL**	–	0	–	–	Length dependence of mobility degradation factor
9	**KUOWEW**	–	0	–	–	Width dependence of mobility degradation factor
10	**KUOWELW**	–	0	–	–	Area dependence of mobility degradation factor

The parameters in the following table are part of PSP's binning parameter set.

No.	Name	Unit	Default	Min.	Max.	Description
0	**SCREF**	m	$1 \cdot 10^{-6}$	0	–	Distance between OD-edge and well edge of a reference device
1	**WEB**	–	0	–	–	Coefficient for **SCB**
2	**WEC**	–	0	–	–	Coefficient for **SCC**
3	**POKVTHOWE**	–	0	–	–	Coefficient for the geometry independent part of threshold shift parameter
4	**PLKVTHOWE**	–	0	–	–	Coefficient for the length dependence of threshold shift parameter
5	**PWKVTHOWE**	–	0	–	–	Coefficient for the width dependence of threshold shift parameter

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No.	Name	Unit	Default	Min.	Max.	Description
6	**PLWKVTHOWE**	–	0	–	–	Coefficient for the length times width dependence of threshold shift parameter
7	**POKUOWE**	–	0	–	–	Coefficient for the geometry independent part of mobility degradation factor
8	**PLKUOWE**	–	0	–	–	Coefficient for the length dependence of mobility degradation factor
9	**PWKUOWE**	–	0	–	–	Coefficient for the width dependence of mobility degradation factor
10	**PLWKUOWE**	–	0	–	–	Coefficient for the length times width dependence of mobility degradation factor

2.5.7 Parameters for local model

The set of local parameters valid for an individual transistor with a specific channel width and length are given in the table below. Since the local parameter set is valid for one device with a specific geometry, it does not contain the channel length and width as instance parameters.

No.	Name	Unit	Default	Min.	Max.	Description
0	**LEVEL**	–	102	–	–	Model selection parameter; see Sec. 6.1
1	**TYPE**	–	1	-1	1	Channel type parameter; $1 \leftrightarrow$ NMOS, $-1 \leftrightarrow$ PMOS[7]
2	**TR**	°C	21	-273	–	Reference temperature
				Switch Parameters		
3	**PARAMCHK**	–	0	–	–	Level of clip-warning info[8]
4	**SWIGATE**	–	0	0	1	Flag for gate current ($0 \leftrightarrow$ “off”)
5	**SWIMPACT**	–	0	0	1	Flag for impact ionization current ($0 \leftrightarrow$ “off”)
6	**SWGIDL**	–	0	0	1	Flag for GIDL/GISL current ($0 \leftrightarrow$ “off”)
7	**SWJUNCAP**	–	0	0	3	Flag for JUNCAP ($0 \leftrightarrow$ “off”); see Sec. 2.5.2
8	**SWJUNASYM**	–	0	–	–	Flag for asymmetric junctions ($0 \leftrightarrow$ “off”)[9]
9	**QMC**	–	1	0	–	Quantum-mechanical correction factor
				Process Parameters		
10	**VFB**	V	-1	–	–	Flat-band voltage at **TR**
11	**STVFB**	V/K	$5 \cdot 10^{-4}$	–	–	Temperature dependence of **VFB**
12	**TOX**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Gate oxide thickness
13	**EPSROX**	–	3.9	1	–	Relative permittivity of gate dielectric
14	**NEFF**	m^{-3}	$5 \cdot 10^{23}$	10^{20}	10^{26}	Substrate doping
15	**VNSUB**	V	0	–	–	Effective doping bias-dependence parameter
16	**NSLP**	V	0.05	10^{-3}	–	Effective doping bias-dependence parameter
17	**DNSUB**	V^{-1}	0	0	1	Effective doping bias-dependence parameter
18	**DPHIB**	V	0	–	–	Offset of φ_B
19	**NP**	m^{-3}	10^{26}	0	–	Gate poly-silicon doping
20	**CT**	–	0	0	–	Interface states factor
21	**TOXOV**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness
22	**TOXOVD**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness for drain side
23	**NOV**	m^{-3}	$5 \cdot 10^{25}$	10^{20}	10^{27}	Effective doping of overlap region
24	**NOVD**	m^{-3}	$5 \cdot 10^{25}$	10^{20}	10^{27}	Effective doping of overlap region for drain side
				DIBL Parameters		
25	**CF**	V^{-1}	0	0	–	DIBL parameter

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[7] See Section 6.3.1 for more information on usage of **TYPE** in various simulators.
[8] Only in SiMKit-version of PSP. See Section 6.5.4 for more information.
[9] See Section 3.7 for more information on usage of **SWJUNASYM**.

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No.	Name	Unit	Default	Min.	Max.	Description
26	**CFB**	V^{-1}	0	0	1	Back-bias dependence of **CF**
			Mobility Parameters			
27	**BETN**	$m^2/V/s$	$7 \cdot 10^{-2}$	0	–	Product of channel aspect ratio and zero-field mobility at **TR**
28	**STBET**	–	1	–	–	Temperature dependence of **BETN**
29	**MUE**	m/V	0.5	0	–	Mobility reduction coefficient at **TR**
30	**STMUE**	–	0	–	–	Temperature dependence of **MUE**
31	**THEMU**	–	1.5	0	–	Mobility reduction exponent at **TR**
32	**STTHEMU**	–	1.5	–	–	Temperature dependence of **THEMU**
33	**CS**	–	0	0	–	Coulomb scattering parameter at **TR**
34	**STCS**	–	0	–	–	Temperature dependence of **CS**
35	**XCOR**	V^{-1}	0	0	–	Non-universality parameter
36	**STXCOR**	–	0	–	–	Temperature dependence of **XCOR**
37	**FETA**	–	1	0	–	Effective field parameter
			Series Resistance Parameters			
38	**RS**	Ω	30	0	–	Source/drain series resistance at **TR**
39	**STRS**	–	1	–	–	Temperature dependence of **RS**
40	**RSB**	V^{-1}	0	−0.5	1	Back-bias dependence of **RS**
41	**RSG**	V^{-1}	0	−0.5	–	Gate-bias dependence of **RS**
			Velocity Saturation Parameters			
42	**THESAT**	V^{-1}	1	0	–	Velocity saturation parameter at **TR**
43	**STTHESAT**	–	1	–	–	Temperature dependence of **THESAT**
44	**THESATB**	V^{-1}	0	−0.5	1	Back-bias dependence of velocity saturation
45	**THESATG**	V^{-1}	0	−0.5	–	Gate-bias dependence of velocity saturation
			Saturation Voltage Parameter			
46	**AX**	-	3	2	–	Linear/saturation transition factor
			Channel Length Modulation (CLM) Parameters			
47	**ALP**	–	0.01	0	–	CLM pre-factor
48	**ALP1**	V	0	0	–	CLM enhancement factor above threshold
49	**ALP2**	V^{-1}	0	0	–	CLM enhancement factor below threshold
50	**VP**	V	0.05	10^{-10}	–	CLM logarithmic dependence parameter
			Impact Ionization (II) Parameters			
51	**A1**	–	1	0	–	Impact-ionization pre-factor
52	**A2**	V	10	0	–	Impact-ionization exponent at **TR**
53	**STA2**	V	0	–	–	Temperature dependence of **A2**
54	**A3**	–	1	0	–	Saturation-voltage dependence of II
55	**A4**	$V^{-\frac{1}{2}}$	0	0	–	Back-bias dependence of II
			Gate Current Parameters			

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No.	Name	Unit	Default	Min.	Max.	Description
56	**GCO**	–	0	-10	10	Gate tunnelling energy adjustment
57	**IGINV**	A	0	0	–	Gate channel current pre-factor
58	**IGOV**	A	0	0	–	Gate overlap current pre-factor
59	**IGOVD**	A	0	0	–	Gate overlap current pre-factor for drain side
60	**STIG**	–	2	–	–	Temperature dependence of gate current
61	**GC2**	–	0.375	0	10	Gate current slope factor
62	**GC3**	–	0.063	-2	2	Gate current curvature factor
63	**CHIB**	V	3.1	1	–	Tunnelling barrier height
			Gate-Induced Drain Leakage (GIDL) Parameters			
64	**AGIDL**	A/V^3	0	0	–	GIDL pre-factor
65	**AGIDLD**	A/V^3	0	0	–	GIDL pre-factor for drain side
66	**BGIDL**	V	41	0	–	GIDL probability factor at **TR**
67	**BGIDLD**	V	41	0	–	GIDL probability factor at **TR** for drain side
68	**STBGIDL**	V/K	0	–	–	Temperature dependence of **BGIDL**
69	**STBGIDLD**	V/K	0	–	–	Temperature dependence of **BGIDL** for drain side
70	**CGIDL**	–	0	–	–	Back-bias dependence of GIDL
71	**CGIDLD**	–	0	–	–	Back-bias dependence of GIDL for drain side
			Charge Model Parameters			
72	**COX**	F	10^{-14}	0	–	Oxide capacitance for intrinsic channel
73	**CGOV**	F	10^{-15}	0	–	Oxide capacitance for gate–drain/source overlap
74	**CGOVD**	F	10^{-15}	0	–	Oxide capacitance for gate–drain/source overlap for drain side
75	**CGBOV**	F	0	0	–	Oxide capacitance for gate–bulk overlap
76	**CFR**	F	0	0	–	Outer fringe capacitance
77	**CFRD**	F	0	0	–	Outer fringe capacitance for drain side
			Noise Model Parameters			
78	**FNT**	–	1.0	0	–	Thermal noise coefficient
79	**FNTEXC**	–	0	0	–	Excess noise coefficient
80	**NFA**	V^{-1}/m^4	$8 \cdot 10^{22}$	0	–	First coefficient of flicker noise
81	**NFB**	V^{-1}/m^2	$3 \cdot 10^{7}$	0	–	Second coefficient of flicker noise
82	**NFC**	V^{-1}	0	0	–	Third coefficient of flicker noise
83	**EF**	–	1.0	0	–	Flicker noise frequency exponent
			Other Parameters			
84	**DTA**	K	0	–	–	Temperature offset w.r.t. ambient circuit temperature

2.5.8 Parameters for source-bulk and drain-bulk junction model

The JUNCAP2 parameters are part of both the global and the local parameter sets. The last column of **Asym.** shows for which value of **SWJUNASYM** the listed parameter is enabled: i.e., when **SWJUNASYM** $= 0$, parameters No. 3-45 are used for both source-bulk and drain-bulk junctions and parameters No. 46-88 are ignored; when **SWJUNASYM** $= 1$, parameters No. 3-45 are used for source-bulk junction and No. 46-88 are used for drain-bulk junction; parameters No. 0-2 are used in both situations.

No.	Name	Unit	Default	Min.	Max.	Description	Asym.
0	**TRJ**	°C	21	$T_{\rm min}$	–	Reference temperature	0, 1
1	**SWJUNEXP**	–	0	0	1	Flag for JUNCAP2 Express; 0 ↔ full JUNCAP2 model, 1 ↔ Express model	0, 1
2	**IMAX**	A	1000	10^{-12}	–	Maximum current up to which forward current behaves exponentially	0, 1
				Capacitance Parameters			
3	**CJORBOT**	F/m^2	10^{-3}	10^{-12}	–	Zero-bias capacitance per unit-of-area of bottom component for source-bulk junction	0, 1
4	**CJORSTI**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of STI-edge component for source-bulk junction	0, 1
5	**CJORGAT**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of gate-edge component for source-bulk junction	0, 1
6	**VBIRBOT**	V	1	$V_{\rm bi,low}$	–	Built-in voltage at the reference temperature of bottom component for source-bulk junction	0, 1
7	**VBIRSTI**	V	1	$V_{\rm bi,low}$	–	Built-in voltage at the reference temperature of STI-edge component for source-bulk junction	0, 1
8	**VBIRGAT**	V	1	$V_{\rm bi,low}$	–	Built-in voltage at the reference temperature of gate-edge component for source-bulk junction	0, 1
9	**PBOT**	–	0.5	0.05	0.95	Grading coefficient of bottom component for source-bulk junction	0, 1
10	**PSTI**	–	0.5	0.05	0.95	Grading coefficient of STI-edge component for source-bulk junction	0, 1
11	**PGAT**	–	0.5	0.05	0.95	Grading coefficient of gate-edge component for source-bulk junction	0, 1
				Ideal-current Parameters			
12	**PHIGBOT**	V	1.16	–	–	Zero-temperature bandgap voltage of bottom component for source-bulk junction	0, 1
13	**PHIGSTI**	V	1.16	–	–	Zero-temperature bandgap voltage of STI-edge component for source-bulk junction	0, 1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
14	**PHIGGAT**	V	1.16	–	–	Zero-temperature bandgap voltage of gate-edge component for source-bulk junction	0, 1
15	**IDSATRBOT**	A/m^2	10^{-12}	0	–	Saturation current density at the reference temperature of bottom component for source-bulk junction	0, 1
16	**IDSATRSTI**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of STI-edge component for source-bulk junction	0, 1
17	**IDSATRGAT**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of gate-edge component for source-bulk junction	0, 1
				Shockley-Read-Hall Parameters			
18	**CSRHBOT**	A/m^3	10^2	0	–	Shockley-Read-Hall prefactor of bottom component for source-bulk junction	0, 1
19	**CSRHSTI**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of STI-edge component for source-bulk junction	0, 1
20	**CSRHGAT**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of gate-edge component for source-bulk junction	0, 1
21	**XJUNSTI**	m	10^{-7}	10^{-9}	–	Junction depth of STI-edge component for source-bulk junction	0, 1
22	**XJUNGAT**	m	10^{-7}	10^{-9}	–	Junction depth of gate-edge component for source-bulk junction	0, 1
				Trap-assisted Tunneling Parameters			
23	**CTATBOT**	A/m^3	10^2	0	–	Trap-assisted tunneling prefactor of bottom component for source-bulk junction	0, 1
24	**CTATSTI**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of STI-edge component for source-bulk junction	0, 1
25	**CTATGAT**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of gate-edge component for source-bulk junction	0, 1
26	**MEFFTATBOT**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of bottom component for source-bulk junction	0, 1
27	**MEFFTATSTI**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of STI-edge component for source-bulk junction	0, 1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
28	**MEFFTATGAT**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of gate-edge component for source-bulk junction	0, 1
				Band-to-band Tunneling Parameters			
29	**CBBTBOT**	AV^{-3}	10^{-12}	0	–	Band-to-band tunneling prefactor of bottom component for source-bulk junction	0, 1
30	**CBBTSTI**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of STI-edge component for source-bulk junction	0, 1
31	**CBBTGAT**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of gate-edge component for source-bulk junction	0, 1
32	**FBBTRBOT**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of bottom component for source-bulk junction	0, 1
33	**FBBTRSTI**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of STI-edge component for source-bulk junction	0, 1
34	**FBBTRGAT**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of gate-edge component for source-bulk junction	0, 1
35	**STFBBTBOT**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of bottom component for source-bulk junction	0, 1
36	**STFBBTSTI**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of STI-edge component for source-bulk junction	0, 1
37	**STFBBTGAT**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of gate-edge component for source-bulk junction	0, 1
				Avalanche and Breakdown Parameters			
38	**VBRBOT**	V	10	0.1	–	Breakdown voltage of bottom component for source-bulk junction	0, 1
39	**VBRSTI**	V	10	0.1	–	Breakdown voltage of STI-edge component for source-bulk junction	0, 1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
40	**VBRGAT**	V	10	0.1	–	Breakdown voltage of gate-edge component for source-bulk junction	0, 1
41	**PBRBOT**	V	4	0.1	–	Breakdown onset tuning parameter of bottom component for source-bulk junction	0, 1
42	**PBRSTI**	V	4	0.1	–	Breakdown onset tuning parameter of STI-edge component for source-bulk junction	0, 1
43	**PBRGAT**	V	4	0.1	–	Breakdown onset tuning parameter of gate-edge component for source-bulk junction	0, 1
				JUNCAP Express Parameters			
44	**VJUNREF**	V	2.5	0.5	–	Typical maximum source-bulk junction voltage; usually about $2 \cdot V_{\mathrm{sup}}$	0, 1
45	**FJUNQ**	V	0.03	0	–	Fraction below which source-bulk junction capacitance components are neglected	0, 1
				Capacitance Parameters			
46	**CJORBOTD**	F/m^2	10^{-3}	10^{-12}	–	Zero-bias capacitance per unit-of-area of bottom component for drain-bulk junction	1
47	**CJORSTID**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of STI-edge component for drain-bulk junction	1
48	**CJORGATD**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of gate-edge component for drain-bulk junction	1
49	**VBIRBOTD**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of bottom component for drain-bulk junction	1
50	**VBIRSTID**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of STI-edge component for drain-bulk junction	1
51	**VBIRGATD**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of gate-edge component for drain-bulk junction	1
52	**PBOTD**	–	0.5	0.05	0.95	Grading coefficient of bottom component for drain-bulk junction	1
53	**PSTID**	–	0.5	0.05	0.95	Grading coefficient of STI-edge component for drain-bulk junction	1
54	**PGATD**	–	0.5	0.05	0.95	Grading coefficient of gate-edge component for drain-bulk junction	1
				Ideal-current Parameters			

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
55	**PHIGBOTD**	V	1.16	–	–	Zero-temperature bandgap voltage of bottom component for drain-bulk junction	1
56	**PHIGSTID**	V	1.16	–	–	Zero-temperature bandgap voltage of STI-edge component for drain-bulk junction	1
57	**PHIGGATD**	V	1.16	–	–	Zero-temperature bandgap voltage of gate-edge component for drain-bulk junction	1
58	**IDSATRBOTD**	A/m^2	10^{-12}	0	–	Saturation current density at the reference temperature of bottom component for drain-bulk junction	1
59	**IDSATRSTID**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of STI-edge component for drain-bulk junction	1
60	**IDSATRGATD**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of gate-edge component for drain-bulk junction	1
				Shockley-Read-Hall Parameters			
61	**CSRHBOTD**	A/m^3	10^2	0	–	Shockley-Read-Hall prefactor of bottom component for drain-bulk junction	1
62	**CSRHSTID**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of STI-edge component for drain-bulk junction	1
63	**CSRHGATD**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of gate-edge component for drain-bulk junction	1
64	**XJUNSTID**	m	10^{-7}	10^{-9}	–	Junction depth of STI-edge component for drain-bulk junction	1
65	**XJUNGATD**	m	10^{-7}	10^{-9}	–	Junction depth of gate-edge component for drain-bulk junction	1
				Trap-assisted Tunneling Parameters			
66	**CTATBOTD**	A/m^3	10^2	0	–	Trap-assisted tunneling prefactor of bottom component for drain-bulk junction	1
67	**CTATSTID**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of STI-edge component for drain-bulk junction	1
68	**CTATGATD**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of gate-edge component for drain-bulk junction	1
69	**MEFFTATBOTD**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of bottom component for drain-bulk junction	1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
70	**MEFFTATSTID**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of STI-edge component for drain-bulk junction	1
71	**MEFFTATGATD**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of gate-edge component for drain-bulk junction	1
				Band-to-band Tunneling Parameters			
72	**CBBTBOTD**	AV^{-3}	10^{-12}	0	–	Band-to-band tunneling prefactor of bottom component for drain-bulk junction	1
73	**CBBTSTID**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of STI-edge component for drain-bulk junction	1
74	**CBBTGATD**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of gate-edge component for drain-bulk junction	1
75	**FBBTRBOTD**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of bottom component for drain-bulk junction	1
76	**FBBTRSTID**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of STI-edge component for drain-bulk junction	1
77	**FBBTRGATD**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of gate-edge component for drain-bulk junction	1
78	**STFBBTBOTD**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of bottom component for drain-bulk junction	1
79	**STFBBTSTID**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of STI-edge component for drain-bulk junction	1
80	**STFBBTGATD**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of gate-edge component for drain-bulk junction	1
				Avalanche and Breakdown Parameters			
81	**VBRBOTD**	V	10	0.1	–	Breakdown voltage of bottom component for drain-bulk junction	1
82	**VBRSTID**	V	10	0.1	–	Breakdown voltage of STI-edge component for drain-bulk junction	1
83	**VBRGATD**	V	10	0.1	–	Breakdown voltage of gate-edge component for drain-bulk junction	1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
84	**PBRBOTD**	V	4	0.1	–	Breakdown onset tuning parameter of bottom component for drain-bulk junction	1
85	**PBRSTID**	V	4	0.1	–	Breakdown onset tuning parameter of STI-edge component for drain-bulk junction	1
86	**PBRGATD**	V	4	0.1	–	Breakdown onset tuning parameter of gate-edge component for drain-bulk junction	1
				JUNCAP Express Parameters			
87	**VJUNREFD**	V	2.5	0.5	–	Typical maximum drain-bulk junction voltage; usually about $2 \cdot V_{\mathrm{sup}}$	1
88	**FJUNQD**	V	0.03	0	–	Fraction below which drain-bulk junction capacitance components are neglected	1

2.5.9 Parameters for parasitic resistances

The parameters in the following table are part of PSP's global and binning parameter sets.

No.	Name	Unit	Default	Min.	Max.	Description
0	**RGO**	Ω	0	–	–	Gate resistance R_{gate}
1	**RINT**	Ω/□	0	0	–	Contact resistance between silicide and ploy
2	**RVPOLY**	Ω/□	0	0	–	Vertical poly resistance
3	**RSHG**	Ω/□	0	0	–	Gate electrode diffusion sheet resistance
4	**DLSIL**	m	0	–	–	Silicide extension over the physical gate length
5	**RBULKO**	Ω	0	–	–	Bulk resistance R_{bulk}
6	**RWELLO**	Ω	0	–	–	Well resistance R_{well}
7	**RJUNSO**	Ω	0	–	–	Source-side bulk resistance R_{juns}
8	**RJUNDO**	Ω	0	–	–	Drain-side bulk resistance R_{jund}

The parameters in the following table are part of PSP's local parameter set.

No.	Name	Unit	Default	Min.	Max.	Description
0	**RG**	Ω	0	0	–	Gate resistance R_{gate}
1	**RBULK**	Ω	0	0	–	Bulk resistance R_{bulk}
2	**RWELL**	Ω	0	0	–	Well resistance R_{well}
3	**RJUNS**	Ω	0	0	–	Source-side bulk resistance R_{juns}
4	**RJUND**	Ω	0	0	–	Drain-side bulk resistance R_{jund}

2.5.10 Parameters for NQS

The parameters in the following table are part of PSP-NQS's global and binning parameter sets.

No.	Name	Unit	Default	Min.	Max.	Description
0	**SWNQS**	–	0	0	9	Switch for NQS effects / number of collocation points
1	**MUNQSO**	–	1	–	–	Relative mobility for NQS modeling

The parameters in the following table are part of PSP-NQS's local parameter set.

No.	Name	Unit	Default	Min.	Max.	Description
0	**SWNQS**	–	0	0	9	Switch for NQS effects / number of collocation points
1	**MUNQS**	–	1	0	–	Relative mobility for NQS modeling

Section 3

Geometry dependence and Other effects

3.1 Introduction

The physical geometry scaling rules of PSP (Section 3.2) have been developed to give a good description over the whole geometry range of CMOS technologies. As an alternative, the binning-rules can be used (Section 3.3) to allow for a more phenomenological geometry dependency. (Note that the user has to choose between the two options; the geometrical scaling rules and the binning scaling rules cannot be used at the same time.) In both cases, the result is a local parameter set (for a transistor of the specified L and W), which is fed into the local model.

Stress and well proximity effects are included in PSP. Use of the stress model (Section 3.5) and/or well proximity effect model (Section 3.6) leads to modification of some of the local parameters calculated from the geometrical or binning scaling rules.

3.2 Geometrical scaling rules

The physical scaling rules to calculate the local parameters from a global parameter set are given in this section.

Note: After calculation of the local parameters (and possible application of the stress equations in Section 3.5), clipping is applied according to Section 2.5.7.

Effective length and width

$$W_{\mathrm{f}} = \frac{W}{\mathbf{NF}} \tag{3.1}$$

$$L_{\mathrm{EN}} = 10^{-6} \tag{3.2}$$

$$W_{\mathrm{EN}} = 10^{-6} \tag{3.3}$$

$$\Delta L_{\mathrm{PS}} = \mathbf{LVARO} \cdot \left(1 + \mathbf{LVARL} \cdot \frac{L_{\mathrm{EN}}}{L}\right) \cdot \left(1 + \mathbf{LVARW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{f}}}\right) \tag{3.4}$$

$$\Delta W_{\mathrm{OD}} = \mathbf{WVARO} \cdot \left(1 + \mathbf{WVARL} \cdot \frac{L_{\mathrm{EN}}}{L}\right) \cdot \left(1 + \mathbf{WVARW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{f}}}\right) \tag{3.5}$$

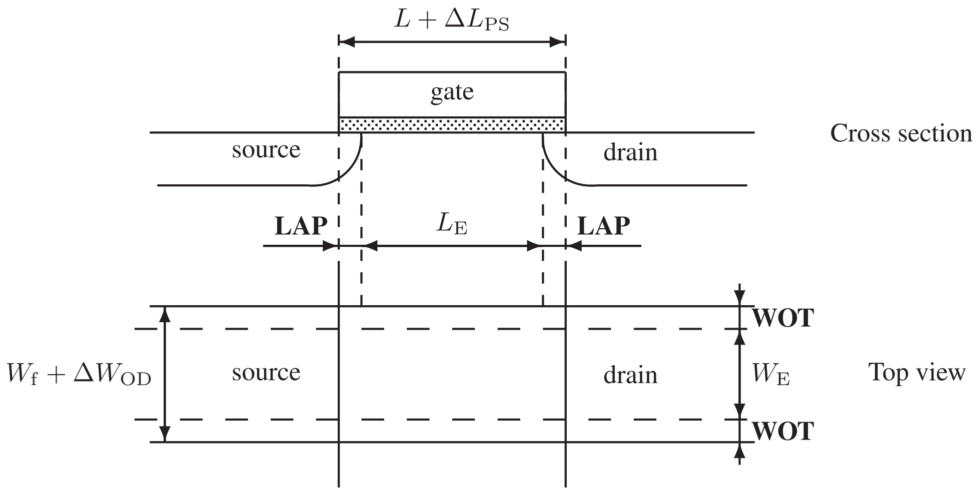

Figure 3.1: Specification of the dimensions of a MOS transistor

$$L_{\mathrm{E}} = L - \Delta L = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} \tag{3.6}$$

$$W_{\mathrm{E}} = W_{\mathrm{f}} - \Delta W = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} \tag{3.7}$$

$$L_{\mathrm{E,CV}} = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} + \mathbf{DLQ} \tag{3.8}$$

$$W_{\mathrm{E,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} + \mathbf{DWQ} \tag{3.9}$$

$$L_{\mathrm{G,CV}} = L + \Delta L_{\mathrm{PS}} + \mathbf{DLQ} \tag{3.10}$$

$$W_{\mathrm{G,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{DWQ} \tag{3.11}$$

Note: If the calculated L_{E}, W_{E}, $L_{\mathrm{E,CV}}$, $W_{\mathrm{E,CV}}$, $L_{\mathrm{G,CV}}$, or $W_{\mathrm{G,CV}}$ is smaller than 1 nm (10^{-9} m), the value is clipped to this lower bound of 1 nm.

Process Parameters

$$\mathbf{VFB} = \mathbf{VFBO} \cdot \left(1 + \mathbf{VFBL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{VFBW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{VFBLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.12}$$

$$\mathbf{STVFB} = \mathbf{STVFBO} \cdot \left(1 + \mathbf{STVFBL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{STVFBW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{STVFBLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.13}$$

$$\mathbf{TOX} = \mathbf{TOXO} \tag{3.14}$$

$$\mathbf{EPSROX} = \mathbf{EPSROXO} \tag{3.15}$$

$$N_{\mathrm{sub0,eff}} = \mathbf{NSUBO} \cdot \mathrm{MAX}\left(\left[1 + \mathbf{NSUBW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} \cdot \ln\left(1 + \frac{W_{\mathrm{E}}}{\mathbf{WSEG}}\right)\right], 10^{-3}\right) \tag{3.16}$$

$$N_{\mathrm{pck,eff}} = \mathbf{NPCK} \cdot \mathrm{MAX}\left(\left[1 + \mathbf{NPCKW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} \cdot \ln\left(1 + \frac{W_{\mathrm{E}}}{\mathbf{WSEGP}}\right)\right], 10^{-3}\right) \tag{3.17}$$

$$L_{\mathrm{pck,eff}} = \mathbf{LPCK} \cdot \mathrm{MAX}\left(\left[1 + \mathbf{LPCKW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} \cdot \ln\left(1 + \frac{W_{\mathrm{E}}}{\mathbf{WSEGP}}\right)\right], 10^{-3}\right) \tag{3.18}$$

$$a = 7.5 \cdot 10^{10} \tag{3.19}$$

$$b = \sqrt{N_{\mathrm{sub0,eff}} + 0.5 \cdot N_{\mathrm{pck,eff}}} - \sqrt{N_{\mathrm{sub0,eff}}} \tag{3.20}$$

$$N_{\mathrm{sub}} = \begin{cases} N_{\mathrm{sub0,eff}} + N_{\mathrm{pck,eff}} \cdot \left[2 - \dfrac{L_{\mathrm{E}}}{L_{\mathrm{pck,eff}}}\right] & \text{for } L_{\mathrm{E}} < L_{\mathrm{pck,eff}} \\[2ex] N_{\mathrm{sub0,eff}} + N_{\mathrm{pck,eff}} \cdot \dfrac{L_{\mathrm{pck,eff}}}{L_{\mathrm{E}}} & \text{for } L_{\mathrm{pck,eff}} \le L_{\mathrm{E}} \le 2 \cdot L_{\mathrm{pck,eff}} \\[2ex] \Bigg[\sqrt{N_{\mathrm{sub0,eff}}} + \\ \quad a \cdot \ln\left(1 + 2 \cdot \dfrac{L_{\mathrm{pck,eff}}}{L_{\mathrm{E}}} \cdot \left[\exp\left(\dfrac{b}{a}\right) - 1\right]\right)\Bigg]^2 & \text{for } L_{\mathrm{E}} > 2 \cdot L_{\mathrm{pck,eff}} \end{cases} \tag{3.21}$$

$$\mathbf{NEFF} = N_{\mathrm{sub}} \cdot \left(1 - \mathbf{FOL1} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} - \mathbf{FOL2} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^2\right) \tag{3.22}$$

$$\mathbf{VNSUB} = \mathbf{VNSUBO} \tag{3.23}$$

$$\mathbf{NSLP} = \mathbf{NSLPO} \tag{3.24}$$

$$\mathbf{DNSUB} = \mathbf{DNSUBO} \tag{3.25}$$

$$\mathbf{DPHIB} = \left(\mathbf{DPHIBO} + \mathbf{DPHIBL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{DPHIBLEXP}}\right) \cdot \left(1 + \mathbf{DPHIBW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{DPHIBLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.26}$$

$$\mathbf{NP} = \mathbf{NPO} \cdot \mathrm{MAX}\left(10^{-6}, 1 + \mathbf{NPL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \tag{3.27}$$

$$\mathbf{CT} = \left(\mathbf{CTO} + \mathbf{CTL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{CTLEXP}}\right) \cdot \left(1 + \mathbf{CTW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{CTLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.28}$$

$$\mathbf{TOXOV} = \mathbf{TOXOVO} \tag{3.29}$$

$$\mathbf{TOXOVD} = \mathbf{TOXOVDO} \tag{3.30}$$

$$\mathbf{NOV} = \mathbf{NOVO} \tag{3.31}$$

$$\mathbf{NOVD} = \mathbf{NOVDO} \tag{3.32}$$

DIBL Parameters

$$\mathbf{CF} = \mathbf{CFL} \cdot \left[\frac{L_\mathrm{EN}}{L_\mathrm{E}}\right]^{\mathbf{CFLEXP}} \cdot \left(1 + \mathbf{CFW} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}}\right) \tag{3.33}$$

$$\mathbf{CFB} = \mathbf{CFBO} \tag{3.34}$$

Mobility Parameters

$$F_{\beta 1,\mathrm{eff}} = \mathbf{FBET1} \cdot \left(1 + \mathbf{FBET1W} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}}\right) \tag{3.35}$$

$$L_{\mathrm{P1,eff}} = \mathbf{LP1} \cdot \mathrm{MAX}\left(\left[1 + \mathbf{LP1W} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}}\right], 10^{-3}\right) \tag{3.36}$$

$$\begin{aligned} G_\mathrm{P,E} = 1 + F_{\beta 1,\mathrm{eff}} \cdot \frac{L_\mathrm{P1,eff}}{L_\mathrm{E}} \cdot \left[1 - \exp\left(-\frac{L_\mathrm{E}}{L_\mathrm{P1,eff}}\right)\right] \\ + \mathbf{FBET2} \cdot \frac{\mathbf{LP2}}{L_\mathrm{E}} \cdot \left[1 - \exp\left(-\frac{L_\mathrm{E}}{\mathbf{LP2}}\right)\right] \end{aligned} \tag{3.37}$$

$$G_\mathrm{W,E} = 1 + \mathbf{BETW1} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{BETW2} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} \cdot \ln\left(1 + \frac{W_\mathrm{E}}{\mathbf{WBET}}\right) \tag{3.38}$$

$$\mathbf{BETN} = \frac{\mathbf{UO}}{G_\mathrm{P,E}} \cdot \frac{W_\mathrm{E}}{L_\mathrm{E}} \cdot G_\mathrm{W,E} \tag{3.39}$$

$$\begin{aligned} \mathbf{STBET} = \mathbf{STBETO} \cdot \left(1 + \mathbf{STBETL} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}}\right) \cdot \left(1 + \mathbf{STBETW} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}}\right) \\ \cdot \left(1 + \mathbf{STBETLW} \cdot \frac{W_\mathrm{EN} \cdot L_\mathrm{EN}}{W_\mathrm{E} \cdot L_\mathrm{E}}\right) \end{aligned}$$

$$\mathbf{MUE} = \mathbf{MUEO} \cdot \left[1 + \mathbf{MUEW} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}}\right] \tag{3.40}$$

$$\mathbf{STMUE} = \mathbf{STMUEO} \tag{3.41}$$

$$\mathbf{THEMU} = \mathbf{THEMUO} \tag{3.42}$$

$$\mathbf{STTHEMU} = \mathbf{STTHEMUO} \tag{3.43}$$

$$\mathbf{CS} = \left(\mathbf{CSO} + \mathbf{CSL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{CSLEXP}}\right) \cdot \left(1 + \mathbf{CSW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{CSLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.44}$$

$$\mathbf{STCS} = \mathbf{STCSO} \tag{3.45}$$

$$\mathbf{XCOR} = \mathbf{XCORO} \cdot \left(1 + \mathbf{XCORL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{XCORW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{XCORLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.46}$$

$$\mathbf{STXCOR} = \mathbf{STXCORO} \tag{3.47}$$

$$\mathbf{FETA} = \mathbf{FETAO} \tag{3.48}$$

Series Resistance Parameters

$$\mathbf{RS} = \mathbf{RSW1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} \cdot \left[1 + \mathbf{RSW2} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right] \tag{3.49}$$

$$\mathbf{STRS} = \mathbf{STRSO} \tag{3.50}$$

$$\mathbf{RSB} = \mathbf{RSBO} \tag{3.51}$$

$$\mathbf{RSG} = \mathbf{RSGO} \tag{3.52}$$

Velocity Saturation Parameters

$$\mathbf{THESAT} = \left(\mathbf{THESATO} + \mathbf{THESATL} \cdot \frac{G_{\mathrm{W,E}}}{G_{\mathrm{P,E}}} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{THESATLEXP}}\right) \cdot \left(1 + \mathbf{THESATW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{THESATLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.53}$$

$$\mathbf{STTHESAT} = \mathbf{STTHESATO} \cdot \left(1 + \mathbf{STTHESATL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{STTHESATW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{STTHESATLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.54}$$

$$\mathbf{THESATB} = \mathbf{THESATBO} \tag{3.55}$$

$$\mathbf{THESATG} = \mathbf{THESATGO} \tag{3.56}$$

Saturation Voltage Parameter

$$\mathbf{AX} = \frac{\mathbf{AXO}}{1 + \mathbf{AXL} \cdot \dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}} \tag{3.57}$$

Channel Length Modulation (CLM) Parameters

$$\mathbf{ALP} = \mathbf{ALPL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALPLEXP}} \cdot \left(1 + \mathbf{ALPW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.58}$$

$$\mathbf{ALP1} = \frac{\mathbf{ALP1L1} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP1LEXP}}}{1 + \mathbf{ALP1L2} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP1LEXP}+1}} \cdot \left(1 + \mathbf{ALP1W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.59}$$

$$\mathbf{ALP2} = \frac{\mathbf{ALP2L1} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP2LEXP}}}{1 + \mathbf{ALP2L2} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP2LEXP}+1}} \cdot \left(1 + \mathbf{ALP2W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.60}$$

$$\mathbf{VP} = \mathbf{VPO} \tag{3.61}$$

Impact Ionization (II) Parameters

$$\mathbf{A1} = \mathbf{A1O} \cdot \left(1 + \mathbf{A1L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A1W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.62}$$

$$\mathbf{A2} = \mathbf{A2O} \tag{3.63}$$

$$\mathbf{STA2} = \mathbf{STA2O} \tag{3.64}$$

$$\mathbf{A3} = \mathbf{A3O} \cdot \left(1 + \mathbf{A3L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A3W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.65}$$

$$\mathbf{A4} = \mathbf{A4O} \cdot \left(1 + \mathbf{A4L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A4W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.66}$$

Gate Current Parameters

$$\mathbf{GCO} = \mathbf{GCOO} \tag{3.67}$$

$$\mathbf{IGINV} = \mathbf{IGINVLW} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.68}$$

$$\mathbf{IGOV} = \mathbf{IGOVW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOV}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.69}$$

$$\mathbf{IGOVD} = \mathbf{IGOVDW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOVD}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.70}$$

$$\mathbf{STIG} = \mathbf{STIGO} \tag{3.71}$$

$$\mathbf{GC2} = \mathbf{GC2O} \tag{3.72}$$

$$\mathbf{GC3} = \mathbf{GC3O} \tag{3.73}$$

$$\mathbf{CHIB} = \mathbf{CHIBO} \tag{3.74}$$

Gate-Induced Drain Leakage (GIDL) Parameters

$$\mathbf{AGIDL} = \mathbf{AGIDLW} \cdot \frac{W_\mathrm{E} \cdot \mathbf{LOV}}{W_\mathrm{EN} \cdot L_\mathrm{EN}} \tag{3.75}$$

$$\mathbf{AGIDLD} = \mathbf{AGIDLDW} \cdot \frac{W_\mathrm{E} \cdot \mathbf{LOVD}}{W_\mathrm{EN} \cdot L_\mathrm{EN}} \tag{3.76}$$

$$\mathbf{BGIDL} = \mathbf{BGIDLO} \tag{3.77}$$

$$\mathbf{BGIDLD} = \mathbf{BGIDLDO} \tag{3.78}$$

$$\mathbf{STBGIDL} = \mathbf{STBGIDLO} \tag{3.79}$$

$$\mathbf{STBGIDLD} = \mathbf{STBGIDLDO} \tag{3.80}$$

$$\mathbf{CGIDL} = \mathbf{CGIDLO} \tag{3.81}$$

$$\mathbf{CGIDLD} = \mathbf{CGIDLDO} \tag{3.82}$$

Charge Model Parameters

$$\epsilon_\mathrm{ox} = \epsilon_0 \cdot \mathbf{EPSROX} \tag{3.83}$$

$$\mathbf{COX} = \epsilon_\mathrm{ox} \cdot \frac{W_\mathrm{E,CV} \cdot L_\mathrm{E,CV}}{\mathbf{TOX}} \tag{3.84}$$

$$\mathbf{CGOV} = \epsilon_\mathrm{ox} \cdot \frac{W_\mathrm{E,CV} \cdot \mathbf{LOV}}{\mathbf{TOXOV}} \tag{3.85}$$

$$\mathbf{CGOVD} = \epsilon_\mathrm{ox} \cdot \frac{W_\mathrm{E,CV} \cdot \mathbf{LOVD}}{\mathbf{TOXOVD}} \tag{3.86}$$

$$\mathbf{CGBOV} = \mathbf{CGBOVL} \cdot \frac{L_\mathrm{G,CV}}{L_\mathrm{EN}} \tag{3.87}$$

$$\mathbf{CFR} = \mathbf{CFRW} \cdot \frac{W_\mathrm{G,CV}}{W_\mathrm{EN}} \tag{3.88}$$

$$\mathbf{CFRD} = \mathbf{CFRDW} \cdot \frac{W_\mathrm{G,CV}}{W_\mathrm{EN}} \tag{3.89}$$

Thermal Noise Model Parameters

Note that the equation below makes use of the value of **BETN** calculated in Eq. (3.39). Because **BETN** is roughly proportional to $W_\mathrm{E}/L_\mathrm{E}$, the resulting **FNTEXC** is roughly proportional to $1/L_\mathrm{E}^2$. In addition, it will inherit some minor L- and W-dependence from **BETN**.

$$\mathbf{FNTEXC} = \mathbf{FNTEXCL} \cdot \mathbf{BETN}^2 \cdot \left[\frac{W_\mathrm{EN}}{W_\mathrm{E}}\right]^2 \tag{3.90}$$

Flicker Noise Model Parameters

$$L_\mathrm{noi} = \mathrm{MAX}\left(1 - \frac{2 \cdot \mathbf{LINTNOI}}{L_\mathrm{E}}, 10^{-3}\right) \tag{3.91}$$

$$L_\mathrm{red} = \frac{1}{L_\mathrm{noi}^{\mathbf{ALPNOI}}} \tag{3.92}$$

$$\mathbf{NFA} = L_\mathrm{red} \cdot \mathbf{NFALW} \cdot \frac{W_\mathrm{EN} \cdot L_\mathrm{EN}}{W_\mathrm{E} \cdot L_\mathrm{E}} \tag{3.93}$$

$$\mathbf{NFB} = L_\mathrm{red} \cdot \mathbf{NFBLW} \cdot \frac{W_\mathrm{EN} \cdot L_\mathrm{EN}}{W_\mathrm{E} \cdot L_\mathrm{E}} \tag{3.94}$$

$$\mathbf{NFC} = L_\mathrm{red} \cdot \mathbf{NFCLW} \cdot \frac{W_\mathrm{EN} \cdot L_\mathrm{EN}}{W_\mathrm{E} \cdot L_\mathrm{E}} \tag{3.95}$$

$$\mathbf{EF} = \mathbf{EFO} \tag{3.96}$$

WPE parameters

$$K_\mathrm{vthowe} = \mathbf{KVTHOWEO} + \mathbf{KVTHOWEL} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{KVTHOWEW} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{KVTHOWELW} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.97}$$

$$K_\mathrm{uowe} = \mathbf{KUOWEO} + \mathbf{KUOWEL} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{KUOWEW} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{KUOWELW} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.98}$$

3.3 Binning equations

The binning equations are provided as a (phenomenological) alternative to the physical scaling equations for computing local parameters. The physical geometrical scaling rules have been developed to give a good description over the whole geometry range of CMOS technologies. For processes under development, however, it is sometimes useful to have more flexible scaling relations. In that case on could opt for a binning strategy, where the accuracy with geometry is mostly determined by the number of bins used. The physical scaling rules of Section 3.2 are generally not suitable for binning strategies, since they may result in discontinuities in local parameter values at the bin boundaries. Consequently, special binning geometrical scaling relations have been developed, which guarantee continuity of the resulting local model parameters at the bin boundaries.

Only four different types of binning scaling rules are used, which are based on first order developments of the geometrical scaling rules in terms of L_E, $1/L_\mathrm{E}$, W_E, and $1/W_\mathrm{E}$ (examples below are for a fictitious parameter **YYY**):

1. Type I

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWYYY} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWYYY} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.99}$$

2. Type II

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_\mathrm{E}}{L_\mathrm{EN}} + \mathbf{PWYYY} \cdot \frac{W_\mathrm{E}}{W_\mathrm{EN}} + \mathbf{PLWYYY} \cdot \frac{L_\mathrm{E} \cdot W_\mathrm{E}}{L_\mathrm{EN} \cdot W_\mathrm{EN}} \tag{3.100}$$

3. Type III

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWYYY} \cdot \frac{W_\mathrm{E}}{W_\mathrm{EN}} + \mathbf{PLWYYY} \cdot \frac{W_\mathrm{E} \cdot L_\mathrm{EN}}{W_\mathrm{EN} \cdot L_\mathrm{E}} \tag{3.101}$$

4. Type IV (no binning)

$$\mathbf{YYY} = \mathbf{POYYY} \tag{3.102}$$

In Table 3.1 a survey of the binning type used for each local parameter is given. In some cases where the geometrical scaling rule is constant, the binning rule is chosen to be more flexible.

When using the binning rules above, the binning parameters for one bin can be directly calculated from the local parameter sets of the four corner devices of the bin (see Sec. 7.6). This results in a *separate parameter set for each bin*. The binning scheme ensures that the local parameters are exactly reproduced at the bin corners and that no humps occur in the local parameter values across bin boundaries.

Note: After calculation of the local parameters from the binning rules (and possible application of the stress equations in Section 3.5), clipping is applied according to Section 2.5.7.

Table 3.1: Overview of local parameters and binning type. The third column indicates whether there is a physical geometrical scaling rule for the local parameters.

#	parameter	physical scaling	binning	#	parameter	physical scaling	binning
0	**LEVEL**	no	no	42	**STTHESAT**	yes	type I
1	**TYPE**	no	no	43	**THESATB**	no	type I
2	**TR**	no	no	44	**THESATG**	no	type I
3	**SWIGATE**	no	no	45	**AX**	yes	type I
4	**SWIMPACT**	no	no	46	**ALP**	yes	type I
5	**SWGIDL**	no	no	47	**ALP1**	yes	type I
6	**SWJUNCAP**	no	no	48	**ALP2**	yes	type I
7	**SWJUNASYM**	no	no	49	**VP**	no	no
8	**QMC**	no	no	50	**A1**	yes	type I
9	**VFB**	yes	type I	51	**A2**	no	no
10	**STVFB**	yes	type I	52	**STA2**	no	no
11	**TOX**	no	no	53	**A3**	yes	type I
12	**EPSROX**	no	no	54	**A4**	yes	type I
13	**NEFF**	yes	type I	55	**GCO**	no	no
14	**VNSUB**	no	no	56	**IGINV**	yes	type II
15	**NSLP**	no	no	57	**IGOV**	yes	type III
16	**DNSUB**	no	no	58	**IGOVD**	yes	type III
17	**DPHIB**	yes	type I	59	**STIG**	no	no
18	**NP**	yes	type I	60	**GC2**	no	no
19	**CT**	yes	type I	61	**GC3**	no	no
20	**TOXOV**	no	no	62	**CHIB**	no	no
21	**TOXOVD**	no	no	63	**AGIDL**	yes	type III
22	**NOV**	no	type I	64	**AGIDLD**	yes	type III
23	**NOVD**	no	type I	65	**BGIDL**	no	no
24	**CF**	yes	type I	66	**BGIDLD**	no	no
25	**CFB**	no	no	67	**STBGIDL**	no	no
26	**BETN**	yes	type III	68	**STBGIDLD**	no	no
27	**STBET**	yes	type I	69	**CGIDL**	no	no
28	**MUE**	yes	type I	70	**CGIDLD**	no	no
29	**STMUE**	no	no	71	**COX**	yes	type II
30	**THEMU**	no	no	72	**CGOV**	yes	type III
31	**STTHEMU**	no	no	73	**CGOVD**	yes	type III
32	**CS**	yes	type I	74	**CGBOV**	yes	type II
33	**STCS**	no	no	75	**CFR**	yes	type III
34	**XCOR**	yes	type I	76	**CFRD**	yes	type III
35	**STXCOR**	no	no	77	**FNT**	no	no
36	**FETA**	no	no	78	**FNTEXC**	yes	type I
37	**RS**	yes	type I	79	**NFA**	yes	type I
38	**STRS**	no	no	80	**NFB**	yes	type I
39	**RSB**	no	no	81	**NFC**	yes	type I
40	**RSG**	no	no	82	**EF**	no	no
41	**THESAT**	yes	type I	83	**DTA**	no	no

Effective length and width

$$L_{\mathrm{EN}} = 10^{-6} \tag{3.103}$$

$$W_{\mathrm{EN}} = 10^{-6} \tag{3.104}$$

$$\Delta L_{\mathrm{PS}} = \mathbf{LVARO} \cdot \left(1 + \mathbf{LVARL} \cdot \frac{L_{\mathrm{EN}}}{L}\right) \tag{3.105}$$

$$\Delta W_{\mathrm{OD}} = \mathbf{WVARO} \cdot \left(1 + \mathbf{WVARW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{f}}}\right) \tag{3.106}$$

$$L_{\mathrm{E}} = L - \Delta L = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} \tag{3.107}$$

$$W_{\mathrm{E}} = W_{\mathrm{f}} - \Delta W = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} \tag{3.108}$$

$$L_{\mathrm{E,CV}} = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} + \mathbf{DLQ} \tag{3.109}$$

$$W_{\mathrm{E,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} + \mathbf{DWQ} \tag{3.110}$$

$$L_{\mathrm{G,CV}} = L + \Delta L_{\mathrm{PS}} + \mathbf{DLQ} \tag{3.111}$$

$$W_{\mathrm{G,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{DWQ} \tag{3.112}$$

Note: If the calculated L_{E}, W_{E}, $L_{\mathrm{E,CV}}$, $W_{\mathrm{E,CV}}$, $L_{\mathrm{G,CV}}$, or $W_{\mathrm{G,CV}}$ is smaller than 1 nm (10^{-9} m), the value is clipped to this lower bound of 1 nm.

Process Parameters

$$\mathbf{VFB} = \mathbf{POVFB} + \mathbf{PLVFB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWVFB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWVFB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.113}$$

$$\mathbf{STVFB} = \mathbf{POSTVFB} + \mathbf{PLSTVFB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWSTVFB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWSTVFB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.114}$$

$$\mathbf{TOX} = \mathbf{POTOX} \tag{3.115}$$

$$\mathbf{EPSROX} = \mathbf{POEPSROX} \tag{3.116}$$

$$\mathbf{NEFF} = \mathbf{PONEFF} + \mathbf{PLNEFF} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNEFF} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNEFF} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.117}$$

$$\mathbf{VNSUB} = \mathbf{POVNSUB} \tag{3.118}$$

$$\mathbf{NSLP} = \mathbf{PONSLP} \tag{3.119}$$

$$\mathbf{DNSUB} = \mathbf{PODNSUB} \tag{3.120}$$

$$\mathbf{DPHIB} = \mathbf{PODPHIB} + \mathbf{PLDPHIB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWDPHIB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWDPHIB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.121}$$

$$\mathbf{NP} = \mathbf{PONP} + \mathbf{PLNP} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNP} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNP} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.122}$$

$$\mathbf{CT} = \mathbf{POCT} + \mathbf{PLCT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWCT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWCT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.123}$$

$$\mathbf{TOXOV} = \mathbf{POTOXOV} \tag{3.124}$$

$$\mathbf{TOXOVD} = \mathbf{POTOXOVD} \tag{3.125}$$

$$\mathbf{NOV} = \mathbf{PONOV} + \mathbf{PLNOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNOV} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNOV} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.126}$$

$$\mathbf{NOVD} = \mathbf{PONOVD} + \mathbf{PLNOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNOVD} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNOVD} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.127}$$

DIBL Parameters

$$\mathbf{CF} = \mathbf{POCF} + \mathbf{PLCF} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWCF} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWCF} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.128}$$

$$\mathbf{CFB} = \mathbf{POCFB} \tag{3.129}$$

Mobility Parameters

$$\mathbf{BETN} = \mathbf{POBETN} + \mathbf{PLBETN} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWBETN} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWBETN} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \tag{3.130}$$

$$\mathbf{STBET} = \mathbf{POSTBET} + \mathbf{PLSTBET} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWSTBET} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWSTBET} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.131}$$

$$\mathbf{MUE} = \mathbf{POMUE} + \mathbf{PLMUE} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWMUE} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWMUE} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.132}$$

$$\mathbf{STMUE} = \mathbf{POSTMUE} \tag{3.133}$$

$$\mathbf{THEMU} = \mathbf{POTHEMU} \tag{3.134}$$

$$\mathbf{STTHEMU} = \mathbf{POSTTHEMU} \tag{3.135}$$

$$\mathbf{CS} = \mathbf{POCS} + \mathbf{PLCS} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWCS} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWCS} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.136}$$

$$\mathbf{STCS} = \mathbf{POSTCS} \tag{3.137}$$

$$\mathbf{XCOR} = \mathbf{POXCOR} + \mathbf{PLXCOR} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWXCOR} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWXCOR} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.138}$$

$$\mathbf{STXCOR} = \mathbf{POSTXCOR} \tag{3.139}$$

$$\mathbf{FETA} = \mathbf{POFETA} \tag{3.140}$$

Series Resistance Parameters

$$\mathbf{RS} = \mathbf{PORS} + \mathbf{PLRS} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWRS} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWRS} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.141}$$

$$\mathbf{STRS} = \mathbf{POSTRS} \tag{3.142}$$

$$\mathbf{RSB} = \mathbf{PORSB} \tag{3.143}$$

$$\mathbf{RSG} = \mathbf{PORSG} \tag{3.144}$$

Velocity Saturation Parameters

$$\begin{aligned}\mathbf{THESAT} = \mathbf{POTHESAT} + \mathbf{PLTHESAT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} \\ + \mathbf{PWTHESAT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESAT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}\end{aligned} \tag{3.145}$$

$$\begin{aligned}\mathbf{STTHESAT} = \mathbf{POSTTHESAT} + \mathbf{PLSTTHESAT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} \\ + \mathbf{PWSTTHESAT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWSTTHESAT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}\end{aligned} \tag{3.146}$$

$$\begin{aligned}\mathbf{THESATB} = \mathbf{POTHESATB} + \mathbf{PLTHESATB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} \\ + \mathbf{PWTHESATB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESATB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}\end{aligned} \tag{3.147}$$

$$\begin{aligned}\mathbf{THESATG} = \mathbf{POTHESATG} + \mathbf{PLTHESATG} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} \\ + \mathbf{PWTHESATG} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESATG} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}\end{aligned} \tag{3.148}$$

Saturation Voltage Parameters

$$\mathbf{AX} = \mathbf{POAX} + \mathbf{PLAX} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAX} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWAX} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.149}$$

Channel Length Modulation (CLM) Parameters

$$\mathbf{ALP} = \mathbf{POALP} + \mathbf{PLALP} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.150}$$

$$\mathbf{ALP1} = \mathbf{POALP1} + \mathbf{PLALP1} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP1} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.151}$$

$$\mathbf{ALP2} = \mathbf{POALP2} + \mathbf{PLALP2} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP2} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP2} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.152}$$

$$\mathbf{VP} = \mathbf{POVP} \tag{3.153}$$

Impact Ionization (II) Parameters

$$\mathbf{A1} = \mathbf{POA1} + \mathbf{PLA1} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA1} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.154}$$

$$\mathbf{A2} = \mathbf{POA2} \tag{3.155}$$

$$\mathbf{STA2} = \mathbf{POSTA2} \tag{3.156}$$

$$\mathbf{A3} = \mathbf{POA3} + \mathbf{PLA3} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA3} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA3} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.157}$$

$$\mathbf{A4} = \mathbf{POA4} + \mathbf{PLA4} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA4} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA4} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.158}$$

Gate Current Parameters

$$\mathbf{GCO} = \mathbf{POGCO} \tag{3.159}$$

$$\mathbf{IGINV} = \mathbf{POIGINV} + \mathbf{PLIGINV} \cdot \frac{L_{\mathrm{E}}}{L_{\mathrm{EN}}} + \mathbf{PWIGINV} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGINV} \cdot \frac{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \tag{3.160}$$

$$\mathbf{IGOV} = \mathbf{POIGOV} + \mathbf{PLIGOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWIGOV} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGOV} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \tag{3.161}$$

$$\mathbf{IGOVD} = \mathbf{POIGOVD} + \mathbf{PLIGOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWIGOVD} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGOVD} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \tag{3.162}$$

$$\mathbf{STIG} = \mathbf{POSTIG} \tag{3.163}$$

$$\mathbf{GC2} = \mathbf{POGC2} \tag{3.164}$$

$$\mathbf{GC3} = \mathbf{POGC3} \tag{3.165}$$

$$\mathbf{CHIB} = \mathbf{POCHIB} \tag{3.166}$$

Gate-Induced Drain Leakage (GIDL) Parameters

$$\mathbf{AGIDL} = \mathbf{POAGIDL} + \mathbf{PLAGIDL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAGIDL} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWAGIDL} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \tag{3.167}$$

$$\mathbf{AGIDLD} = \mathbf{POAGIDLD} + \mathbf{PLAGIDLD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAGIDLD} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWAGIDLD} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \tag{3.168}$$

$$\mathbf{BGIDL} = \mathbf{POBGIDL} \tag{3.169}$$

$$\mathbf{BGIDLD} = \mathbf{POBGIDLD} \tag{3.170}$$

$$\mathbf{STBGIDL} = \mathbf{POSTBGIDL} \tag{3.171}$$

$$\mathbf{STBGIDLD} = \mathbf{POSTBGIDLD} \tag{3.172}$$

$$\mathbf{CGIDL} = \mathbf{POCGIDL} \tag{3.173}$$

$$\mathbf{CGIDLD} = \mathbf{POCGIDLD} \tag{3.174}$$

Charge Model Parameters

$$\textbf{COX} = \textbf{POCOX} + \textbf{PLCOX} \cdot \frac{L_{\mathrm{E,CV}}}{L_{\mathrm{EN}}} + \textbf{PWCOX} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCOX} \cdot \frac{L_{\mathrm{E,CV}} \cdot W_{\mathrm{E,CV}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \tag{3.175}$$

$$\textbf{CGOV} = \textbf{POCGOV} + \textbf{PLCGOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E,CV}}} + \textbf{PWCGOV} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCGOV} \cdot \frac{W_{\mathrm{E,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E,CV}}} \tag{3.176}$$

$$\textbf{CGOVD} = \textbf{POCGOVD} + \textbf{PLCGOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E,CV}}} + \textbf{PWCGOVD} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCGOVD} \cdot \frac{W_{\mathrm{E,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E,CV}}} \tag{3.177}$$

$$\textbf{CGBOV} = \textbf{POCGBOV} + \textbf{PLCGBOV} \cdot \frac{L_{\mathrm{G,CV}}}{L_{\mathrm{EN}}} + \textbf{PWCGBOV} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCGBOV} \cdot \frac{L_{\mathrm{G,CV}} \cdot W_{\mathrm{G,CV}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \tag{3.178}$$

$$\textbf{CFR} = \textbf{POCFR} + \textbf{PLCFR} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{G,CV}}} + \textbf{PWCFR} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCFR} \cdot \frac{W_{\mathrm{G,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{G,CV}}} \tag{3.179}$$

$$\textbf{CFRD} = \textbf{POCFRD} + \textbf{PLCFRD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{G,CV}}} + \textbf{PWCFRD} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \textbf{PLWCFRD} \cdot \frac{W_{\mathrm{G,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{G,CV}}} \tag{3.180}$$

Thermal Noise Model Parameters

$$\textbf{FNT} = \textbf{POFNT} \tag{3.181}$$

$$\textbf{FNTEXC} = \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^2 \cdot \left(\textbf{POFNTEXC} + \textbf{PLFNTEXC} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \textbf{PWFNTEXC} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \textbf{PLWFNTEXC} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}\right) \tag{3.182}$$

Flicker Noise Model Parameters

$$\textbf{NFA} = \textbf{PONFA} + \textbf{PLNFA} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \textbf{PWNFA} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \textbf{PLWNFA} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.183}$$

$$\textbf{NFB} = \textbf{PONFB} + \textbf{PLNFB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \textbf{PWNFB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \textbf{PLWNFB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.184}$$

$$\textbf{NFC} = \textbf{PONFC} + \textbf{PLNFC} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \textbf{PWNFC} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \textbf{PLWNFC} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.185}$$

$$\textbf{EF} = \textbf{POEF} \tag{3.186}$$

WPE parameters

$$K_{\mathrm{vthowe}} = \mathbf{POKVTHOWE} + \mathbf{PLKVTHOWE} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWKVTHOWE} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWKVTHOWE} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.187)$$

$$K_{\mathrm{uowe}} = \mathbf{POKUOWE} + \mathbf{PLKUOWE} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWKUOWE} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWKUOWE} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.188)$$

3.4 Parasitic resistances

PSP model contains a network of parasitic elements: a gate resistance and four bulk resistances. Note that the junction diodes are no longer directly connected to the bulk terminal of the intrinsic MOS-transistor. The complete circuit is shown in Fig. 3.2. At this moment, only the gate resistance is scaled with geometry (facilitating the implementation of multi-finger devices).

$$L_\mathrm{f} = L + \Delta L_\mathrm{PS} \tag{3.189}$$

$$L_\mathrm{sil,f} = L_\mathrm{f} + \mathbf{DLSIL} \tag{3.190}$$

$$W_\mathrm{E,f} = W_\mathrm{f} + \Delta W_\mathrm{OD} \tag{3.191}$$

$$X_\mathrm{GWE} = \mathbf{XGW} - 0.5 \cdot \Delta W_\mathrm{OD} \tag{3.192}$$

$$\mathbf{RG} = \mathbf{RGO} + \frac{1}{\mathbf{NF}} \cdot \left[\frac{\mathbf{RSHG} \cdot \left(\frac{W_\mathrm{E,f}}{3 \cdot \mathbf{NGCON}} + X_\mathrm{GWE} \right)}{\mathbf{NGCON} \cdot L_\mathrm{sil,f}} + \frac{\mathbf{RINT} + \mathbf{RVPOLY}}{W_\mathrm{E,f} \cdot L_\mathrm{f}} \right] \tag{3.193}$$

$$\mathbf{RBULK} = \mathbf{RBULKO} \tag{3.194}$$

$$\mathbf{RWELL} = \mathbf{RWELLO} \tag{3.195}$$

$$\mathbf{RJUNS} = \mathbf{RJUNSO} \tag{3.196}$$

$$\mathbf{RJUND} = \mathbf{RJUNDO} \tag{3.197}$$

Note: The values of L_f, $L_\mathrm{sil,f}$, $W_\mathrm{E,f}$ and X_GWE are clipped to a minimum value of 1 nm. The calculated local parameters are subject to the boundaries specified in Section 2.5.9.

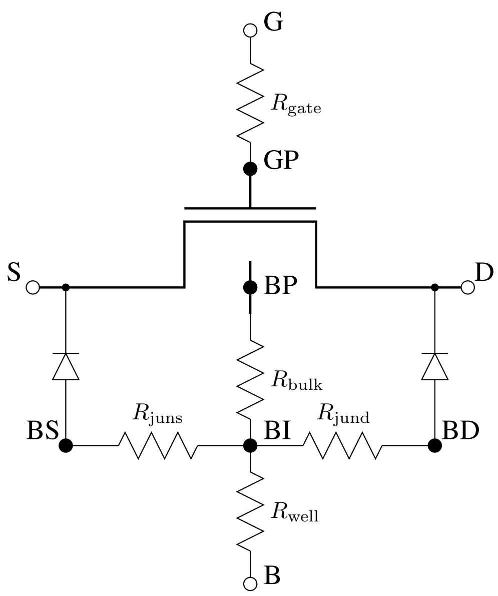

Figure 3.2: Parasitics circuit

3.5 Stress effects

The stress model of BSIM4.4.0 [3] has been adopted in PSP without any modifications, except for two changes: (1) in the original BSIM parameter names all zeros have been replaced by "O"s, in order to comply with PSP conventions and (2) the BSIM parameters *STK2* and *LODK2* are not available in PSP. Some trivial conversion of parameters BSIM→PSP is still necessary, see [2].

The local PSP parameters affected by the stress equations are **BETN**, **THESAT**, **VFB**, and **CF**.

Calculation of **SA** and **SB** for irregular layouts is given in Section B.1.

Note:

- After modification of the local parameters by the stress equations, clipping is applied according to Section 2.5.7.
- If both **SA** and **SB** are set to 0, the stress-equations are *not* computed.

3.5.1 Layout effects for multi-finger devices

For multi-finger devices, effective values $\mathbf{SA}_{\text{eff}}$ and $\mathbf{SB}_{\text{eff}}$ for the instance parameters are calculated (see Fig. 3.3).

$$\frac{1}{\mathbf{SA}_{\text{eff}} + 0.5 \cdot L} = \frac{1}{\mathbf{NF}} \cdot \sum_{i=0}^{\mathbf{NF}-1} \frac{1}{\mathbf{SA} + 0.5 \cdot L + i \cdot (\mathbf{SD} + L)} \tag{3.198}$$

$$\frac{1}{\mathbf{SB}_{\text{eff}} + 0.5 \cdot L} = \frac{1}{\mathbf{NF}} \cdot \sum_{i=0}^{\mathbf{NF}-1} \frac{1}{\mathbf{SB} + 0.5 \cdot L + i \cdot (\mathbf{SD} + L)} \tag{3.199}$$

3.5.2 Layout effects for regular shapes

$$R_{\text{A}} = \frac{1}{\mathbf{SA}_{\text{eff}} + 0.5 \cdot L} \tag{3.200}$$

$$R_{\text{B}} = \frac{1}{\mathbf{SB}_{\text{eff}} + 0.5 \cdot L} \tag{3.201}$$

$$R_{\text{A,ref}} = \frac{1}{\mathbf{SAREF} + 0.5 \cdot L} \tag{3.202}$$

$$R_{\text{B,ref}} = \frac{1}{\mathbf{SBREF} + 0.5 \cdot L} \tag{3.203}$$

3.5.3 Parameter modifications

Mobility-related equations

$$K_{\text{u0}} = \left(1 + \frac{\mathbf{LKUO}}{(L + \Delta L_{\text{PS}})^{\mathbf{LLODKUO}}} + \frac{\mathbf{WKUO}}{(W_{\text{f}} + \Delta W_{\text{OD}} + \mathbf{WLOD})^{\mathbf{WLODKUO}}} + \frac{\mathbf{PKUO}}{(L + \Delta L_{\text{PS}})^{\mathbf{LLODKUO}} \cdot (W_{\text{f}} + \Delta W_{\text{OD}} + \mathbf{WLOD})^{\mathbf{WLODKUO}}}\right) \cdot \left[1 + \mathbf{TKUO} \cdot \left(\frac{T_{\text{KD}}}{T_{\text{KR}}} - 1\right)\right] \tag{3.204}$$

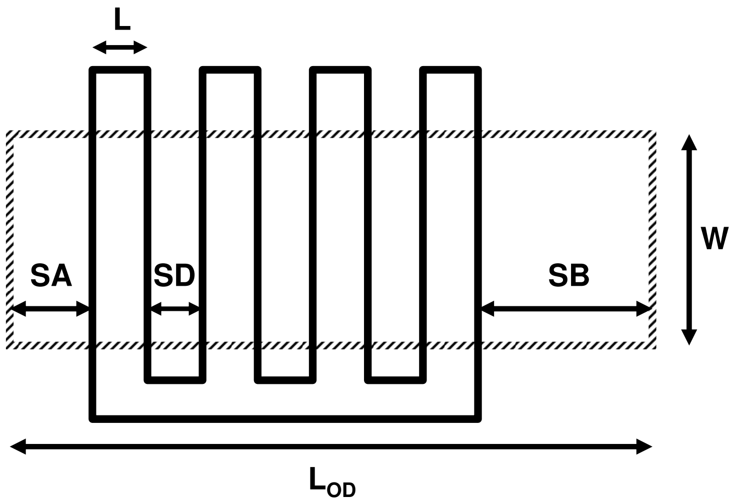

Figure 3.3: A typical layout of multi-finger devices with an additional instance parameters **SD**.

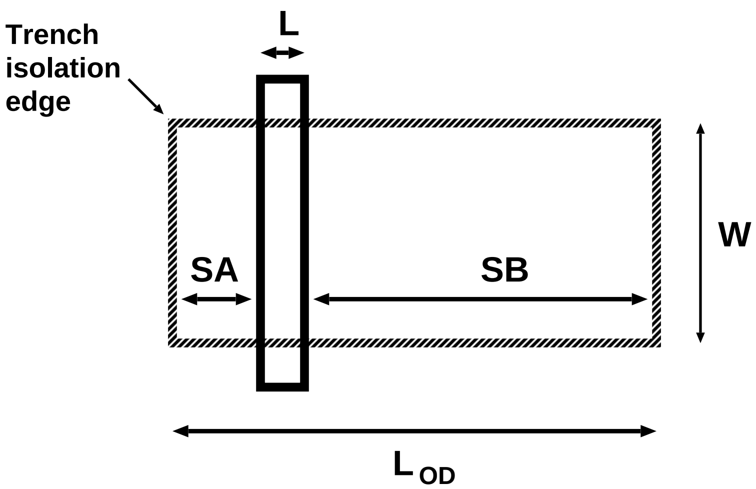

Figure 3.4: Typical layout of a MOSFET. Note that $L_{\rm OD} = \mathbf{SA} + \mathbf{SB} + L$, where OD is the active region definition.

$$\rho_\beta = \frac{\mathbf{KUO}}{K_{\mathrm{u0}}} \cdot (R_\mathrm{A} + R_\mathrm{B}) \tag{3.205}$$

$$\rho_{\beta,\mathrm{ref}} = \frac{\mathbf{KUO}}{K_{\mathrm{u0}}} \cdot (R_{\mathrm{A,ref}} + R_{\mathrm{B,ref}}) \tag{3.206}$$

$$\mathbf{BETN} = \frac{1+\rho_\beta}{1+\rho_{\beta,\mathrm{ref}}} \cdot \mathbf{BETN}_\mathrm{ref} \tag{3.207}$$

$$\mathbf{THESAT} = \frac{1+\rho_\beta}{1+\rho_{\beta,\mathrm{ref}}} \cdot \frac{1+\mathbf{KVSAT}\cdot\rho_{\beta,\mathrm{ref}}}{1+\mathbf{KVSAT}\cdot\rho_\beta} \cdot \mathbf{THESAT}_\mathrm{ref} \tag{3.208}$$

Threshold-voltage-related equations

$$K_{\mathrm{vth0}} = 1 + \frac{\mathbf{LKVTHO}}{(L+\Delta L_{\mathrm{PS}})^{\mathbf{LLODVTH}}} + \frac{\mathbf{WKVTHO}}{(W_\mathrm{f}+\Delta W_{\mathrm{OD}}+\mathbf{WLOD})^{\mathbf{WLODVTH}}} + \frac{\mathbf{PKVTHO}}{(L+\Delta L_{\mathrm{PS}})^{\mathbf{LLODVTH}}\cdot(W_\mathrm{f}+\Delta W_{\mathrm{OD}}+\mathbf{WLOD})^{\mathbf{WLODVTH}}} \tag{3.209}$$

$$\Delta R = R_\mathrm{A} + R_\mathrm{B} - R_{\mathrm{A,ref}} - R_{\mathrm{B,ref}} \tag{3.210}$$

$$\mathbf{VFB} = \mathbf{VFB}_\mathrm{ref} + \mathbf{KVTHO} \cdot \frac{\Delta R}{K_{\mathrm{vth0}}} \tag{3.211}$$

$$\mathbf{CF} = \mathbf{CF}_\mathrm{ref} + \mathbf{STETAO} \cdot \frac{\Delta R}{K_{\mathrm{vth0}}^{\mathbf{LODETAO}}} \tag{3.212}$$

3.6 Well proximity effects

The well proximity effect (WPE) model from BSIM4.5.0 [4, 5, 6] has been adopted in PSP with two changes relative to BSIM4.5.0: (1) in the original BSIM parameter names all zeros have been replaced by 'O's in order to comply with PSP naming convention and (2) the BSIM parameter *K2WE* is not available in PSP. Except for some trivial conversion of parameters BSIM→PSP [2], WPE parameters from BSIM can be used directly in PSP.

The local PSP parameters affected by the WPE equations are **VFB** and **BETN**.

How to calculate **SCA**, **SCB**, and **SCC** is shown in Section B.2.

Note:

- After modification of the local parameters by the WPE equations, clipping is applied according to Section 2.5.7.
- If **SCA**, **SCB**, **SCC** and **SC** are all set to 0, the WPE equations are *not* computed.

3.6.1 Parameters for pre-layout simulation

If **SCA** $=$ **SCB** $=$ **SCC** $= 0$ and **SC** > 0, **SCA**, **SCB**, and **SCC** will be computed from **SC** according to Eqs. (B.9)–(B.11), as shown below. Here, **SC** should be taken as the distance to the nearest well edge (see Fig. 3.5). If any of the parameters **SCA**, **SCB**, or **SCC** is positive, all three values as supplied will be used and **SC** will be ignored.

If **SCA** $=$ **SCB** $=$ **SCC** $= 0$ and **SC** > 0

$$\mathbf{SCA} = \frac{\mathbf{SCREF}^2}{W_\mathrm{f}} \cdot \left(\frac{1}{\mathbf{SC}} - \frac{1}{\mathbf{SC} + W_\mathrm{f}} \right) \tag{3.213}$$

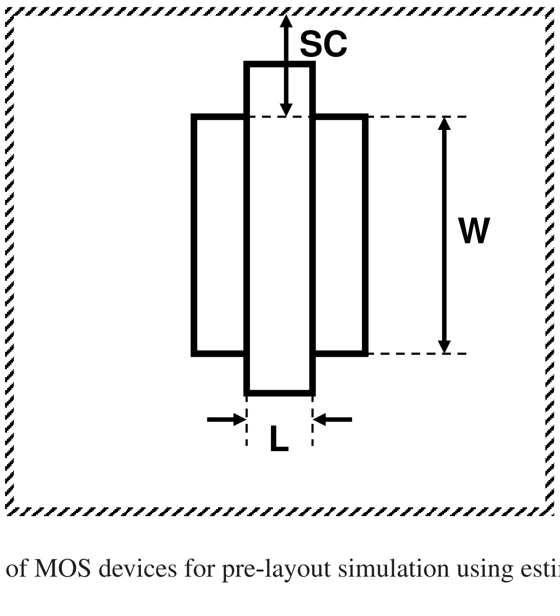

Figure 3.5: A layout of MOS devices for pre-layout simulation using estimated value for **SC**.

$$\mathbf{SCB} = \frac{1}{W_\mathrm{f} \cdot \mathbf{SCREF}} \cdot \left[\frac{\mathbf{SCREF}}{10} \cdot \mathbf{SC} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) + \frac{\mathbf{SCREF}^2}{100} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) \right.$$
$$- \frac{\mathbf{SCREF}}{10} \cdot (\mathbf{SC} + W_\mathrm{f}) \cdot \exp\left(-10 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right)$$
$$\left. - \frac{\mathbf{SCREF}^2}{100} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) \right] \quad (3.214)$$

$$\mathbf{SCC} = \frac{1}{W_\mathrm{f} \cdot \mathbf{SCREF}} \cdot \left[\frac{\mathbf{SCREF}}{20} \cdot \mathbf{SC} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) + \frac{\mathbf{SCREF}^2}{400} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) \right.$$
$$- \frac{\mathbf{SCREF}}{20} \cdot (\mathbf{SC} + W_\mathrm{f}) \cdot \exp\left(-20 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right)$$
$$\left. - \frac{\mathbf{SCREF}^2}{400} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) \right] \quad (3.215)$$

3.6.2 Calculation of parameter modifications

The calculation of K_vthowe and K_uowe is given in Section 3.2 (global model) or 3.3 (binning model).

$$\mathbf{VFB} = \mathbf{VFB}_\mathrm{ref} + K_\mathrm{vthowe} \cdot (\mathbf{SCA} + \mathbf{WEB} \cdot \mathbf{SCB} + \mathbf{WEC} \cdot \mathbf{SCC}) \quad (3.216)$$

$$\mathbf{BETN} = \mathbf{BETN}_\mathrm{ref} \cdot [1 + K_\mathrm{uowe} \cdot (\mathbf{SCA} + \mathbf{WEB} \cdot \mathbf{SCB} + \mathbf{WEC} \cdot \mathbf{SCC})] \quad (3.217)$$

3.7 Asymmetric junctions

From PSP 102.3 onwards, asymmetric junction can be modeled in PSP. This includes asymmetric source-bulk and drain-bulk junctions, GIDL/GISL, overlap gate currents, overlap capacitances and outer fringe capacitances. The asymmetric junction model can be switched on by means of the parameter **SWJUNASYM**. Note that if **SWJUNASYM** $= 1$, the new parameters for the drain side are used all together. Those whose values are not explicitly specified in the model card are set to their default value, *not* to their counterparts for the source side. In other words, it is not possible to activate the parameters for the drain side on a one-by-one basis. The physical scaling and binning rules to calculate the related local parameters for the drain side are given in Section 3.2 and 3.3.

If **SWJUNASYM** $= 0$, the related parameters for the drain side are ignored. Effectively, the following assignments are applied before evaluation of the calculations described in Section 4.

If **SWJUNASYM** $= 0$:

$$\mathbf{TOXOVD} = \mathbf{TOXOV} \tag{3.218}$$

$$\mathbf{NOVD} = \mathbf{NOV} \tag{3.219}$$

$$\mathbf{AGIDLD} = \mathbf{AGIDL} \tag{3.220}$$

$$\mathbf{BGIDLD} = \mathbf{BGIDL} \tag{3.221}$$

$$\mathbf{STBGIDLD} = \mathbf{STBGIDL} \tag{3.222}$$

$$\mathbf{CGIDLD} = \mathbf{CGIDL} \tag{3.223}$$

$$\mathbf{IGOVD} = \mathbf{IGOV} \tag{3.224}$$

$$\mathbf{CGOVD} = \mathbf{CGOV} \tag{3.225}$$

$$\mathbf{CFRD} = \mathbf{CFR} \tag{3.226}$$

Section 4

PSP Model Equations

4.1 Internal Parameters (including Temperature Scaling)

In this section, bias-independent internal parameters will be calculated, including temperature scaling. These parameters are computed from local parameters. Local parameters are (as usual) denoted by capital characters in bold font, whereas the internal parameters are denoted by symbols in bold font.

Transistor temperature

$$T_{\mathrm{KR}} = T_0 + \mathbf{TR} \tag{4.1}$$

$$T_{\mathrm{KD}} = T_0 + T_{\mathrm{A}} + \mathbf{DTA} \tag{4.2}$$

$$\Delta T = T_{\mathrm{KD}} - T_{\mathrm{KR}} \tag{4.3}$$

$$\boldsymbol{\phi}_{\mathbf{T}} = \frac{k_{\mathrm{B}} \cdot T_{\mathrm{KD}}}{q} \tag{4.4}$$

Local process parameters

$$\boldsymbol{\phi}^{*}_{\mathbf{T}} = \boldsymbol{\phi}_{\mathbf{T}} \cdot \left(1 + \mathbf{CT} \cdot \frac{T_{\mathrm{KR}}}{T_{\mathrm{KD}}}\right) \tag{4.5}$$

$$\boldsymbol{V}_{\mathbf{FB}} = \mathbf{VFB} + \mathbf{STVFB} \cdot \Delta T + \mathbf{DELVTO} \tag{4.6}$$

$$E_{\mathrm{g}}/q = 1.179 - 9.025 \cdot 10^{-5} \cdot T_{\mathrm{KD}} - 3.05 \cdot 10^{-7} \cdot {T_{\mathrm{KD}}}^2 \tag{4.7}$$

$$r_{\mathrm{T}} = \left(1.045 + 4.5 \cdot 10^{-4} \cdot T_{\mathrm{KD}}\right) \cdot \left(0.523 + 1.4 \cdot 10^{-3} \cdot T_{\mathrm{KD}} - 1.48 \cdot 10^{-6} \cdot {T_{\mathrm{KD}}}^2\right) \tag{4.8}$$

$$n_{\mathrm{i}} = 2.5 \cdot 10^{25} \cdot {r_{\mathrm{T}}}^{3/4} \cdot \left(T_{\mathrm{KD}}/300\right)^{3/2} \cdot \exp\left(-\frac{E_{\mathrm{g}}/q}{2 \cdot \boldsymbol{\phi}_{\mathbf{T}}}\right) \tag{4.9}$$

$$\phi_{\mathrm{B}}^{\mathrm{cl}} = \mathrm{MAX}\left(\mathbf{DPHIB} + 2 \cdot \boldsymbol{\phi}_{\mathbf{T}} \cdot \ln\left[\mathbf{NEFF}/n_{\mathrm{i}}\right],\, 0.05\right) \tag{4.10}$$

$$\epsilon_{\mathrm{ox}} = \mathbf{EPSROX} \cdot \epsilon_0 \tag{4.11}$$

$$C_{\mathrm{ox}} = \epsilon_{\mathrm{ox}}/\mathbf{TOX} \tag{4.12}$$

$$\epsilon_{\mathrm{Si}} = \epsilon_{\mathrm{r,Si}} \cdot \epsilon_0 \tag{4.13}$$

$$\gamma_0 = \sqrt{2 \cdot q \cdot \epsilon_{\mathrm{Si}} \cdot \mathbf{NEFF}}/C_{\mathrm{ox}} \tag{4.14}$$

$$G_0^{\mathrm{cl}} = \gamma_0/\sqrt{\boldsymbol{\phi}_{\mathbf{T}}} \tag{4.15}$$

Polysilicon depletion parameter

$$\boldsymbol{k_\mathrm{P}} = \begin{cases} \text{if } \mathbf{NP} = 0 & \left\{ \boldsymbol{k_\mathrm{P}} = 0 \right. \\ \text{if } \mathbf{NP} > 0 & \begin{cases} \mathrm{NP}_1 = \mathrm{MAX}(\mathbf{NP},\, 8 \cdot 10^7/\mathbf{TOX}^2) \\ \mathrm{NP}_2 = \mathrm{MAX}(\mathrm{NP}_1,\, 5 \cdot 10^{24}) \\ \boldsymbol{k_\mathrm{P}} = 2 \cdot \boldsymbol{\phi_\mathrm{T}} \cdot C_\mathrm{ox}^2/(q \cdot \epsilon_\mathrm{Si} \cdot \mathrm{NP}_2) \end{cases} \end{cases} \tag{4.16}$$

Quantum-mechanical correction parameters

$$\boldsymbol{q_\mathrm{lim}} = 10 \cdot \boldsymbol{\phi_\mathrm{T}} \tag{4.17}$$

$$\boldsymbol{q_\mathrm{q}} = \begin{cases} 0.4 \cdot \mathbf{QMC} \cdot QM_\mathrm{N} \cdot C_\mathrm{ox}^{2/3} & \text{for NMOS} \\ 0.4 \cdot \mathbf{QMC} \cdot QM_\mathrm{P} \cdot C_\mathrm{ox}^{2/3} & \text{for PMOS} \end{cases} \tag{4.18}$$

$$q_\mathrm{b0} = \gamma_0 \cdot \sqrt{\phi_\mathrm{B}^\mathrm{cl}} \tag{4.19}$$

$$\boldsymbol{\phi_\mathrm{B}} = \phi_\mathrm{B}^\mathrm{cl} + 0.75 \cdot \boldsymbol{q_\mathrm{q}} \cdot q_\mathrm{b0}^{2/3} \tag{4.20}$$

$$\boldsymbol{G_0} = G_0^\mathrm{cl} \cdot \left(1 + \boldsymbol{q_\mathrm{q}} \cdot q_\mathrm{b0}^{-1/3}\right) \tag{4.21}$$

V_SB-clipping parameters

$$\boldsymbol{\phi_\mathrm{X}} = 0.95 \cdot \boldsymbol{\phi_\mathrm{B}} \tag{4.22}$$

$$\boldsymbol{a_\phi} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi_\mathrm{B}^2} \tag{4.23}$$

$$\boldsymbol{b_\phi} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi_\mathrm{B}^2} \tag{4.24}$$

$$\boldsymbol{\phi_\mathrm{X}^\star} = 0.5 \cdot \sqrt{\boldsymbol{b_\phi}} \tag{4.25}$$

$$\boldsymbol{\phi_\mathrm{X}^*} = \mathrm{MINA}\left(\boldsymbol{\phi_\mathrm{X}} - \boldsymbol{\phi_\mathrm{X}^\star},\, 0,\, \boldsymbol{a_\phi}\right) \tag{4.26}$$

Local process parameters in gate overlap regions

$$\gamma_\mathrm{ov} = \sqrt{2 \cdot q \cdot \epsilon_\mathrm{Si} \cdot \mathbf{NOV}} \cdot \mathbf{TOXOV}/\epsilon_\mathrm{ox} \tag{4.27}$$

$$\gamma_\mathrm{dov} = \sqrt{2 \cdot q \cdot \epsilon_\mathrm{Si} \cdot \mathbf{NOVD}} \cdot \mathbf{TOXOVD}/\epsilon_\mathrm{ox} \tag{4.28}$$

$$\boldsymbol{G_\mathrm{ov}} = \gamma_\mathrm{ov}/\sqrt{\boldsymbol{\phi_\mathrm{T}}} \tag{4.29}$$

$$\boldsymbol{G_\mathrm{dov}} = \gamma_\mathrm{dov}/\sqrt{\boldsymbol{\phi_\mathrm{T}}} \tag{4.30}$$

$$\boldsymbol{\xi_\mathrm{ov}} = 1 + \boldsymbol{G_\mathrm{ov}}/\sqrt{2} \tag{4.31}$$

$$\boldsymbol{\xi_\mathrm{dov}} = 1 + \boldsymbol{G_\mathrm{dov}}/\sqrt{2} \tag{4.32}$$

$$\boldsymbol{x_\mathrm{mrgov}} = 10^{-5} \cdot \boldsymbol{\xi_\mathrm{ov}} \tag{4.33}$$

$$\boldsymbol{x_\mathrm{mrgdov}} = 10^{-5} \cdot \boldsymbol{\xi_\mathrm{dov}} \tag{4.34}$$

Mobility parameters

$$\boldsymbol{\beta} = \textbf{FACTUO} \cdot \textbf{BETN} \cdot C_{\rm ox} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STBET}} \tag{4.35}$$

$$\boldsymbol{\theta_\mu} = \textbf{THEMU} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STTHEMU}} \tag{4.36}$$

$$\boldsymbol{\mu_{\rm E}} = \textbf{MUE} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STMUE}} \tag{4.37}$$

$$\boldsymbol{X_{\rm cor}} = \textbf{XCOR} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STXCOR}} \tag{4.38}$$

$$\boldsymbol{C_{\rm S}} = \textbf{CS} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STCS}} \tag{4.39}$$

$$\boldsymbol{E_{\rm eff0}} = 10^{-8} \cdot C_{\rm ox}/\epsilon_{\rm Si} \tag{4.40}$$

$$\boldsymbol{\eta_\mu} = \begin{cases} 1/2 \cdot \textbf{FETA} & \text{for NMOS} \\ 1/3 \cdot \textbf{FETA} & \text{for PMOS} \end{cases} \tag{4.41}$$

Series resistance parameter

$$R_{\rm s} = \textbf{RS} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STRS}} \tag{4.42}$$

$$\boldsymbol{\theta_{\rm R}} = 2 \cdot \boldsymbol{\beta} \cdot R_{\rm s} \tag{4.43}$$

Velocity saturation parameter

$$\boldsymbol{\theta_{\rm sat}} = \textbf{THESAT} \cdot (T_{\rm KR}/T_{\rm KD})^{\textbf{STTHESAT}} \tag{4.44}$$

Impact-ionization parameter

$$\boldsymbol{a_2} = \textbf{A2} \cdot (T_{\rm KD}/T_{\rm KR})^{\textbf{STA2}} \tag{4.45}$$

Gate current parameters

$$\boldsymbol{I_{\rm GINV}} = \textbf{IGINV} \cdot (T_{\rm KD}/T_{\rm KR})^{\textbf{STIG}} \tag{4.46}$$

$$\boldsymbol{I_{\rm GOV}} = \textbf{IGOV} \cdot (T_{\rm KD}/T_{\rm KR})^{\textbf{STIG}} \tag{4.47}$$

$$\boldsymbol{I_{\rm GOVD}} = \textbf{IGOVD} \cdot (T_{\rm KD}/T_{\rm KR})^{\textbf{STIG}} \tag{4.48}$$

$$\boldsymbol{B} = \frac{4}{3} \cdot \frac{\textbf{TOX}}{\hbar} \cdot \sqrt{2 \cdot q \cdot m_0 \cdot \textbf{CHIB}} = 6.830909 \cdot 10^9 \cdot \textbf{TOX} \cdot \sqrt{\textbf{CHIB}} \tag{4.49}$$

$$\boldsymbol{B_{\rm ov}} = \boldsymbol{B} \cdot \textbf{TOXOV}/\textbf{TOX} \tag{4.50}$$

$$\boldsymbol{B_{\rm ovd}} = \boldsymbol{B} \cdot \textbf{TOXOVD}/\textbf{TOX} \tag{4.51}$$

$$\boldsymbol{GC_{\rm Q}} = \begin{cases} -0.99 \cdot \dfrac{\textbf{GC2}}{2 \cdot \textbf{GC3}} & \text{for } \textbf{GC3} < 0 \\ 0 & \text{for } \textbf{GC3} \geq 0 \end{cases} \tag{4.52}$$

$$\boldsymbol{\alpha_{\rm b}} = \frac{E_{\rm g}/q + \boldsymbol{\phi_{\rm B}}}{2} \tag{4.53}$$

$$\boldsymbol{D_{\rm ch}} = \textbf{GCO} \cdot \boldsymbol{\phi^*_{\rm T}} \tag{4.54}$$

$$\boldsymbol{D_{\rm ov}} = \textbf{GCO} \cdot \boldsymbol{\phi_{\rm T}} \tag{4.55}$$

Gate-induced drain leakage parameters

$$\boldsymbol{A}_{\mathbf{GIDL}} = \mathbf{AGIDL} \cdot \left(\frac{2 \cdot 10^{-9}}{\mathbf{TOXOV}} \right)^2 \tag{4.56}$$

$$\boldsymbol{A}_{\mathbf{GIDLD}} = \mathbf{AGIDLD} \cdot \left(\frac{2 \cdot 10^{-9}}{\mathbf{TOXOVD}} \right)^2 \tag{4.57}$$

$$\boldsymbol{B}_{\mathbf{GIDL}} = \mathbf{BGIDL} \cdot \mathrm{MAX}\left([1 + \mathbf{STBGIDL} \cdot \Delta T] \, , \, 0 \right) \cdot \left(\frac{\mathbf{TOXOV}}{2 \cdot 10^{-9}} \right) \tag{4.58}$$

$$\boldsymbol{B}_{\mathbf{GIDLD}} = \mathbf{BGIDLD} \cdot \mathrm{MAX}\left([1 + \mathbf{STBGIDLD} \cdot \Delta T] \, , \, 0 \right) \cdot \left(\frac{\mathbf{TOXOVD}}{2 \cdot 10^{-9}} \right) \tag{4.59}$$

Noise parameter

$$\boldsymbol{N}_{\mathbf{T}} = \mathbf{FNT} \cdot 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} \tag{4.60}$$

Additional internal parameters

$$\boldsymbol{x}_{\mathbf{1}} = 1.25 \tag{4.61}$$

$$\boldsymbol{x}_{\mathbf{g1}} = \boldsymbol{x}_{\mathbf{1}} + \boldsymbol{G}_{\mathbf{ov}} \cdot \sqrt{\exp(-\boldsymbol{x}_{\mathbf{1}}) + \boldsymbol{x}_{\mathbf{1}} - 1} \tag{4.62}$$

$$\boldsymbol{x}_{\mathbf{dg1}} = \boldsymbol{x}_{\mathbf{1}} + \boldsymbol{G}_{\mathbf{dov}} \cdot \sqrt{\exp(-\boldsymbol{x}_{\mathbf{1}}) + \boldsymbol{x}_{\mathbf{1}} - 1} \tag{4.63}$$

4.2 Current Model

In this section, the model equations of the PSP-model are given. Use is made of the applied terminal bias values V_{GS}, V_{DS} and V_{SB}, the local parameters listed in Section 2.5.7 and the internal parameters introduced in Section 4.1. Local parameters are denoted by capital characters in bold font, whereas internal (bias-independent) parameters are denoted by symbols in bold font.

The definitions of the auxiliary functions MINA(.), MAXA(.), $\chi(.)$ and $\sigma_{1,2}(.)$ can be found in Appendix A.

4.2.1 Conditioning of Terminal Voltages

$$\phi_{\mathrm{V}} = \mathrm{MINA}\left(V_{\mathrm{SB}},\, V_{\mathrm{SB}} + V_{\mathrm{DS}},\, \boldsymbol{b_\phi}\right) + \boldsymbol{\phi_{\mathrm{X}}} \tag{4.64}$$

$$V^*_{\mathrm{SB}} = V_{\mathrm{SB}} - \mathrm{MINA}\left(\phi_{\mathrm{V}},\, 0,\, \boldsymbol{a_\phi}\right) + \boldsymbol{\phi^*_{\mathrm{X}}} \tag{4.65}$$

$$V^*_{\mathrm{DB}} = V_{\mathrm{DS}} + V^*_{\mathrm{SB}} \tag{4.66}$$

$$V_{\mathrm{dsx}} = \sqrt{{V_{\mathrm{DS}}}^2 + 0.01} - 0.1 \tag{4.67}$$

$$V_{\mathrm{sbx}} = V^*_{\mathrm{SB}} + \frac{V_{\mathrm{DS}} - V_{\mathrm{dsx}}}{2} \tag{4.68}$$

Drain-induced barrier lowering:

$$\Delta V_{\mathrm{G}} = \mathbf{CF} \cdot V_{\mathrm{dsx}} \cdot \left(1 + \mathbf{CFB} \cdot V_{\mathrm{sbx}}\right) \tag{4.69}$$

$$V^*_{\mathrm{GB}} = V_{\mathrm{GS}} + V^*_{\mathrm{SB}} + \Delta V_{\mathrm{G}} - \boldsymbol{V_{\mathrm{FB}}} \tag{4.70}$$

$$x_{\mathrm{g}} = V^*_{\mathrm{GB}} / \boldsymbol{\phi^*_{\mathrm{T}}} \tag{4.71}$$

4.2.2 Bias-Dependent Body Factor

$$D_{\mathrm{nsub}} = \mathbf{DNSUB} \cdot \mathrm{MAXA}\big(0,\, V_{\mathrm{GS}} + V_{\mathrm{SB}} - \mathbf{VNSUB},\, \mathbf{NSLP}\big) \tag{4.72}$$

$$G = \boldsymbol{G_0} \cdot \sqrt{1 + D_{\mathrm{nsub}}} \tag{4.73}$$

4.2.3 Surface Potential at Source Side and Related Variables

$$\xi = 1 + G/\sqrt{2} \tag{4.74}$$

$$x_{\mathrm{ns}} = \frac{\boldsymbol{\phi_{\mathrm{B}}} + V^*_{\mathrm{SB}}}{\boldsymbol{\phi^*_{\mathrm{T}}}} \tag{4.75}$$

$$\Delta_{\mathrm{ns}} = \exp\left(-x_{\mathrm{ns}}\right) \tag{4.76}$$

$$x_{\mathrm{mrg}} = 10^{-5} \cdot \xi \tag{4.77}$$

$$
\text{if } x_\mathrm{g} < -x_\mathrm{mrg} \begin{cases}
y_\mathrm{g} = -x_\mathrm{g} \\
z = 1.25 \cdot y_\mathrm{g}/\xi \\
\eta = \left[z + 10 - \sqrt{(z-6)^2 + 64}\right]/2 \\
a = \left(y_\mathrm{g} - \eta\right)^2 + G^2 \cdot (\eta + 1) \\
c = 2 \cdot (y_\mathrm{g} - \eta) - G^2 \\
\tau = -\eta + \ln\left(a/G^2\right) \\
y_0 = \sigma_1(a,\, c,\, \tau,\, \eta) \\
\Delta_0 = \exp\left(y_0\right) \\
p = 2 \cdot (y_\mathrm{g} - y_0) + G^2 \cdot [\Delta_0 - 1 + \Delta_\mathrm{ns} \cdot (1 - \chi'(y_0) - 1/\Delta_0)] \\
q = \left(y_\mathrm{g} - y_0\right)^2 + G^2 \cdot [y_0 - \Delta_0 + 1 + \Delta_\mathrm{ns} \cdot (1 + \chi(y_0) - 1/\Delta_0 - 2 \cdot y_0)] \\
x_\mathrm{s} = -y_0 - \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [\Delta_0 + \Delta_\mathrm{ns} \cdot (1/\Delta_0 - \chi''(y_0))]\}}}
\end{cases} \tag{4.78}
$$

$$
\text{if } |x_\mathrm{g}| \le x_\mathrm{mrg} \left\{ \; x_\mathrm{s} = \frac{x_\mathrm{g}}{\xi} \cdot \left[1 + G \cdot x_\mathrm{g} \cdot \frac{1 - \Delta_\mathrm{ns}}{\xi^2 \cdot 6 \cdot \sqrt{2}}\right] \right. \tag{4.79}
$$

$$
\text{if } x_\mathrm{g} > x_\mathrm{mrg} \begin{cases}
\hat{x}_\mathrm{g1} = \boldsymbol{x_1} + G \cdot \sqrt{\exp(-\boldsymbol{x_1}) + \boldsymbol{x_1} - 1} \\
\bar{x} = \dfrac{x_\mathrm{g}}{\xi} \cdot \left[1 + x_\mathrm{g} \cdot (\xi \cdot \boldsymbol{x_1} - \hat{x}_\mathrm{g1})/\hat{x}_\mathrm{g1}^2\right] \\
x_0 = x_\mathrm{g} + G^2/2 - G \cdot \sqrt{x_\mathrm{g} + G^2/4 - 1 + \exp(-\bar{x})} \\
b_\mathrm{x} = x_\mathrm{ns} + 3 \\
\eta = \mathrm{MINA}(x_0,\, b_\mathrm{x},\, 5) - \left(b_\mathrm{x} - \sqrt{b_\mathrm{x}^2 + 5}\right)/2 \\
a = (x_\mathrm{g} - \eta)^2 - G^2 \cdot [\exp(-\eta) + \eta - 1 - \Delta_\mathrm{ns} \cdot (\eta + 1 + \chi(\eta))] \\
b = 1 - G^2/2 \cdot [\exp(-\eta) - \Delta_\mathrm{ns} \cdot \chi''(\eta)] \\
c = 2 \cdot (x_\mathrm{g} - \eta) + G^2 \cdot [1 - \exp(-\eta) - \Delta_\mathrm{ns} \cdot (1 + \chi'(\eta))] \\
\tau = x_\mathrm{ns} - \eta + \ln\left(a/G^2\right) \\
y_0 = \sigma_2(a,\, b,\, c,\, \tau,\, \eta) \\
\Delta_0 = \exp\left(y_0\right) \\
p = 2 \cdot (x_\mathrm{g} - y_0) + G^2 \cdot [1 - 1/\Delta_0 + \Delta_\mathrm{ns} \cdot (\Delta_0 - 1 - \chi'(y_0))] \\
q = \left(x_\mathrm{g} - y_0\right)^2 - G^2 \cdot [y_0 + 1/\Delta_0 - 1 + \Delta_\mathrm{ns} \cdot (\Delta_0 - y_0 - 1 - \chi(y_0))] \\
x_\mathrm{s} = y_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [1/\Delta_0 + \Delta_\mathrm{ns} \cdot (\Delta_0 - \chi''(y_0))]\}}}
\end{cases} \tag{4.80}
$$

Eqs. (4.81)-(4.83) are only calculated for $x_\mathrm{g} > 0$.

$$
E_\mathrm{s} = \exp\left(-x_\mathrm{s}\right) \tag{4.81}
$$

$$D_\mathrm{s} = [1/E_\mathrm{s} - x_\mathrm{s} - 1 - \chi(x_\mathrm{s})] \cdot \Delta_\mathrm{ns} \tag{4.82}$$

$$P_\mathrm{s} = x_\mathrm{s} - 1 + E_\mathrm{s} \tag{4.83}$$

$$x_\mathrm{gs} = \begin{cases} x_\mathrm{g} - x_\mathrm{s} & \text{for } x_\mathrm{g} \leq 0 \\ G \cdot \sqrt{D_\mathrm{s} + P_\mathrm{s}} & \text{for } x_\mathrm{g} > 0 \end{cases} \tag{4.84}$$

$$\psi_\mathrm{ss} = \boldsymbol{\phi}^*_\mathbf{T} \cdot x_\mathrm{s} \tag{4.85}$$

4.2.4 Drain Saturation Voltage

Eqs. (4.86)-(4.106) are only calculated for $x_\mathrm{g} > 0$.

$$q_\mathrm{is} = \frac{G^2 \cdot \boldsymbol{\phi}^*_\mathbf{T} \cdot D_\mathrm{s}}{x_\mathrm{gs} + G \cdot \sqrt{P_\mathrm{s}}} \tag{4.86}$$

$$\alpha_\mathrm{s} = 1 + \frac{G \cdot (1 - E_\mathrm{s})}{2 \cdot \sqrt{P_\mathrm{s}}} \tag{4.87}$$

$$q_\mathrm{bs} = \boldsymbol{\phi}^*_\mathbf{T} \cdot G \cdot \sqrt{P_\mathrm{s}} \tag{4.88}$$

$$\rho_\mathrm{b} = \begin{cases} 1 + \mathbf{RSB} \cdot V_\mathrm{sbx} & \text{for } \mathbf{RSB} \geq 0 \\ \dfrac{1}{1 - \mathbf{RSB} \cdot V_\mathrm{sbx}} & \text{for } \mathbf{RSB} < 0 \end{cases} \tag{4.89}$$

$$\rho_\mathrm{g,s} = \begin{cases} \dfrac{1}{1 + \mathbf{RSG} \cdot q_\mathrm{is}} & \text{for } \mathbf{RSG} \geq 0 \\ 1 - \mathbf{RSG} \cdot q_\mathrm{is} & \text{for } \mathbf{RSG} < 0 \end{cases} \tag{4.90}$$

$$\rho_\mathrm{s} = \boldsymbol{\theta}_\mathbf{R} \cdot \rho_\mathrm{b} \cdot \rho_\mathrm{g,s} \cdot q_\mathrm{is} \tag{4.91}$$

$$\mu_\mathrm{x} = \frac{1 + \boldsymbol{X}_\mathbf{cor} \cdot V_\mathrm{sbx}}{1 + 0.2 \cdot \boldsymbol{X}_\mathbf{cor} \cdot V_\mathrm{sbx}} \tag{4.92}$$

$$E_\mathrm{eff,s} = \boldsymbol{E}_\mathbf{eff0} \cdot \left(q_\mathrm{bs} + \boldsymbol{\eta}_{\boldsymbol{\mu}} \cdot q_\mathrm{is}\right) \tag{4.93}$$

$$G_\mathrm{mob,s} = \frac{1 + (\boldsymbol{\mu}_\mathbf{E} \cdot E_\mathrm{eff,s})^{\boldsymbol{\theta}_{\boldsymbol{\mu}}} + \boldsymbol{C}_\mathbf{S} \cdot \left(\dfrac{q_\mathrm{bs}}{q_\mathrm{is} + q_\mathrm{bs}}\right)^2 + \rho_\mathrm{s}}{\mu_\mathrm{x}} \tag{4.94}$$

$$\xi_\mathrm{tb} = \begin{cases} 1 + \mathbf{THESATB} \cdot V_\mathrm{sbx} & \text{for } \mathbf{THESATB} \geq 0 \\ \dfrac{1}{1 - \mathbf{THESATB} \cdot V_\mathrm{sbx}} & \text{for } \mathbf{THESATB} < 0 \end{cases} \tag{4.95}$$

$$w_\mathrm{sat,s} = \frac{100 \cdot q_\mathrm{is} \cdot \xi_\mathrm{tb}}{100 + q_\mathrm{is} \cdot \xi_\mathrm{tb}} \tag{4.96}$$

$$\theta^*_{\mathrm{sat,s}} = \begin{cases} \dfrac{\boldsymbol{\theta_{\mathrm{sat}}}}{G_{\mathrm{mob,s}}} \cdot (1 + \mathbf{THESATG} \cdot w_{\mathrm{sat,s}}) & \text{for } \mathbf{THESATG} \geq 0 \\ \dfrac{\boldsymbol{\theta_{\mathrm{sat}}}}{G_{\mathrm{mob,s}}} \cdot \dfrac{1}{1 - \mathbf{THESATG} \cdot w_{\mathrm{sat,s}}} & \text{for } \mathbf{THESATG} < 0 \end{cases} \tag{4.97}$$

$$\phi_\infty = q_{\mathrm{is}}/\alpha_{\mathrm{s}} + \boldsymbol{\phi^*_{\mathrm{T}}} \tag{4.98}$$

$$y_{\mathrm{sat}} = \begin{cases} \theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2} & \text{for NMOS} \\ \dfrac{\theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2}}{\sqrt{1 + \theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2}}} & \text{for PMOS} \end{cases} \tag{4.99}$$

$$z_{\mathrm{a}} = \frac{2}{1 + \sqrt{1 + 4 \cdot y_{\mathrm{sat}}}} \tag{4.100}$$

$$\phi_0 = \phi_\infty \cdot z_{\mathrm{a}} \cdot \left[1 + 0.86 \cdot z_{\mathrm{a}} \cdot y_{\mathrm{sat}} \cdot \frac{1 - z_{\mathrm{a}}^2 \cdot y_{\mathrm{sat}}}{1 + 4 \cdot z_{\mathrm{a}}^3 \cdot y_{\mathrm{sat}}^2}\right] \tag{4.101}$$

$$a_{\mathrm{sat}} = x_{\mathrm{gs}} + G^2/2 \tag{4.102}$$

$$\phi_2 = \frac{\boldsymbol{\phi^*_{\mathrm{T}}} \cdot 0.98 \cdot G^2 \cdot D_{\mathrm{s}}}{a_{\mathrm{sat}} + \sqrt{a_{\mathrm{sat}}^2 - 0.98 \cdot G^2 \cdot D_{\mathrm{s}}}} \tag{4.103}$$

$$\phi_{\mathrm{sat}} = \frac{2 \cdot \phi_0 \cdot \phi_2}{\phi_0 + \phi_2 + \sqrt{(\phi_0 + \phi_2)^2 - 3.96 \cdot \phi_0 \cdot \phi_2}} \tag{4.104}$$

$$V_{\mathrm{dsat}} = \phi_{\mathrm{sat}} - \boldsymbol{\phi^*_{\mathrm{T}}} \cdot \ln\left[1 + \frac{\phi_{\mathrm{sat}} \cdot \left(\phi_{\mathrm{sat}} - 2 \cdot a_{\mathrm{sat}} \cdot \boldsymbol{\phi^*_{\mathrm{T}}}\right)}{G^2 \cdot D_{\mathrm{s}} \cdot \boldsymbol{\phi^*_{\mathrm{T}}}^2}\right] \tag{4.105}$$

$$V_{\mathrm{dse}} = \frac{V_{\mathrm{DS}}}{\left[1 + (V_{\mathrm{DS}}/V_{\mathrm{dsat}})^{\mathbf{AX}}\right]^{1/\mathbf{AX}}} \tag{4.106}$$

4.2.5 Surface Potential at Drain Side and Related Variables

Eqs. (4.107)-(4.116) are only calculated for $x_{\mathrm{g}} > 0$.

$$x_{\mathrm{nd}} = \frac{\boldsymbol{\phi_{\mathrm{B}}} + V^*_{\mathrm{SB}} + V_{\mathrm{dse}}}{\boldsymbol{\phi^*_{\mathrm{T}}}} \tag{4.107}$$

$$k_{\mathrm{ds}} = \exp\left(-V_{\mathrm{dse}}/\boldsymbol{\phi^*_{\mathrm{T}}}\right) \tag{4.108}$$

$$\Delta_{\mathrm{nd}} = \Delta_{\mathrm{ns}} \cdot k_{\mathrm{ds}} \tag{4.109}$$

$$\text{if } x_{\mathrm{g}} \leq x_{\mathrm{mrg}} \left\{ \; x_{\mathrm{d}} = \frac{x_{\mathrm{g}}}{\xi} \cdot \left[1 + G \cdot x_{\mathrm{g}} \cdot \frac{1 - \Delta_{\mathrm{nd}}}{\xi^2 \cdot 6 \cdot \sqrt{2}}\right] \right. \tag{4.110}$$

$$\text{if } x_{\mathrm{g}} > x_{\mathrm{mrg}} \begin{cases} b_{\mathrm{x}} = x_{\mathrm{nd}} + 3.0 \\ \eta = \mathrm{MINA}(x_0,\, b_{\mathrm{x}},\, 5) - \left(b_{\mathrm{x}} - \sqrt{b_{\mathrm{x}}^2 + 5}\right)/2 \\ a = (x_{\mathrm{g}} - \eta)^2 - G^2 \cdot [\exp(-\eta) + \eta - 1 - \Delta_{\mathrm{nd}} \cdot (\eta + 1 + \chi(\eta))] \\ b = 1 - G^2/2 \cdot [\exp(-\eta) - \Delta_{\mathrm{nd}} \cdot \chi''(\eta)] \\ c = 2 \cdot (x_{\mathrm{g}} - \eta) + G^2 \cdot [1 - \exp(-\eta) - \Delta_{\mathrm{nd}} \cdot (1 + \chi'(\eta))] \\ \tau = x_{\mathrm{nd}} - \eta + \ln\left(a/G^2\right) \\ y_0 = \sigma_2(a,\, b,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp\left(y_0\right) \\ p = 2 \cdot (x_{\mathrm{g}} - y_0) + G^2 \cdot [1 - 1/\Delta_0 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - 1 - \chi'(y_0))] \\ q = (x_{\mathrm{g}} - y_0)^2 - G^2 \cdot [y_0 + 1/\Delta_0 - 1 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - y_0 - 1 - \chi(y_0))] \\ x_{\mathrm{d}} = y_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [1/\Delta_0 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - \chi''(y_0))]\}}} \end{cases} \tag{4.111}$$

$$x_{\mathrm{ds}} = x_{\mathrm{d}} - x_{\mathrm{s}} \tag{4.112}$$

$$\text{if } x_{\mathrm{ds}} < 10^{-10} \begin{cases} p = 2 \cdot x_{\mathrm{gs}} + G^2 \cdot [1 - E_{\mathrm{s}} + \Delta_{\mathrm{nd}} \cdot (1/E_{\mathrm{s}} - 1 - \chi'(x_{\mathrm{s}}))] \\ q = G^2 \cdot (1 - k_{\mathrm{ds}}) \cdot D_{\mathrm{s}} \\ \xi = 1 - G^2/2 \cdot [E_{\mathrm{s}} + \Delta_{\mathrm{nd}}\,(1/E_{\mathrm{s}} - \chi''(x_{\mathrm{s}}))] \\ x_{\mathrm{ds}} = \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot \xi \cdot q}} \\ x_{\mathrm{d}} = x_{\mathrm{s}} + x_{\mathrm{ds}} \end{cases} \tag{4.113}$$

$$E_{\mathrm{d}} = \exp\left(-x_{\mathrm{d}}\right) \tag{4.114}$$

$$D_{\mathrm{d}} = (1/E_{\mathrm{d}} - x_{\mathrm{d}} - 1 - \chi(x_{\mathrm{d}})) \cdot \Delta_{\mathrm{nd}} \tag{4.115}$$

$$\Delta\psi = \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot x_{\mathrm{ds}} \tag{4.116}$$

$$\psi_{\mathrm{sd}} = \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot x_{\mathrm{d}} \tag{4.117}$$

4.2.6 Mid-Point Surface Potential and Related Variables

$$\text{if } x_{\mathrm{g}} > 0 \begin{cases} x_{\mathrm{m}} = \left(x_{\mathrm{s}} + x_{\mathrm{d}}\right)/2 \\ E_{\mathrm{m}} = \sqrt{E_{\mathrm{s}} \cdot E_{\mathrm{d}}} \\ \bar{D} = \left(D_{\mathrm{s}} + D_{\mathrm{d}}\right)/2 \\ D_{\mathrm{m}} = \bar{D} + x_{\mathrm{ds}}^2/8 \cdot \left(E_{\mathrm{m}} - 2/G^2\right) \\ P_{\mathrm{m}} = x_{\mathrm{m}} - 1 + E_{\mathrm{m}} \\ x_{\mathrm{gm}} = G \cdot \sqrt{D_{\mathrm{m}} + P_{\mathrm{m}}} \end{cases} \tag{4.118}$$

$$\text{if } x_{\mathrm{g}} \leq 0 \begin{cases} x_{\mathrm{m}} = x_{\mathrm{s}} \\ x_{\mathrm{gm}} = x_{\mathrm{g}} - x_{\mathrm{s}} \end{cases} \tag{4.119}$$

4.2.7 Polysilicon Depletion

Eqs. (4.120)-(4.134) are only calculated for $\boldsymbol{k_{\mathrm{P}}} > 0$ and $x_{\mathrm{g}} > 0$ (otherwise $\eta_{\mathrm{p}} = 1$):

$$x_{\mathrm{m}}^{(0)} = x_{\mathrm{m}}, \qquad x_{\mathrm{ds}}^{(0)} = x_{\mathrm{ds}}, \qquad D_{\mathrm{m}}^{(0)} = D_{\mathrm{m}}, \qquad E_{\mathrm{m}}^{(0)} = E_{\mathrm{m}}, \tag{4.120}$$

$$d_0 = 1 - E_{\mathrm{m}}^{(0)} + 2 \cdot x_{\mathrm{gm}}/G^2 \tag{4.121}$$

$$\eta_{\mathrm{p}} = 1/\sqrt{1 + \boldsymbol{k_{\mathrm{P}}} \cdot x_{\mathrm{gm}}} \tag{4.122}$$

$$x_{\mathrm{pm}} = \boldsymbol{k_{\mathrm{P}}} \cdot \left[\frac{\eta_{\mathrm{p}} \cdot x_{\mathrm{gm}}}{1 + \eta_{\mathrm{p}}}\right]^2 \cdot \frac{D_{\mathrm{m}}^{(0)}}{D_{\mathrm{m}}^{(0)} + P_{\mathrm{m}}} \tag{4.123}$$

$$p = 2 \cdot (x_{\mathrm{gm}} - x_{\mathrm{pm}}) + G^2 \cdot \left(1 - E_{\mathrm{m}}^{(0)} + D_{\mathrm{m}}^{(0)}\right) \tag{4.124}$$

$$q = x_{\mathrm{pm}} \cdot (x_{\mathrm{pm}} - 2 \cdot x_{\mathrm{gm}}) \tag{4.125}$$

$$\xi_{\mathrm{p}} = 1 - G^2/2 \cdot \left(E_{\mathrm{m}}^{(0)} + D_{\mathrm{m}}^{(0)}\right) \tag{4.126}$$

$$u_{\mathrm{p}} = \frac{p \cdot q}{p^2 - \xi_{\mathrm{p}} \cdot q} \tag{4.127}$$

$$x_{\mathrm{m}} = x_{\mathrm{m}}^{(0)} + u_{\mathrm{p}} \tag{4.128}$$

$$E_{\mathrm{m}} = E_{\mathrm{m}}^{(0)} \cdot \exp\left(-u_{\mathrm{p}}\right) \tag{4.129}$$

$$D_{\mathrm{m}} = D_{\mathrm{m}}^{(0)} \cdot \exp\left(u_{\mathrm{p}}\right) \tag{4.130}$$

$$P_{\mathrm{m}} = x_{\mathrm{m}} - 1 + E_{\mathrm{m}} \tag{4.131}$$

$$x_{\mathrm{gm}} = G \cdot \sqrt{D_{\mathrm{m}} + P_{\mathrm{m}}} \tag{4.132}$$

$$x_{\mathrm{ds}} = x_{\mathrm{ds}}^{(0)} \cdot \frac{\exp\left(u_{\mathrm{p}}\right) \cdot \left[\bar{D} + d_0\right]}{1 - E_{\mathrm{m}} + 2 \cdot x_{\mathrm{gm}} \cdot \eta_{\mathrm{p}}/G^2 + \exp\left(u_{\mathrm{p}}\right) \cdot \bar{D}} \tag{4.133}$$

$$\Delta\psi = \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot x_{\mathrm{ds}} \tag{4.134}$$

4.2.8 Potential Mid-Point Inversion Charge and Related Variables

Eqs. (4.135)-(4.142) are only calculated for $x_\mathrm{g} > 0$.

$$q_\mathrm{im} = \frac{G^2 \cdot \boldsymbol{\phi}^*_\mathbf{T} \cdot D_\mathrm{m}}{x_\mathrm{gm} + G \cdot \sqrt{P_\mathrm{m}}} \tag{4.135}$$

$$\alpha_\mathrm{m} = \eta_\mathrm{p} + \frac{G \cdot (1 - E_\mathrm{m})}{2 \cdot \sqrt{P_\mathrm{m}}} \tag{4.136}$$

$$q^*_\mathrm{im} = q_\mathrm{im} + \boldsymbol{\phi}^*_\mathbf{T} \cdot \alpha_\mathrm{m} \tag{4.137}$$

$$q_\mathrm{bm} = \boldsymbol{\phi}^*_\mathbf{T} \cdot G \cdot \sqrt{P_\mathrm{m}} \tag{4.138}$$

Series resistance:

$$\rho_\mathrm{g} = \begin{cases} \dfrac{1}{1 + \mathbf{RSG} \cdot q_\mathrm{im}} & \text{for } \mathbf{RSG} \geq 0 \\ \\ 1 - \mathbf{RSG} \cdot q_\mathrm{im} & \text{for } \mathbf{RSG} < 0 \end{cases} \tag{4.139}$$

$$\rho_\mathrm{s} = \boldsymbol{\theta}_\mathbf{R} \cdot \rho_\mathrm{b} \cdot \rho_\mathrm{g} \cdot q_\mathrm{im} \tag{4.140}$$

Mobility reduction:

$$E_\mathrm{eff} = \boldsymbol{E}_\mathbf{eff0} \cdot \left(q_\mathrm{bm} + \boldsymbol{\eta}_{\boldsymbol{\mu}} \cdot q_\mathrm{im}\right) \tag{4.141}$$

$$G_\mathrm{mob} = \frac{1 + \left(\boldsymbol{\mu}_\mathbf{E} \cdot E_\mathrm{eff}\right)^{\boldsymbol{\theta}_{\boldsymbol{\mu}}} + \boldsymbol{C}_\mathbf{S} \cdot \left(\frac{q_\mathrm{bm}}{q_\mathrm{im} + q_\mathrm{bm}}\right)^2 + \rho}{\mu_\mathrm{x}} \tag{4.142}$$

4.2.9 Drain-Source Channel Current

Eqs. (4.143)-(4.154) are only calculated for $x_\mathrm{g} > 0$:

Channel length modulation:

$$R_1 = q_\mathrm{im} / q^*_\mathrm{im} \tag{4.143}$$

$$R_2 = \boldsymbol{\phi}^*_\mathbf{T} \cdot \alpha_\mathrm{m} / q^*_\mathrm{im} \tag{4.144}$$

$$T_1 = \ln\left(\frac{1 + \dfrac{V_\mathrm{DS} - \Delta\psi}{\mathbf{VP}}}{1 + \dfrac{V_\mathrm{dse} - \Delta\psi}{\mathbf{VP}}}\right) \tag{4.145}$$

$$T_2 = \ln\left(1 + \frac{V_\mathrm{dsx}}{\mathbf{VP}}\right) \tag{4.146}$$

$$\Delta L / L = \mathbf{ALP} \cdot T_1 \tag{4.147}$$

$$G_{\Delta L} = \frac{1}{1 + \Delta L/L + (\Delta L/L)^2} \tag{4.148}$$

$$\Delta L_1 / L = \left[\mathbf{ALP} + \frac{\mathbf{ALP1}}{q^*_\mathrm{im}} \cdot R_1\right] \cdot T_1 + \mathbf{ALP2} \cdot q_\mathrm{bm} \cdot R_2^2 \cdot T_2 \tag{4.149}$$

$$F_{\Delta L} = \left[1 + \Delta L_1/L + (\Delta L_1/L)^2\right] \cdot G_{\Delta L} \tag{4.150}$$

Velocity saturation:

$$w_{\mathrm{sat}} = \frac{100 \cdot q_{\mathrm{im}} \cdot \xi_{\mathrm{tb}}}{100 + q_{\mathrm{im}} \cdot \xi_{\mathrm{tb}}} \tag{4.151}$$

$$\theta^*_{\mathrm{sat}} = \begin{cases} \dfrac{\boldsymbol{\theta_{\mathrm{sat}}}}{G_{\mathrm{mob,s}} \cdot G_{\Delta L}} \cdot (1 + \mathbf{THESATG} \cdot w_{\mathrm{sat}}) & \text{for } \mathbf{THESATG} \geq 0 \\ \dfrac{\boldsymbol{\theta_{\mathrm{sat}}}}{G_{\mathrm{mob,s}} \cdot G_{\Delta L}} \cdot \dfrac{1}{1 - \mathbf{THESATG} \cdot w_{\mathrm{sat}}} & \text{for } \mathbf{THESATG} < 0 \end{cases} \tag{4.152}$$

$$z_{\mathrm{sat}} = \begin{cases} (\theta^*_{\mathrm{sat}} \cdot \Delta\psi)^2 & \text{for NMOS} \\ \dfrac{(\theta^*_{\mathrm{sat}} \cdot \Delta\psi)^2}{1 + \theta^*_{\mathrm{sat}} \cdot \Delta\psi} & \text{for PMOS} \end{cases} \tag{4.153}$$

$$G_{\mathrm{vsat}} = \frac{G_{\mathrm{mob}} \cdot G_{\Delta L}}{2} \cdot \left(1 + \sqrt{1 + 2 \cdot z_{\mathrm{sat}}}\right) \tag{4.154}$$

Drain-Source channel current:

$$I_{\mathrm{DS}} = \begin{cases} 0 & \text{for } x_{\mathrm{g}} \leq 0 \\ \boldsymbol{\beta} \cdot F_{\Delta L} \cdot \dfrac{q^*_{\mathrm{im}}}{G_{\mathrm{vsat}}} \cdot \Delta\psi & \text{for } x_{\mathrm{g}} > 0 \end{cases} \tag{4.155}$$

4.2.10 Auxiliary Variables for Calculation of Intrinsic Charges and Gate Current

Eqs. (4.156)-(4.158) are only calculated for $x_{\mathrm{g}} > 0$.

$$V_{\mathrm{oxm}} = \boldsymbol{\phi^*_{\mathrm{T}}} \cdot x_{\mathrm{gm}} \tag{4.156}$$

$$\alpha'_{\mathrm{m}} = \alpha_{\mathrm{m}} \cdot \left[1 + \frac{z_{\mathrm{sat}}}{2} \cdot \left(\frac{G_{\mathrm{mob}} \cdot G_{\Delta L}}{G_{\mathrm{vsat}}}\right)^2\right] \tag{4.157}$$

$$H = \frac{G_{\mathrm{mob}} \cdot G_{\Delta L}}{G_{\mathrm{vsat}}} \cdot \frac{q^*_{\mathrm{im}}}{\alpha'_{\mathrm{m}}} \tag{4.158}$$

4.2.11 Impact Ionization or Weak-Avalanche

The equations in this Section are only calculated when **SWIMPACT** $= 1$ and $x_{\mathrm{g}} > 0$.

$$a^*_2 = \boldsymbol{a_2} \cdot \left[1 + \mathbf{A4} \cdot \left(\sqrt{V^*_{\mathrm{SB}} + \boldsymbol{\phi_{\mathrm{B}}}} - \sqrt{\boldsymbol{\phi_{\mathrm{B}}}}\right)\right] \tag{4.159}$$

$$\Delta V_{\mathrm{sat}} = V_{\mathrm{DS}} - \mathbf{A3} \cdot \Delta\psi \tag{4.160}$$

$$M_{\mathrm{avl}} = \begin{cases} 0 & \text{for } \Delta V_{\mathrm{sat}} \leq 0 \\ \mathbf{A1} \cdot \Delta V_{\mathrm{sat}} \cdot \exp\left(-\dfrac{a^*_2}{\Delta V_{\mathrm{sat}}}\right) & \text{for } \Delta V_{\mathrm{sat}} > 0 \end{cases} \tag{4.161}$$

$$I_{\mathrm{avl}} = M_{\mathrm{avl}} \cdot I_{\mathrm{DS}} \tag{4.162}$$

4.2.12 Surface Potential in Gate Overlap Regions

$$x_{\mathrm{sov}}\left(x_{\mathrm{g}}\right)=\begin{cases}\text{if } x_{\mathrm{g}}<-\boldsymbol{x}_{\mathbf{mrgov}} \begin{cases} y_{\mathrm{g}}=-x_{\mathrm{g}} \\ z=\boldsymbol{x}_{\mathbf{1}}\cdot y_{\mathrm{g}}/\boldsymbol{\xi}_{\mathbf{ov}} \\ \eta=\left[z+10-\sqrt{(z-6)^2+64}\right]\Big/2 \\ a=\left(y_{\mathrm{g}}-\eta\right)^2+\boldsymbol{G}_{\mathbf{ov}}^2\cdot(\eta+1) \\ c=2\cdot\left(y_{\mathrm{g}}-\eta\right)-\boldsymbol{G}_{\mathbf{ov}}^2 \\ \tau=-\eta+\ln\left(a/\boldsymbol{G}_{\mathbf{ov}}^2\right) \\ y_0=\sigma_1(a,\,c,\,\tau,\,\eta) \\ \Delta_0=\exp\left(y_0\right) \\ p=2\cdot\left(y_{\mathrm{g}}-y_0\right)+\boldsymbol{G}_{\mathbf{ov}}^2\cdot\left(\Delta_0-1\right) \\ q=\left(y_{\mathrm{g}}-y_0\right)^2+\boldsymbol{G}_{\mathbf{ov}}^2\cdot\left(y_0-\Delta_0+1\right) \\ x_{\mathrm{sov}}=-y_0-\dfrac{2\cdot q}{p+\sqrt{p^2-2\cdot q\cdot\left(2-\boldsymbol{G}_{\mathbf{ov}}^2\cdot\Delta_0\right)}} \end{cases} \\ \text{if } \left|x_{\mathrm{g}}\right|<\boldsymbol{x}_{\mathbf{mrgov}} \begin{cases} x_{\mathrm{sov}}=x_{\mathrm{g}}/\boldsymbol{\xi}_{\mathbf{ov}} \end{cases} \\ \text{if } x_{\mathrm{g}}>\boldsymbol{x}_{\mathbf{mrgov}} \begin{cases} \bar{x}=x_{\mathrm{g}}/\boldsymbol{\xi}_{\mathbf{ov}}\cdot\left[1+x_{\mathrm{g}}\cdot\left(\boldsymbol{\xi}_{\mathbf{ov}}\cdot\boldsymbol{x}_{\mathbf{1}}-\boldsymbol{x}_{\mathbf{g1}}\right)/\boldsymbol{x}_{\mathbf{g1}}^2\right] \\ \omega=1-\exp\left(-\bar{x}\right) \\ x_0=x_{\mathrm{g}}+\boldsymbol{G}_{\mathbf{ov}}^2/2-\boldsymbol{G}_{\mathbf{ov}}\cdot\sqrt{x_{\mathrm{g}}+\boldsymbol{G}_{\mathbf{ov}}^2/4-\omega} \\ \Delta_0=\exp\left(-x_0\right) \\ p=2\cdot\left(x_{\mathrm{g}}-x_0\right)+\boldsymbol{G}_{\mathbf{ov}}^2\cdot\left(1-\Delta_0\right) \\ q=\left(x_{\mathrm{g}}-x_0\right)^2-\boldsymbol{G}_{\mathbf{ov}}^2\cdot\left(x_0+\Delta_0-1\right) \\ x_{\mathrm{sov}}=x_0+\dfrac{2\cdot q}{p+\sqrt{p^2-2\cdot q\cdot\left(2-\boldsymbol{G}_{\mathbf{ov}}^2\cdot\Delta_0\right)}} \end{cases} \end{cases} \tag{4.163}$$

$$x_{\rm dov}\left(x_{\rm g}\right)=\begin{cases}\text{if } x_{\rm g}<-\boldsymbol{x_{\rm mrgdov}} & \begin{cases} y_{\rm g}=-x_{\rm g}\\ z=\boldsymbol{x_1}\cdot y_{\rm g}/\boldsymbol{\xi_{\rm dov}}\\ \eta=\left[z+10-\sqrt{(z-6)^2+64}\right]\Big/2\\ a=\left(y_{\rm g}-\eta\right)^2+\boldsymbol{G_{\rm dov}^2}\cdot(\eta+1)\\ c=2\cdot\left(y_{\rm g}-\eta\right)-\boldsymbol{G_{\rm dov}^2}\\ \tau=-\eta+\ln\left(a/\boldsymbol{G_{\rm dov}^2}\right)\\ y_0=\sigma_1(a,\,c,\,\tau,\,\eta)\\ \Delta_0=\exp\left(y_0\right)\\ p=2\cdot\left(y_{\rm g}-y_0\right)+\boldsymbol{G_{\rm dov}^2}\cdot\left(\Delta_0-1\right)\\ q=\left(y_{\rm g}-y_0\right)^2+\boldsymbol{G_{\rm dov}^2}\cdot\left(y_0-\Delta_0+1\right)\\ x_{\rm dov}=-y_0-\dfrac{2\cdot q}{p+\sqrt{p^2-2\cdot q\cdot\left(2-\boldsymbol{G_{\rm dov}^2}\cdot\Delta_0\right)}}\end{cases}\\ \text{if } \left|x_{\rm g}\right|<\boldsymbol{x_{\rm mrgdov}} & \left\{\ x_{\rm dov}=x_{\rm g}/\boldsymbol{\xi_{\rm dov}}\right.\\ \text{if } x_{\rm g}>\boldsymbol{x_{\rm mrgdov}} & \begin{cases}\bar{x}=x_{\rm g}/\boldsymbol{\xi_{\rm dov}}\cdot\left[1+x_{\rm g}\cdot\left(\boldsymbol{\xi_{\rm dov}}\cdot\boldsymbol{x_1}-\boldsymbol{x_{\rm dg1}}\right)/\boldsymbol{x_{\rm dg1}^2}\right]\\ \omega=1-\exp\left(-\bar{x}\right)\\ x_0=x_{\rm g}+\boldsymbol{G_{\rm dov}^2}/2-\boldsymbol{G_{\rm dov}}\cdot\sqrt{x_{\rm g}+\boldsymbol{G_{\rm dov}^2}/4-\omega}\\ \Delta_0=\exp\left(-x_0\right)\\ p=2\cdot\left(x_{\rm g}-x_0\right)+\boldsymbol{G_{\rm dov}^2}\cdot\left(1-\Delta_0\right)\\ q=\left(x_{\rm g}-x_0\right)^2-\boldsymbol{G_{\rm dov}^2}\cdot\left(x_0+\Delta_0-1\right)\\ x_{\rm dov}=x_0+\dfrac{2\cdot q}{p+\sqrt{p^2-2\cdot q\cdot\left(2-\boldsymbol{G_{\rm dov}^2}\cdot\Delta_0\right)}}\end{cases}\end{cases}\tag{4.164}$$

$$\psi_{\rm sov}=-\boldsymbol{\phi_{\rm T}}\cdot x_{\rm sov}\left(-\frac{V_{\rm GS}}{\boldsymbol{\phi_{\rm T}}}\right)\tag{4.165}$$

$$\psi_{\rm dov}=-\boldsymbol{\phi_{\rm T}}\cdot x_{\rm dov}\left(-\frac{V_{\rm GS}-V_{\rm DS}}{\boldsymbol{\phi_{\rm T}}}\right)\tag{4.166}$$

$$V_{\rm ov_0}=V_{\rm GS}-\psi_{\rm sov}\tag{4.167}$$

$$V_{\rm ov_L}=V_{\rm GS}-V_{\rm DS}-\psi_{\rm dov}\tag{4.168}$$

4.2.13 Gate Current

The equations in this Section are only calculated when **SWIGATE** $=1$.

Source/Drain gate overlap current:

$$I_{\rm GSov}(V_{\rm GX},\,\psi_{\rm ov},\,V_{\rm ov}) = \begin{cases} V_{\rm ov}^{*} = \sqrt{V_{\rm ov}^{2} + 10^{-6}} \\ \psi_{\rm tov} = \mathrm{MINA}\left(0,\,V_{\rm ov} + \boldsymbol{D_{\rm ov}},\,0.01\right) \\ z_{\rm g} = \begin{cases} \mathrm{MINA}\left(\dfrac{V_{\rm ov}^{*}}{\mathbf{CHIB}},\,\boldsymbol{GC_{\rm Q}},\,10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\ \dfrac{V_{\rm ov}^{*}}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \\ \Delta_{\rm Siov} = \exp\left(\dfrac{3.0 \cdot \boldsymbol{\phi_{\rm T}} + \psi_{\rm ov} + \psi_{\rm tov}}{\boldsymbol{\phi_{\rm T}}}\right) \\ F_{\rm Sov} = \ln\left[\dfrac{1 + \Delta_{\rm Siov}}{1 + \Delta_{\rm Siov} \cdot \exp\left(-V_{\rm GX}/\boldsymbol{\phi_{\rm T}}\right)}\right] \\ I_{\rm Gov} = \boldsymbol{I_{\rm GOV}} \cdot F_{\rm Sov} \cdot \\ \qquad \exp\left(\boldsymbol{B_{\rm ov}} \cdot \left[-\dfrac{3}{2} + z_{\rm g} \cdot \left(\mathbf{GC2} + \mathbf{GC3} \cdot z_{\rm g}\right)\right]\right) \end{cases} \tag{4.169}$$

$$I_{\rm GDov}(V_{\rm GX},\,\psi_{\rm ov},\,V_{\rm ov}) = \begin{cases} V_{\rm ov}^{*} = \sqrt{V_{\rm ov}^{2} + 10^{-6}} \\ \psi_{\rm tov} = \mathrm{MINA}\left(0,\,V_{\rm ov} + \boldsymbol{D_{\rm ov}},\,0.01\right) \\ z_{\rm g} = \begin{cases} \mathrm{MINA}\left(\dfrac{V_{\rm ov}^{*}}{\mathbf{CHIB}},\,\boldsymbol{GC_{\rm Q}},\,10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\ \dfrac{V_{\rm ov}^{*}}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \\ \Delta_{\rm Siov} = \exp\left(\dfrac{3.0 \cdot \boldsymbol{\phi_{\rm T}} + \psi_{\rm ov} + \psi_{\rm tov}}{\boldsymbol{\phi_{\rm T}}}\right) \\ F_{\rm Sov} = \ln\left[\dfrac{1 + \Delta_{\rm Siov}}{1 + \Delta_{\rm Siov} \cdot \exp\left(-V_{\rm GX}/\boldsymbol{\phi_{\rm T}}\right)}\right] \\ I_{\rm Gov} = \boldsymbol{I_{\rm GOVD}} \cdot F_{\rm Sov} \cdot \\ \qquad \exp\left(\boldsymbol{B_{\rm dov}} \cdot \left[-\dfrac{3}{2} + z_{\rm g} \cdot \left(\mathbf{GC2} + \mathbf{GC3} \cdot z_{\rm g}\right)\right]\right) \end{cases} \tag{4.170}$$

$$I_{\rm GSov} = I_{\rm GSov}\left(V_{\rm GS},\,\psi_{\rm sov},\,V_{\rm ov_0}\right) \tag{4.171}$$

$$I_{\rm GDov} = I_{\rm GDov}\left(V_{\rm GS} - V_{\rm DS}\,,\,\psi_{\rm dov},\,V_{\rm ov_L}\right) \tag{4.172}$$

Gate-channel current:

$$V_{\rm m} = V_{\rm SB}^{*} + \boldsymbol{\phi_{\rm T}^{*}} \cdot \left[\frac{x_{\rm ds}}{2} - \ln\left(\frac{1 + \exp(x_{\rm ds} - V_{\rm dse}/\boldsymbol{\phi_{\rm T}^{*}})}{2}\right)\right] \tag{4.173}$$

$$\psi_{\rm t} = \mathrm{MINA}\left(0,\,V_{\rm oxm} + \boldsymbol{D_{\rm ch}},\,0.01\right) \tag{4.174}$$

$$V_{\rm oxm}^{*} = \sqrt{V_{\rm oxm}^{2} + 10^{-6}} \tag{4.175}$$

$$z_{\mathrm{g}} = \begin{cases} \mathrm{MINA}\left(\dfrac{V^*_{\mathrm{oxm}}}{\mathbf{CHIB}}, \boldsymbol{GC}_{\mathbf{Q}}, 10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\ \dfrac{V^*_{\mathrm{oxm}}}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \tag{4.176}$$

$$\Delta_{\mathrm{Si}} = \exp\left(x_{\mathrm{m}} - \frac{\boldsymbol{\alpha}_{\mathbf{b}} + V_{\mathrm{m}} - \psi_{\mathrm{t}}}{\boldsymbol{\phi}^*_{\mathbf{T}}}\right) \tag{4.177}$$

$$F_{\mathrm{S}} = \ln\left[\frac{1 + \Delta_{\mathrm{Si}}}{1 + \Delta_{\mathrm{Si}} \cdot \exp\left(-\dfrac{V_{\mathrm{GS}} + V^*_{\mathrm{SB}} - V_{\mathrm{m}}}{\boldsymbol{\phi}^*_{\mathbf{T}}}\right)}\right] \tag{4.178}$$

$$I_{\mathrm{GCO}} = \boldsymbol{I}_{\mathbf{GINV}} \cdot F_{\mathrm{S}} \cdot \exp\left(\boldsymbol{B} \cdot \left[-3/2 + z_{\mathrm{g}} \cdot \left(\mathbf{GC2} + \mathbf{GC3} \cdot z_{\mathrm{g}}\right)\right]\right) \tag{4.179}$$

$$\text{if } x_{\mathrm{g}} > 0 \begin{cases} u_0 = \mathbf{CHIB}/\left[\boldsymbol{B} \cdot \left(\mathbf{GC2} + 2 \cdot \mathbf{GC3} \cdot z_{\mathrm{g}}\right)\right] \\ x = \Delta\psi/\left(2 \cdot u_0\right) \\ b = u_0/H \\ B_{\mathrm{g}} = b \cdot (1 - b)/2 \\ A_{\mathrm{g}} = 1/2 - 3 \cdot B_{\mathrm{g}} \\ p_{\mathrm{gc}} = (1 - b) \cdot \dfrac{\sinh(x)}{x} + b \cdot \cosh(x) \\ p_{\mathrm{gd}} = \dfrac{p_{\mathrm{gc}}}{2} - B_{\mathrm{g}} \cdot \sinh(x) - A_{\mathrm{g}} \cdot \dfrac{\sinh(x)}{x} \cdot \left[\coth(x) - \dfrac{1}{x}\right] \end{cases} \tag{4.180}$$

$$\text{if } x_{\mathrm{g}} \leq 0 \begin{cases} p_{\mathrm{gc}} = 1 \\ p_{\mathrm{gd}} = 1/2 \end{cases} \tag{4.181}$$

$$S_{\mathrm{g}} = \frac{1}{2} \cdot \left(1 + \frac{x_{\mathrm{g}}}{\sqrt{x_{\mathrm{g}}^2 + 10^{-6}}}\right) \tag{4.182}$$

$$I_{\mathrm{GC}} = I_{\mathrm{GCO}} \cdot p_{\mathrm{gc}} \cdot S_{\mathrm{g}} \tag{4.183}$$

$$I_{\mathrm{GCD}} = I_{\mathrm{GCO}} \cdot p_{\mathrm{gd}} \cdot S_{\mathrm{g}} \tag{4.184}$$

$$I_{\mathrm{GCS}} = I_{\mathrm{GC}} - I_{\mathrm{GCD}} \tag{4.185}$$

$$I_{\mathrm{GB}} = I_{\mathrm{GCO}} \cdot p_{\mathrm{gc}} \cdot \left(1 - S_{\mathrm{g}}\right) \tag{4.186}$$

4.2.14 Gate-Induced Drain/Source Leakage Current

The equations in this section are only calculated when **SWGIDL** $= 1$.

$$I_{\mathrm{gisl}}(V_{\mathrm{ov}}, V) = \begin{cases} V_{\mathrm{tov}} = \sqrt{V_{\mathrm{ov}}^2 + \mathbf{CGIDL}^2 \cdot V^2 + 10^{-6}} \\ t = V \cdot V_{\mathrm{tov}} \cdot V_{\mathrm{ov}} \\ I_{\mathrm{gisl}} = \begin{cases} -\boldsymbol{A}_{\mathbf{GIDL}} \cdot t \cdot \exp\left(-\dfrac{\boldsymbol{B}_{\mathbf{GIDL}}}{V_{\mathrm{tov}}}\right) & \text{for } V_{\mathrm{ov}} < 0 \\ 0 & \text{for } V_{\mathrm{ov}} \geq 0 \end{cases} \end{cases} \tag{4.187}$$

$$I_{\mathrm{gidl}}(V_{\mathrm{ov}}, V) = \begin{cases} V_{\mathrm{tov}} = \sqrt{V_{\mathrm{ov}}^2 + \mathbf{CGIDLD}^2 \cdot V^2 + 10^{-6}} \\ t = V \cdot V_{\mathrm{tov}} \cdot V_{\mathrm{ov}} \\ I_{\mathrm{gidl}} = \begin{cases} -\boldsymbol{A}_{\mathbf{GIDLD}} \cdot t \cdot \exp\left(-\dfrac{\boldsymbol{B}_{\mathbf{GIDLD}}}{V_{\mathrm{tov}}}\right) & \text{for } V_{\mathrm{ov}} < 0 \\ 0 & \text{for } V_{\mathrm{ov}} \geq 0 \end{cases} \end{cases} \tag{4.188}$$

$$I_{\mathrm{gisl}} = I_{\mathrm{gisl}}(V_{\mathrm{ov}_0}, V_{\mathrm{SB}}) \tag{4.189}$$

$$I_{\mathrm{gidl}} = I_{\mathrm{gidl}}(V_{\mathrm{ov}_\mathrm{L}}, V_{\mathrm{DS}} + V_{\mathrm{SB}}) \tag{4.190}$$

4.2.15 Total Terminal Currents

$$I_{\mathrm{D}} = I_{\mathrm{DS}} + I_{\mathrm{avl}} - I_{\mathrm{GDov}} - I_{\mathrm{GCD}} + I_{\mathrm{gidl}} \tag{4.191}$$

$$I_{\mathrm{S}} = -I_{\mathrm{DS}} - I_{\mathrm{GSov}} - I_{\mathrm{GCS}} + I_{\mathrm{gisl}} \tag{4.192}$$

$$I_{\mathrm{G}} = I_{\mathrm{GC}} + I_{\mathrm{GB}} + I_{\mathrm{GDov}} + I_{\mathrm{GSov}} \tag{4.193}$$

$$I_{\mathrm{B}} = -I_{\mathrm{avl}} - I_{\mathrm{GB}} - I_{\mathrm{gidl}} - I_{\mathrm{gisl}} \tag{4.194}$$

4.3 Charge Model

4.3.1 Quantum-Mechanical Corrections

$$q_{\mathrm{eff}} = \begin{cases} V_{\mathrm{oxm}} & \text{for } x_{\mathrm{g}} \leq 0 \\ q_{\mathrm{bm}} + \boldsymbol{\eta_\mu} \cdot q_{\mathrm{im}} & \text{for } x_{\mathrm{g}} > 0 \end{cases} \tag{4.195}$$

$$C_{\mathrm{OX}}^{\mathrm{qm}} = \begin{cases} \mathbf{COX} & \text{for } \boldsymbol{q_{\mathrm{q}}} = 0 \\ \dfrac{\mathbf{COX}}{1 + \boldsymbol{q_{\mathrm{q}}}/({q_{\mathrm{eff}}}^2 + {\boldsymbol{q_{\mathrm{lim}}}}^2)^{1/6}} & \text{for } \boldsymbol{q_{\mathrm{q}}} > 0 \end{cases} \tag{4.196}$$

4.3.2 Intrinsic Charge Model

$$\text{if } x_{\mathrm{g}} > 0 \begin{cases} F_{\mathrm{j}} = \Delta\psi / (2 \cdot H) \\ q_{\Delta L} = (1 - G_{\Delta L}) \cdot (q_{\mathrm{im}} - \alpha_{\mathrm{m}} \cdot \Delta\psi/2) \\ q_{\Delta L}^{*} = q_{\Delta L} \cdot (1 + G_{\Delta L}) \\ Q_{\mathrm{G}}^{(i)} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \left[V_{\mathrm{oxm}} + \dfrac{\eta_{\mathrm{p}} \cdot \Delta\psi}{2} \cdot \left(\dfrac{G_{\Delta L}}{3} \cdot F_{\mathrm{j}} + G_{\Delta L} - 1 \right) \right] \\ Q_{\mathrm{I}}^{(i)} = -C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \left[G_{\Delta L} \cdot \left(q_{\mathrm{im}} + \dfrac{\alpha_{\mathrm{m}} \cdot \Delta\psi}{6} \cdot F_{\mathrm{j}} \right) + q_{\Delta L} \right] \\ Q_{\mathrm{D}}^{(i)} = -\dfrac{C_{\mathrm{OX}}^{\mathrm{qm}}}{2} \cdot \left[G_{\Delta L}^2 \cdot \left(q_{\mathrm{im}} + \dfrac{\alpha_{\mathrm{m}} \cdot \Delta\psi}{6} \cdot \left[\dfrac{F_{\mathrm{j}}^2}{5} + F_{\mathrm{j}} - 1 \right] \right) + q_{\Delta L}^{*} \right] \end{cases} \tag{4.197}$$

$$\text{if } x_{\mathrm{g}} \leq 0 \begin{cases} Q_{\mathrm{G}}^{(i)} & = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot V_{\mathrm{oxm}} \\ Q_{\mathrm{I}}^{(i)} & = 0 \\ Q_{\mathrm{D}}^{(i)} & = 0 \end{cases} \tag{4.198}$$

$$Q_{\mathrm{S}}^{(i)} = Q_{\mathrm{I}}^{(i)} - Q_{\mathrm{D}}^{(i)} \tag{4.199}$$

$$Q_{\mathrm{B}}^{(i)} = -Q_{\mathrm{I}}^{(i)} - Q_{\mathrm{G}}^{(i)} \tag{4.200}$$

4.3.3 Extrinsic Charge Model

The charges of the source and drain overlap regions:

$$Q_{\mathrm{sov}} = \mathbf{CGOV} \cdot (V_{\mathrm{GS}} - \psi_{\mathrm{sov}}) \tag{4.201}$$

$$Q_{\mathrm{dov}} = \mathbf{CGOVD} \cdot (V_{\mathrm{GS}} - V_{\mathrm{DS}} - \psi_{\mathrm{dov}}) \tag{4.202}$$

The charge of the bulk overlap region

$$Q_{\mathrm{bov}} = \mathbf{CGBOV} \cdot (V_{\mathrm{GS}} + V_{\mathrm{SB}}) \tag{4.203}$$

Outer fringe charge:

$$Q_{\mathrm{ofs}} = \mathbf{CFR} \cdot V_{\mathrm{GS}} \tag{4.204}$$

$$Q_{\mathrm{ofd}} = \mathbf{CFRD} \cdot (V_{\mathrm{GS}} - V_{\mathrm{DS}}) \tag{4.205}$$

4.3.4 Total Terminal Charges

$$Q_{\rm G} = Q_{\rm G}^{(i)} + Q_{\rm sov} + Q_{\rm dov} + Q_{\rm ofs} + Q_{\rm ofd} + Q_{\rm bov} \tag{4.206}$$

$$Q_{\rm S} = Q_{\rm S}^{(i)} - Q_{\rm sov} - Q_{\rm ofs} \tag{4.207}$$

$$Q_{\rm D} = Q_{\rm D}^{(i)} - Q_{\rm dov} - Q_{\rm ofd} \tag{4.208}$$

$$Q_{\rm B} = Q_{\rm B}^{(i)} - Q_{\rm bov} \tag{4.209}$$

4.4 Noise Model

Eqs. (4.210)-(4.236) are only calculated for $x_\mathrm{g} > 0$. In these equations f_op represents the operation frequency of the transistor and $j = \sqrt{-1}$.

4.4.1 Flicker noise

$$N^* = \frac{C_\mathrm{ox}}{q} \cdot \alpha_\mathrm{m} \cdot \boldsymbol{\phi}_\mathbf{T} \tag{4.210}$$

$$N_\mathrm{m}^* = \frac{C_\mathrm{ox}}{q} \cdot q_\mathrm{im}^* \tag{4.211}$$

$$\Delta N = \frac{C_\mathrm{ox}}{q} \cdot \alpha_\mathrm{m} \cdot \Delta\psi \tag{4.212}$$

$$S_\mathrm{fl} = \frac{q \cdot \boldsymbol{\phi}_\mathbf{T}^2 \cdot \boldsymbol{\beta} \cdot I_\mathrm{DS}}{f_\mathrm{op}^\mathbf{EF} \cdot C_\mathrm{ox} \cdot G_\mathrm{vsat} \cdot N^*} \cdot \left[(\mathbf{NFA} - \mathbf{NFB} \cdot N^* + \mathbf{NFC} \cdot N^{*\,2}) \cdot \ln\left(\frac{N_\mathrm{m}^* + \Delta N/2}{N_\mathrm{m}^* - \Delta N/2}\right) \right.$$
$$\left. + \Big(\mathbf{NFB} + \mathbf{NFC} \cdot [N_\mathrm{m}^* - 2 \cdot N^*]\Big) \cdot \Delta N \right] \tag{4.213}$$

4.4.2 Thermal noise

Intrinsic thermal noise

$$H_0 = \frac{q_\mathrm{im}^*}{\alpha_\mathrm{m}} \tag{4.214}$$

$$t_1 = \frac{q_\mathrm{im}}{q_\mathrm{im}^*} \tag{4.215}$$

$$t_2 = \left(\frac{\Delta\psi}{12 \cdot H_0}\right)^2 \tag{4.216}$$

$$R = \frac{H_0}{H} - 1 \tag{4.217}$$

$$l_\mathrm{c} = 1 - 12 \cdot t_2 \cdot R \tag{4.218}$$

$$g_\mathrm{ideal} = \frac{\boldsymbol{\beta} \cdot q_\mathrm{im}^*}{G_\mathrm{vsat}} \cdot F_{\Delta L} \tag{4.219}$$

$$C_\mathrm{Geff} = \left(\frac{G_\mathrm{vsat}}{G_\mathrm{mob} \cdot G_{\Delta L}}\right)^2 \cdot C_\mathrm{OX}^\mathrm{qm} \cdot \eta_\mathrm{p} \tag{4.220}$$

$$m_\mathrm{id,int} = \frac{g_\mathrm{ideal}}{l_\mathrm{c}^2} \cdot [t_1 + 12 \cdot t_2 - 24 \cdot (1 + t_1) \cdot t_2 \cdot R] \tag{4.221}$$

$$m_\mathrm{ig,int} = \frac{1}{l_\mathrm{c}^2 \cdot g_\mathrm{ideal}} \cdot \left[\frac{t_1}{12} - t_2 \cdot \left(t_1 + \frac{1}{5} - 12 \cdot t_2\right) - \frac{8}{5} \cdot t_2 \cdot (t_1 + 1 - 12 \cdot t_2) \cdot R\right] \tag{4.222}$$

$$m_\mathrm{igid,int} = \frac{\sqrt{t_2}}{l_\mathrm{c}^2} \cdot \left[1 - 12 \cdot t_2 - \left(t_1 + \frac{96}{5} \cdot t_2 - 12 \cdot t_1 \cdot t_2\right) \cdot R\right] \tag{4.223}$$

Excess thermal noise

For short (sub-100-nm) devices, it has been shown that the conventional local source for thermal noise gets a field dependent extra term [7, 8] and changes from

$$\langle i_\mathrm{n}^2 \rangle = 4 \cdot k \cdot T \cdot g$$

to

$$\langle i_\mathrm{n}^2 \rangle = 4 \cdot k \cdot T \cdot g \cdot \left[1 + 3 \cdot \frac{(q \cdot E \cdot \tau)^2}{m^* \cdot k \cdot T} \right] = 4 \cdot k \cdot T \cdot g + 12 \cdot g \cdot m^* \cdot \mu^2 \cdot E^2.$$

Here, g denotes the local channel conductance. Integration along the channel (following the improved Klaassen-Prins method) leads to expressions for the drain-current noise, induced gate noise, and correlation.

Excess thermal noise equations:

$$\theta^*_\mathrm{sat,exc} = \begin{cases} \dfrac{\boldsymbol{\theta}_\mathbf{sat}}{G_\mathrm{mob,dc}} \cdot (1 + \mathbf{THESATG} \cdot w_\mathrm{sat}) & \text{for } \mathbf{THESATG} \geq 0 \\[2ex] \dfrac{\boldsymbol{\theta}_\mathbf{sat}}{G_\mathrm{mob,dc}} \cdot \dfrac{1}{1 - \mathbf{THESATG} \cdot w_\mathrm{sat}} & \text{for } \mathbf{THESATG} < 0 \end{cases} \tag{4.224}$$

$$z_\mathrm{sat,exc} = \begin{cases} \left(\theta^*_\mathrm{sat,exc} \cdot \Delta\psi_\mathrm{dc}\right)^2 & \text{for NMOS} \\[2ex] \dfrac{\left(\theta^*_\mathrm{sat,exc} \cdot \Delta\psi_\mathrm{dc}\right)^2}{1 + \theta^*_\mathrm{sat,exc} \cdot \Delta\psi_\mathrm{dc}} & \text{for PMOS} \end{cases} \tag{4.225}$$

$$G_\mathrm{vsat,exc} = \frac{G_\mathrm{mob,dc}}{2} \cdot \left(1 + \sqrt{1 + 2 \cdot z_\mathrm{sat,exc}}\right) \tag{4.226}$$

$$g_\mathrm{fac} = \frac{G_\mathrm{mob,dc}}{G_\mathrm{vsat,exc} \cdot l_\mathrm{c}} \tag{4.227}$$

$$m_\mathrm{id,exc} = \frac{\mathbf{FNTEXC} \cdot m_0}{4 \cdot k_\mathrm{B} \cdot T_\mathrm{KD}} \cdot g_\mathrm{fac}^2 \cdot I_\mathrm{DS} \cdot V_\mathrm{dse,dc} \tag{4.228}$$

$$m_\mathrm{ig,exc} = m_\mathrm{id,exc} \cdot \frac{1 + 12 \cdot t_2}{12 \cdot g_\mathrm{ideal}^2} \tag{4.229}$$

$$m_\mathrm{igid,exc} = -m_\mathrm{id,exc} \cdot \frac{\sqrt{t_2} \cdot (1 + R)}{g_\mathrm{ideal}} \tag{4.230}$$

Total thermal noise

$$m_\mathrm{id} = m_\mathrm{id,int} + m_\mathrm{id,exc} \tag{4.231}$$

$$m_\mathrm{ig} = m_\mathrm{ig,int} + m_\mathrm{ig,exc} \tag{4.232}$$

$$m_\mathrm{igid} = m_\mathrm{igid,int} + m_\mathrm{igid,exc} \tag{4.233}$$

$$S_\mathrm{id} = \boldsymbol{N}_\mathbf{T} \cdot m_\mathrm{id} \tag{4.234}$$

$$S_\mathrm{ig} = \boldsymbol{N}_\mathbf{T} \cdot \frac{(2 \cdot \pi \cdot f_\mathrm{op} \cdot C_\mathrm{Geff})^2 \cdot m_\mathrm{ig}}{1 + (2 \cdot \pi \cdot f_\mathrm{op} \cdot C_\mathrm{Geff} \cdot m_\mathrm{ig})^2} \tag{4.235}$$

$$S_\mathrm{igid} = \boldsymbol{N}_\mathbf{T} \cdot \frac{2 \cdot \pi \cdot j \cdot f_\mathrm{op} \cdot C_\mathrm{Geff} \cdot m_\mathrm{igid}}{1 + 2 \cdot \pi \cdot j \cdot f_\mathrm{op} \cdot C_\mathrm{Geff} \cdot m_\mathrm{ig}} \tag{4.236}$$

Thermal noise for parasitic resistances (see Fig. 3.2)

$$S_{\mathrm{R_G}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{gate}} \tag{4.237}$$

$$S_{\mathrm{R_{BULK}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{bulk}} \tag{4.238}$$

$$S_{\mathrm{R_{WELL}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{well}} \tag{4.239}$$

$$S_{\mathrm{R_{JUNS}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{juns}} \tag{4.240}$$

$$S_{\mathrm{R_{JUND}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{jund}} \tag{4.241}$$

4.4.3 Shot noise

Gate current shot noise:

$$S_{\mathrm{igs}} = 2 \cdot q \cdot (I_{\mathrm{GCS}} + I_{\mathrm{GSov}}) \tag{4.242}$$

$$S_{\mathrm{igd}} = 2 \cdot q \cdot (I_{\mathrm{GCD}} + I_{\mathrm{GDov}}) \tag{4.243}$$

Avalanche current shot noise:

$$S_{\mathrm{avl}} = 2 \cdot q \cdot (1 + M_{\mathrm{avl}}) \cdot I_{\mathrm{avl}} \tag{4.244}$$

Section 5

Non-quasi-static RF model

5.1 Introduction

For high-frequency modeling and fast transient simulations, a special version of the PSP model is available, which enables the simulation of non-quasi-static (NQS) effects, and includes several parasitic resistances.

5.2 NQS-effects

In the PSP-NQS model, NQS-effects are introduced by applying the one-dimensional current continuity equation ($\partial I/\partial y \propto -\partial \rho/\partial t$) to the channel. A full numerical solution of this equation is too inefficient for compact modeling, therefore an approximate technique is used. The channel is partitioned into $N+1$ sections of equal length by assigning N equidistant *collocation points*. The charge density (per unit channel area) along the channel is then approximated by a cubic spline through these collocation points, assuring that both the charge and its first and second spatial derivatives are continuous along the channel. Within this approximation, the current continuity equation reduces to a system of N coupled first order ordinary differential equations, from which the channel charge at each collocation point can be found:

$$\left\{\begin{array}{rcl} \dfrac{\mathrm{d}Q_1}{\mathrm{d}t} & = & f_1(Q_1,\ldots,Q_N) \\ \vdots & & \vdots \\ \dfrac{\mathrm{d}Q_N}{\mathrm{d}t} & = & f_N(Q_1,\ldots,Q_N) \end{array}\right. \tag{5.1}$$

Here, Q_i is the charge density at the i-th collocation point and f_i are functions, which contain the *complete* PSP-charge model. These equations are implemented by the definition of appropriate subcircuits (see left part of Fig. 5.1) and solved by the circuit simulator. Finally, the four terminal charges are calculated from the channel charges, using the Ward-Dutton partitioning scheme for the source and drain charges.

A full description of the PSP-NQS model is given in Section 5.3. More background information can be found in literature [9, 10].

5.3 NQS Model Equations

In this section, several symbols and notations are used which were defined in Section 4. Moreover, y denotes the (normalized) position along the channel ($y = 0$ is source side, $y = 1$ is drain side), while x denotes the surface potential (normalized to ϕ_T^*) at a certain position.

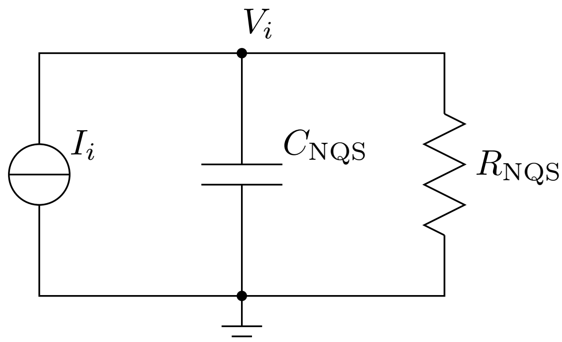

Figure 5.1: The subcircuit used to solve one of the differential equations of Eq. (5.1). The current is set to $I_i = C_{\mathrm{NQS}} \cdot f(V_1, \ldots, V_N)$, where the voltage V_i represents the charge density Q_i at the i-th collocation point and is solved by the circuit simulator. N of these circuits are defined and they are coupled through the dependence of I_i on the voltages of the other circuits. The resistance R_{NQS} has a very large value and is present only for convergence purposes. *Right:* The full network of parasitic elements in the PSP-NQS model. The large full dots indicate the five additional internal nodes.

5.3.1 Internal constants

Eqs. (5.2)–(5.7) are independent of bias conditions and time. Consequently, they have to be computed only once.

Note: In PSP only **SWNQS** $= 0, 1, 2, 3, 5, 9$ are allowed!

$$n = \textbf{SWNQS} + 1 \tag{5.2}$$

$$h = 1/n \tag{5.3}$$

The matrix A is a square $(n+1) \times (n+1)$-matrix with elements $A_{i,j}$ $(0 \leq i, j \leq n)$, which are used in Eq. 5.25. They are computed using the following algorithm (adapted from [11]):

1. Initial values:

$$A_{i,j} = 0 \qquad \text{for } 0 \leq i, j \leq n \tag{5.4}$$

$$v_i = 0 \qquad \text{for } 0 \leq i \leq n \tag{5.5}$$

2. First loop:

$$\left.\begin{aligned} & p = 2 + v_{i-1}/2 \\ & v_i = -1/(2 \cdot p) \\ & A_{i,i-1} = 1/h \\ & A_{i,i} = -2/h \\ & A_{i,i+1} = 1/h \\ & A_{i,j} = \frac{1}{p} \cdot (3 \cdot A_{i,j}/h - A_{i-1,j}/2) \quad \Big\} \text{for } j = 0 \ldots n \end{aligned}\right\} \text{for } i = 1 \ldots (n-1) \tag{5.6}$$

3. Second loop (back substitution):

$$\left. A_{i,j} = v_i \cdot A_{i+1,j} + A_{i,j} \qquad \text{for } j = 0 \dots n \right\} \text{for } i = (n-1) \dots 0 \tag{5.7}$$

5.3.2 Position independent quantities

The following quantities depend on the bias conditions, but are constant along the channel:

$$\text{if } x_\mathrm{g} > 0 \begin{cases} y_\mathrm{m} = \dfrac{1}{2} \cdot \left(1 + \dfrac{\Delta\psi}{4 \cdot H}\right) \\[2ex] p_\mathrm{d} = \dfrac{x_\mathrm{gm}}{x_\mathrm{g} - x_\mathrm{m}} \\[2ex] G_\mathrm{p} = G / p_\mathrm{d} \end{cases} \tag{5.8}$$

$$\text{if } x_\mathrm{g} \leq 0 \begin{cases} y_\mathrm{m} = 1/2 \\ p_\mathrm{d} = 1 \\ G_\mathrm{p} = G \end{cases} \tag{5.9}$$

$$a_\mathrm{p} = 1 + G_\mathrm{p} / \sqrt{2} \tag{5.10}$$

$$p_\mathrm{mrg} = 10^{-5} \cdot a_\mathrm{p} \tag{5.11}$$

5.3.3 Position dependent surface potential and charge

Interpolated (quasi-static) surface potential along the channel:

$$\Psi(y) = x_\mathrm{m} + \frac{H}{\boldsymbol{\phi}_\mathbf{T}^*} \cdot \left(1 - \sqrt{1 - \frac{2 \cdot \Delta\psi}{H} \cdot (y - y_\mathrm{m})}\right) \tag{5.12}$$

Normalized bulk-charge and its first two derivatives as functions of surface potential:

$$q_\mathrm{b}(x) = -\mathrm{sgn}(x) \cdot G_\mathrm{p} \cdot \sqrt{\exp(-x) + x - 1} \tag{5.13}$$

$$q_\mathrm{b}'(x) = \frac{G_\mathrm{p}^2 \cdot [1 - \exp(-x)]}{2 \cdot q_\mathrm{b}(x)} \tag{5.14}$$

$$q_\mathrm{b}''(x) = -q_\mathrm{b}'(x) - \frac{q_\mathrm{b}'(x)^2 - G_\mathrm{p}^2/2}{q_\mathrm{b}(x)} \tag{5.15}$$

Surface potential as a function of normalized inversion charge (note that these equations are identical to Eq. (4.163), despite the different notation and physical background):

$$\Pi(x_\mathrm{g}) = \begin{cases} \text{if } x_\mathrm{g} < -p_\mathrm{mrg} & \begin{cases} y_\mathrm{g} = -x_\mathrm{g} \\ z = 1.25 \cdot y_\mathrm{g}/a_\mathrm{p} \\ \eta = \left[z + 10 - \sqrt{(z-6)^2 + 64}\right]/2 \\ a = \left(y_\mathrm{g} - \eta\right)^2 + G_\mathrm{p}^2 \cdot (\eta + 1) \\ c = 2 \cdot (y_\mathrm{g} - \eta) - G_\mathrm{p}^2 \\ \tau = -\eta + \ln\left(a/G_\mathrm{p}^2\right) \\ y_0 = \sigma_1(a,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp(y_0) \\ \xi = 1 - G_\mathrm{p}^2 \cdot \Delta_0/2 \\ p = 2 \cdot (y_\mathrm{g} - y_0) + G_\mathrm{p}^2 \cdot (\Delta_0 - 1) \\ q = \left(y_\mathrm{g} - y_0\right)^2 + G_\mathrm{p}^2 \cdot (y_0 - \Delta_0 + 1) \\ \Pi = -y_0 - \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot q \cdot \xi}} \end{cases} \\ \text{if } |x_\mathrm{g}| \leq p_\mathrm{mrg} & \begin{cases} \Pi = \dfrac{x_\mathrm{g}}{a_\mathrm{p}} \end{cases} \\ \text{if } x_\mathrm{g} > p_\mathrm{mrg} & \begin{cases} \hat{x}_\mathrm{g1} = \boldsymbol{x_1} + G \cdot \sqrt{\exp(-\boldsymbol{x_1}) + \boldsymbol{x_1} - 1} \\ \bar{x} = \dfrac{x_\mathrm{g}}{a_\mathrm{p}} \cdot \left[1 + x_\mathrm{g} \cdot (\boldsymbol{x_1} \cdot a_\mathrm{p}/\hat{x}_\mathrm{g1} - 1)/\hat{x}_\mathrm{g1}\right] \\ x_0 = x_\mathrm{g} + G_\mathrm{p}^2/2 - G_\mathrm{p} \cdot \sqrt{x_\mathrm{g} + G_\mathrm{p}^2/4 - 1 + \exp(-\bar{x})} \\ \Delta_0 = \exp(-x_0) \\ \xi = 1 - G_\mathrm{p}^2 \cdot \Delta_0/2 \\ p = 2 \cdot (x_\mathrm{g} - x_0) + G_\mathrm{p}^2 \cdot (1 - \Delta_0) \\ q = (x_\mathrm{g} - x_0)^2 - G_\mathrm{p}^2 \cdot (x_0 + \Delta_0 - 1) \\ \Pi = x_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot q \cdot \xi}} \end{cases} \end{cases} \tag{5.16}$$

$$X(x_\mathrm{g}, q_\mathrm{inv}) = \Pi(x_\mathrm{g} + q_\mathrm{inv}/p_\mathrm{d}) \tag{5.17}$$

Auxiliary functions:

$$q(x) = -p_\mathrm{d} \cdot (x_\mathrm{g} - x) - q_\mathrm{b}(x) \tag{5.18}$$

$$\psi(q, q_{x1}) = \frac{q}{q_{x1}} - 1 \tag{5.19}$$

$$\phi(q, q_{x1}, q_{x2}) = \left(1 - \frac{q \cdot q_{x2}}{q_{x1}^2}\right)/q_{x1} \tag{5.20}$$

Normalized right-hand-side of continuity equation:

$$f(x_\mathrm{g}, q, q', q'') = \begin{cases} x_\mathrm{z} = X(x_\mathrm{g}, q) \\ q_{x1} = \dfrac{\partial q}{\partial x}(x_\mathrm{z}) = p_\mathrm{d} - q_\mathrm{b}'(x_\mathrm{z}) \\ q_{x2} = \dfrac{\partial^2 q}{\partial x^2}(x_\mathrm{z}) = q_\mathrm{b}''(x_\mathrm{z}) \\ f_0 = \psi(q, q_{x1}) \cdot q'' + \phi(q, q_{x1}, q_{x2}) \cdot q'^2 \\ x_{y1} = \dfrac{\partial x_\mathrm{z}}{\partial y} = q'/q_{x1} \\ z_\mathrm{sat} = \begin{cases} \left(\theta_\mathrm{sat}^* \cdot \boldsymbol{\phi}_\mathbf{T}^* \cdot x_{y1}\right)^2 & \text{for NMOS} \\ \dfrac{\left(\theta_\mathrm{sat}^* \cdot \boldsymbol{\phi}_\mathbf{T}^* \cdot x_{y1}\right)^2}{1 + \theta_\mathrm{sat}^* \cdot \Delta\psi} & \text{for PMOS} \end{cases} \\ \zeta = \sqrt{1 + 2 \cdot z_\mathrm{sat}} \\ F_\mathrm{vsat} = 2/(1+\zeta) \\ f = F_\mathrm{vsat} \cdot \left[f_0 - F_\mathrm{vsat} \cdot \dfrac{z_\mathrm{sat}}{\zeta} \cdot \psi(q, q_{x1}) \cdot (q'' + x_{y1}^2 \cdot q_\mathrm{b}''(x_\mathrm{z}))\right] \end{cases} \tag{5.21}$$

Normalization constant:

$$T_\mathrm{norm} = \frac{\mathbf{MUNQS} \cdot \boldsymbol{\phi}_\mathbf{T}^* \cdot \boldsymbol{\beta}}{C_\mathrm{OX}^\mathrm{qm} \cdot G_\mathrm{mob} \cdot G_{\Delta L}} \tag{5.22}$$

5.3.4 Cubic spline interpolation

Using cubic spline interpolation, the spatial derivatives $\frac{\partial q_i}{\partial y}(t)$ and $\frac{\partial^2 q_i}{\partial y^2}(t)$ can be expressed as functions of the $q_i(t)$.

$$q_0'' = 0 \tag{5.23}$$

$$q_n'' = 0 \tag{5.24}$$

$$q_i'' = \sum_{j=0}^{n} A_{i,j} \cdot q_i \qquad \text{for } 1 \le i \le n-1 \tag{5.25}$$

$$q_i' = \frac{q_{i+1} - q_i}{h} - \frac{h}{6} \cdot (2 \cdot q_i'' + q_{i+1}'') \qquad \text{for } 1 \le i \le n-1 \tag{5.26}$$

5.3.5 Continuity equation

Initial value for the q_i ($0 \le i \le n$). These values are used for the DC operating point.

$$x_{i,0} = \Psi(i \cdot h) \tag{5.27}$$

$$q_{i,0} = q(x_{i,0}) \tag{5.28}$$

Note: $x_{0,0} = x_\mathrm{s}$ and $x_{n,0} = x_\mathrm{d}$. Moreover, these values coincide with those in the quasi-static part of PSP.

The core of the NQS-model is the solution of $q(y,t)$ from the charge continuity equation along the channel. By approximating the y-dependence by a cubic spline through a number of collocation points, the problem is reduced to solving the $q_i(t)$ from the following set of coupled differential equations.

$$\boxed{\begin{cases} \dfrac{\partial q_i}{\partial t}(t) + T_\mathrm{norm} \cdot f\left(x_\mathrm{g},\, q_i(t),\, \dfrac{\partial q_i}{\partial y}(t),\, \dfrac{\partial^2 q_i}{\partial y^2}(t)\right) = 0 & \text{for } 1 \le i \le n-1 \\ q_i(0) = q_{i,0} & \end{cases}} \tag{5.29}$$

Note that the boundary points $q_0(t) = q(x_\mathrm{s}) = q_\mathrm{is}$ and $q_n(t) = q(x_\mathrm{d}) = q_\mathrm{id}$ remain fixed to their quasi-static values; they are not solved from the equation above.

The set of differential equations defined above is solved by the circuit simulator via the subcircuits shown in the left part of Fig. 5.1.

5.3.6 Non-quasi-static terminal charges

Once the q_i are known, the NQS terminal charges can be computed:

$$S_0 = \sum_{i=1}^{n-1} q_i \tag{5.30}$$

$$S_2 = \sum_{i=1}^{n-1} q_i'' \tag{5.31}$$

$$q_\mathrm{I}^\mathrm{NQS} = \int_0^1 q(y)\,\mathrm{d}y = h \cdot S_0 + \frac{h}{2} \cdot (u_0 + u_n) - \frac{h^3}{12} \cdot S_2 \tag{5.32}$$

$$U_0 = \sum_{i=1}^{n-1} i \cdot q_i \tag{5.33}$$

$$U_2 = \sum_{i=1}^{n-1} i \cdot q_i'' \tag{5.34}$$

$$q_\mathrm{D}^\mathrm{NQS} = \int_0^1 y \cdot q(y)\,\mathrm{d}y = h^2 \cdot U_0 + \frac{h^2}{6} \cdot [q_0 + (3n-1)u_n] - \frac{h^4}{12} \cdot U_2 \tag{5.35}$$

$$q_\mathrm{S}^\mathrm{NQS} = q_\mathrm{I}^\mathrm{NQS} - q_\mathrm{D}^\mathrm{NQS} \tag{5.36}$$

Currently, only **SWNQS** $= 0, 1, 2, 3, 5, 9$ are allowed. For odd values of **SWNQS** the gate charge is integrated along the channel using “Simpson’s rule”. If **SWNQS** $= 2$, “Simpson’s $3/8$-rule” is used.

- If **SWNQS** is odd (that is, n is even):

$$q_\mathrm{G}^\mathrm{NQS} = p_\mathrm{d} \cdot \left[x_\mathrm{g} - \frac{h}{3} \cdot \left(X(x_\mathrm{g}, q_0) + 4 \cdot \sum_{i=1}^{n/2} X(x_\mathrm{g}, q_{2i-1}) + \right.\right.$$
$$\left.\left. 2 \cdot \sum_{i=1}^{n/2-1} X(x_\mathrm{g}, q_{2i}) + X(x_\mathrm{g}, q_n)\right)\right] \tag{5.37}$$

- If **SWNQS** $= 2$ (that is, $n = 3$):

$$q_{\mathrm{G}}^{\mathrm{NQS}} = p_{\mathrm{d}} \cdot \left[x_{\mathrm{g}} - \frac{3 \cdot h}{8} \cdot (X(x_{\mathrm{g}}, q_0) + 3 \cdot X(x_{\mathrm{g}}, q_1) + 3 \cdot X(x_{\mathrm{g}}, q_2) + X(x_{\mathrm{g}}, q_3)) \right] \tag{5.38}$$

Convert back to conventional units:

$$Q_{\mathrm{S}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{S}}^{\mathrm{NQS}} \tag{5.39}$$

$$Q_{\mathrm{D}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{D}}^{\mathrm{NQS}} \tag{5.40}$$

$$Q_{\mathrm{G}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{G}}^{\mathrm{NQS}} \tag{5.41}$$

$$Q_{\mathrm{B}}^{\mathrm{NQS}} = -(Q_{\mathrm{S}}^{\mathrm{NQS}} + Q_{\mathrm{D}}^{\mathrm{NQS}} + Q_{\mathrm{G}}^{\mathrm{NQS}}) \tag{5.42}$$

Section 6

Embedding

6.1 Model selection

Circuit simulators have different ways for the user to determine which model must be used for simulation. Typically, model selection is either done by *name* or by assigning a value to the parameter **LEVEL**. The method to be used is prescribed by the circuit simulator vendor. If selection is done by name, the value of the parameter **LEVEL** is generally ignored. When Verilog-A code is used, model selection is always done by name.

For the SiMKit and the Verilog-A code provided by the PSP model developers, the method and values to be used are given in the table below. For other implementations, the method/value provided by the circuit simulator vendor is to be used.

Simulator	Model selection by	Global (geom.)	Global (binning)	Local
Spectre	name	`psp1020`	`psp1021`	`psp102e`
Pstar	**LEVEL**	1020	1021	102
ADS	name	`psp1020`	`psp1021`	`psp102e`
Verilog-A	name	`PSP102VA`	`PSP102BVA`	`PSP102EVA`

6.2 Case of parameters

Throughout this document, all parameter names are printed in uppercase characters. Similarly, in the Verilog-A code provided by the PSP model developers, the parameters are in upper case characters. However, in other PSP implementations a different choice can be made. For example, the parameter names may be in lowercase characters (possibly first character capitalized) if this is conform the conventions of the circuit simulator.

6.3 Embedding PSP in a Circuit Simulator

In CMOS technologies both n- and p-channel MOS transistors are supported. It is convenient to use the same set of equations for both types of transistor instead of two separate models. This is accomplished by mapping a p-channel device with its bias conditions and parameter set onto an equivalent n-channel device with appropriately changed bias conditions (i.e. currents, voltages and charges) and parameters. In this way both types of transistor can be treated internally as an n-channel transistor. Nevertheless, the electrical behavior of electrons and holes is not exactly the same (e.g., the mobility and tunneling behavior), and consequently slightly different equations have to be used in case of n- or p-type transistors.

Designers are used to the standard terminology of source, drain, gate and bulk. Therefore, in the context of a circuit simulator it is traditionally possible to address, say, the drain of MOST number 17, even if in reality the corresponding source is at a higher potential (n-channel case). More strongly, most circuit simulators provide for model evaluation values for $V_{\rm DS}$, $V_{\rm GS}$, and $V_{\rm SB}$ based on an a priori assignment of source, drain, and bulk, independent of the actual bias conditions. Since PSP assumes that saturation occurs at the drain side of the MOSFET, the basic model cannot cope with bias conditions that correspond to $V_{\rm DS} < 0$. Again a transformation of the bias conditions is necessary. In this case, the transformation corresponds to internally reassigning source and drain, applying the standard electrical model, and then reassigning the currents and charges to the original terminals. In PSP care has been taken to preserve symmetry with respect to drain and source at $V_{\rm DS} = 0$. In other words, no singularities will occur in the higher-order derivatives at $V_{\rm DS} = 0$.

In detail, for correct embedding of PSP into a circuit simulator, the following procedure—illustrated in Fig. 6.1—is followed. It is assumed that the simulator provides the nodal potentials $V_{\rm D}^e$, $V_{\rm G}^e$, $V_{\rm S}^e$ and $V_{\rm B}^e$ based on an a priori assignment of drain, gate, source and bulk.

Step 1 The voltages $V'_{\rm DS}$, $V'_{\rm GS}$, and $V'_{\rm SB}$ are calculated from the nodal potentials provided by the circuit simulator. In the same step, the value of the parameter **TYPE** is used to deal with the polarity of the device. From here onwards, all transistors can be treated as n-channel devices.

Step 2 Depending on the sign of $V'_{\rm DS}$, 'source-drain interchange' is performed. At this level, the voltages comply to all the requirements for input quantities of PSP.

Step 3 All the internal output quantities (i.e. channel current, weak-avalanche current, gate current, nodal charges, and noise-power spectral densities) are evaluated using the standard PSP equations (Section 4) and the internal voltages.

Step 4 The internal output quantities are corrected for a possible source-drain interchange.

Step 5 External output are corrected for a possible p-channel transformation and **MULT** is applied. The quantities of the intrinsic MOSFET and the junctions are combined.

In general, separate parameter sets are used for n- and p-channel transistors, which are distinguished by the value of **TYPE**. As a consequence, the changes in the parameter values necessary for a p-channel type transistor are normally already included in the parameter sets on file. The changes should therefore not be included in the simulator.

6.3.1 Selection of device type

In the SiMKit-based and built-in version of PSP in certain circuit simulators, the selection of device type (nmos or pmos) is done using a different parameter, or using different parameter values. The correct values for some circuit simulators are given in the table below.

Simulator	Parameter	Value NMOS	value PMOS
Spectre	`type`	n	p
Pstar	`type`	1	-1
ADS	`gender`	1	0
Verilog-A	`TYPE`	1	-1

6.4 Integration of JUNCAP2 in PSP

Introduction

The JUNCAP2 model 200.3 is an integral part of PSP 102.2. In addition, it is available as a stand-alone model. A complete description of the JUNCAP2-model (including all model equations) can be found in the

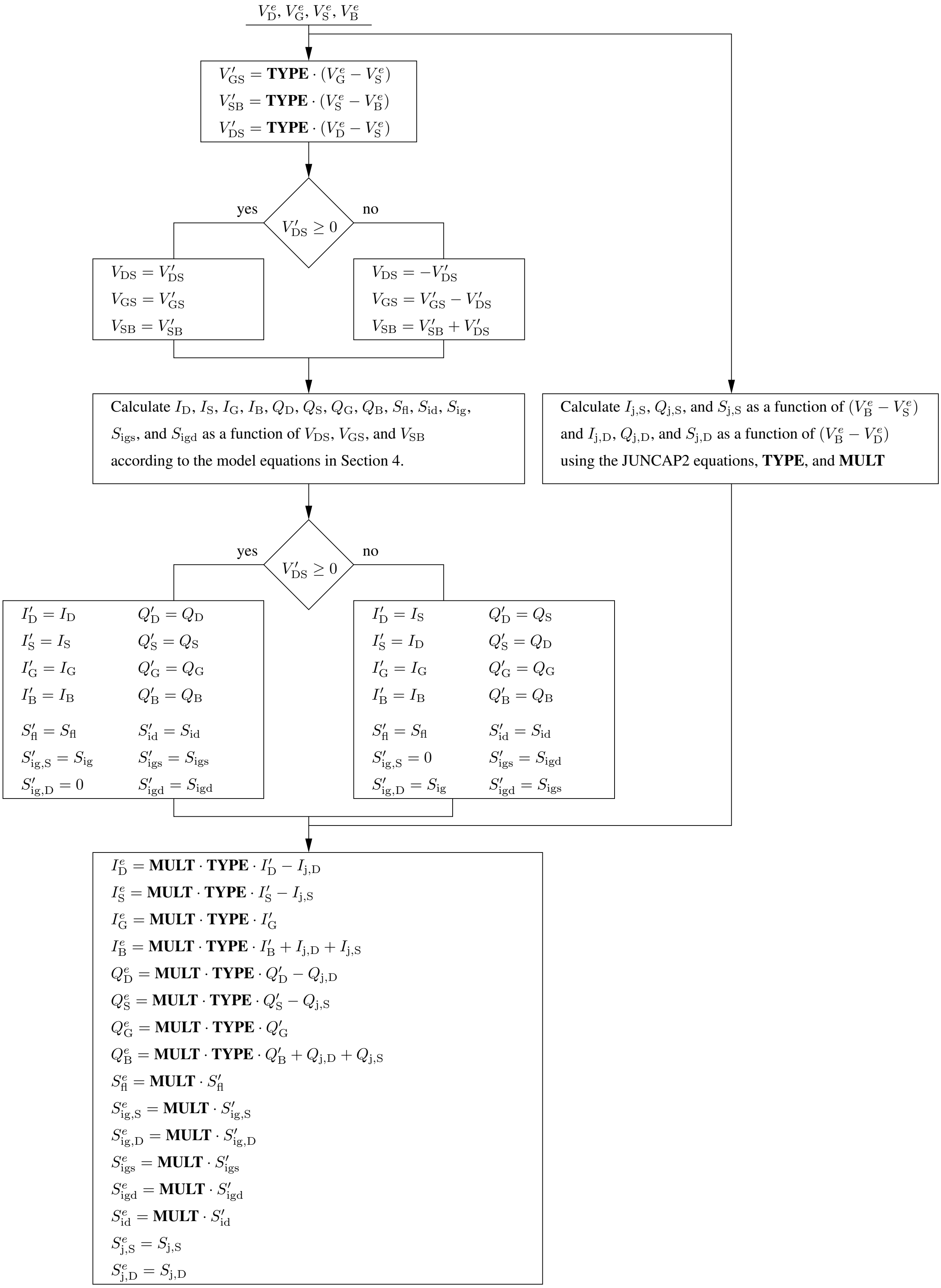

Figure 6.1: Schematic overview of source-drain interchange and handling of **TYPE** and **MULT**. Note that **TYPE** and **MULT** are included in the JUNCAP2 model equations.

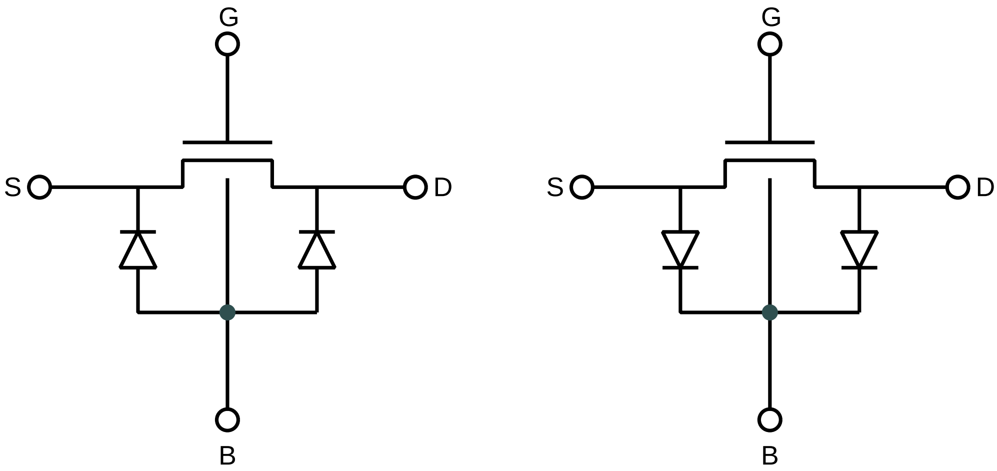

Figure 6.2: Topology of the PSP model. *Left:* n-channel MOSFET; *Right:* p-channel MOSFET. In PSP, the correct diode polarity is automatically chosen via the **TYPE**-parameter.

documentation of JUNCAP2's stand alone version [12]. In this section, only the integration of JUNCAP2 in PSP is described.

Topology

In a MOS transistor, there are two junctions: one between source and bulk, and one between drain and bulk. In case of an n-channel MOSFET, the junction anode corresponds to the MOSFET bulk terminal, and the junction cathodes correspond to the source and the drain. In case of a p-channel MOSFET, it is the other way around: now the junction cathode corresponds to the MOSFET bulk terminal, and the junction anodes correspond to the source and the drain. The connections are schematically given in Fig. 6.2. In PSP, this change of junction terminal connections in case of a p-MOSFET is handled automatically via the **TYPE** parameter.

In most cases, the MOSFET is operated in such a way that the junctions are either biased in the reverse mode of operation or not biased at all. In some applications, however, the source-bulk junction has a small forward bias. This is also the case in partially depleted SOI (PDSOI).

As indicated in Fig. 6.1, the interchange of source and drain for $V_{\mathrm{DS}} < 0$ (as explained above for the intrinsic MOS model) does *not* apply to the junctions. For example, **ABDRAIN** always refers to junction between the bulk and the terminal known as 'drain' to the simulator, independent of the sign of V_{DS}.

Global and local model level

As explained in the introduction, the PSP model has a local and a global level. The JUNCAP2 model is a geometrically scaled model, i.e. it is valid for a range of junction geometries (as described by the geometrical parameters **AB**, **LS**, and **LG**). It has turned out that it is very unnatural to create a local parameter set for JUNCAP2, valid for one particular junction geometry: such a parameter set would have as many parameters as the global parameter set, and would be of no use. (Note that, in contrast, the local model for the intrinsic MOSFET is very useful in, e.g., parameter extraction; this is not the case for JUNCAP2.)

Therefore, the JUNCAP2 model is connected in exactly the same way to both the local and global model levels of PSP. That means that the resulting PSP local model is valid for a MOSFET with one particular channel width and length, but with arbitrary junction geometry.

Parameters

Both junctions in the MOSFET are modeled with the same set of JUNCAP2 parameters. In the PSP model, the geometrical parameters **AB**, **LS**, and **LG** need to be specified for both source and drain. They will be denoted as **ABSOURCE**, **LSSOURCE**, and **LGSOURCE** for the source junction, and **ABDRAIN**, **LSDRAIN**, and **LGDRAIN** for the drain junction. For compatibility with BSIM instance parameters, there is also an option to use **AS**, **AD**, **PS**, and **PD**. The complete list of instance parameters (PSP and JUNCAP2) can be found in Sections 2.5.1 and 2.5.2.

The parameter **MULT** is merged with the parameter **MULT** of the intrinsic MOSFET model. In other words, both intrinsic currents, charges, and noise as well as junction currents, charges and noise are multiplied by one single parameter **MULT**. Beside **MULT**, also the parameters **DTA** and **TYPE** are shared by the intrinsic MOSFET model and the junction model. For clarity, we mention here that the reference temperatures of the intrinsic MOSFET model and junction model are *not* merged; they each have their own value and name (**TR** and **TRJ**, respectively). The currents, charges and spectral noise densities of the source and drain junctions are labeled $I_{\mathrm{j,S}}$, $Q_{\mathrm{j,S}}$, $S_{\mathrm{j,S}}$, $I_{\mathrm{j,D}}$, $Q_{\mathrm{j,D}}$, and $S_{\mathrm{j,D}}$ in Fig. 6.1.

6.5 Verilog-A versus C

As mentioned in Section 1.3, two implementations of the PSP-model are distributed: in Verilog-A language and in C-language (as part of the SiMKit). The C-version is automatically generated from the Verilog-A version by a software package called ADMS [1]. This procedure guarantees that the two implementations contain identical model equations.

Nevertheless, there are a few minor differences between the two, which are due to certain limitations of either the Verilog-A language or the circuit simulators supported in the SiMKit-framework. These differences are described below.

6.5.1 Implementation of GMIN

In both implementations, there is an additional term in Eqs. (4.191) and (4.192), resulting in

$$I_{\mathrm{D}} = I_{\mathrm{DS}} + I_{\mathrm{avl}} - I_{\mathrm{GDov}} - I_{\mathrm{GCD}} + I_{\mathrm{gidl}} + G_{\mathrm{min}} \cdot V_{\mathrm{DS}} \tag{6.1}$$

and

$$I_{\mathrm{S}} = -I_{\mathrm{DS}} - I_{\mathrm{GSov}} - I_{\mathrm{GCS}} + I_{\mathrm{gisl}} - G_{\mathrm{min}} \cdot V_{\mathrm{DS}}. \tag{6.2}$$

In the SiMKit, G_{min} is a variable which is accessible by the circuit simulator. This allows the circuit simulator to improve the convergence properties of a circuit by making use of so-called 'G_{min}-stepping'.

In the Verilog-A version of PSP, G_{min} is set to a fixed value $G_{\mathrm{min}} = 1 \cdot 10^{-15}$ S.[1]

6.5.2 Implementation of parasitic resistances

From PSP 102.2 onwards, a network of parasitic resistors has been inserted around the intrinsic MOSFET. If the user sets one or more of these resistance values to zero, the associated internal node(s) could be shorted to one of its neighbors, reducing the size of the matrix in the circuit simulator. This phenomenon is called 'node collapse' and is supported by most major circuit simulators.

Flexible topology (and thus node collapse) is presently supported by most Verilog-A compilers. As a result, node collapse is functional in the official PSP Verilog-A in the majority of today's circuit simulators.

[1] If supported by the circuit simulator, Verilog-A version 2.2 allows the value of G_{min} to be accessed by the circuit simulator. Once this feature is generally available in Verilog-A compilers, it will be included in PSP as well.

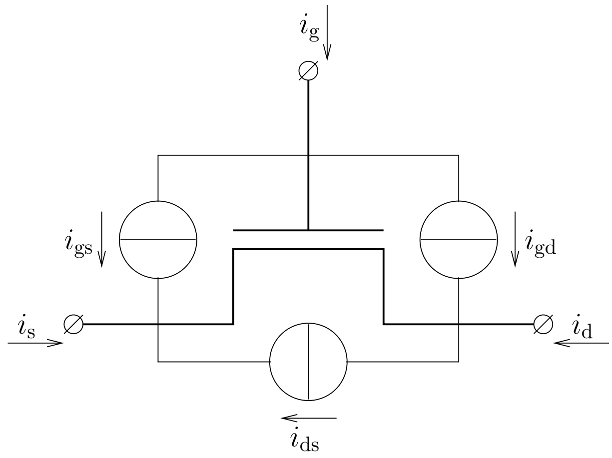

Figure 6.3: Definition of noise currents.

From SiMKit 3.0 onwards, the SiMKit architecture allows for flexible topologies and therefore supports node collapse in PSP. This functionality is therefore available in circuit simulations with that can work with SiMKit. Besides, many circuit simulators that have a native implementation of PSP support node collapse.

6.5.3 Implementation of the noise-equations

Definition of noise model

Eqs. (4.234), (4.235), and (4.236) describe the noise power spectral density of the thermal noise. In this section, the relationship between the quantities S_{id}, S_{ig}, and S_{igid} (as calculated in these equations) and noise sources in the model is defined.

Fig. 6.3 shows a schematic representation of a noiseless transistor (model) and three noise sources. The small-signal noise currents of these noise current sources are indicated by i_{ds}, i_{gs}, and i_{gd}. The two noise sources connected to G are fully correlated. Moreover, each of them is partly correlated with the noise source between S and D. More precisely, the noise powers and correlations associated with these sources are given by

$$\begin{aligned}
\langle i_{\mathrm{ds}} \cdot i_{\mathrm{ds}}^* \rangle &= S_{\mathrm{id}} \\
\langle i_{\mathrm{gd}} \cdot i_{\mathrm{ds}}^* \rangle &= S_{\mathrm{igid}}/2 \\
\langle i_{\mathrm{gs}} \cdot i_{\mathrm{ds}}^* \rangle &= S_{\mathrm{igid}}/2 \\
\langle i_{\mathrm{gd}} \cdot i_{\mathrm{gd}}^* \rangle &= S_{\mathrm{ig}}/4 \\
\langle i_{\mathrm{gs}} \cdot i_{\mathrm{gd}}^* \rangle &= S_{\mathrm{ig}}/4 \\
\langle i_{\mathrm{gs}} \cdot i_{\mathrm{gs}}^* \rangle &= S_{\mathrm{ig}}/4
\end{aligned} \tag{6.3}$$

The non-listed elements follow from the fact that this is a complex correlation matrix and therefore self-adjoint. This defines the noise model of PSP.

For completeness, we will give the noise correlation matrix associated with the *terminal* currents i_{d}, i_{g} and i_{s}, because it is closer related to the numbers that are obtained in a circuit simulation. Because $i_{\mathrm{d}} = i_{\mathrm{ds}} - i_{\mathrm{gs}}$, $i_{\mathrm{g}} = i_{\mathrm{gs}} + i_{\mathrm{gd}}$ and $i_{\mathrm{s}} = i_{\mathrm{gs}} - i_{\mathrm{ds}}$, we find by straightforward substitution and some basic arithmetic

$$\begin{aligned}
\langle i_{\mathrm{d}} \cdot i_{\mathrm{d}}^* \rangle &= S_{\mathrm{id}} + S_{\mathrm{ig}}/4 - \mathrm{Re}(S_{\mathrm{igid}}) \\
\langle i_{\mathrm{g}} \cdot i_{\mathrm{d}}^* \rangle &= S_{\mathrm{igid}} - S_{\mathrm{ig}}/2 \\
\langle i_{\mathrm{s}} \cdot i_{\mathrm{d}}^* \rangle &= -S_{\mathrm{id}} + S_{\mathrm{ig}}/4 - \mathrm{Im}(S_{\mathrm{igid}}) \\
\langle i_{\mathrm{g}} \cdot i_{\mathrm{g}}^* \rangle &= S_{\mathrm{ig}} \\
\langle i_{\mathrm{s}} \cdot i_{\mathrm{g}}^* \rangle &= -S_{\mathrm{igid}}^* - S_{\mathrm{ig}}/2 \\
\langle i_{\mathrm{s}} \cdot i_{\mathrm{s}}^* \rangle &= S_{\mathrm{id}} + S_{\mathrm{ig}}/4 + \mathrm{Re}(S_{\mathrm{igid}})
\end{aligned} \tag{6.4}$$

Verilog-A

In Verilog-A it is not possible to define noise sources that are frequency dependent (except for $1/f$-noise), nor is it possible to directly define correlations between noise sources. Instead, the desired model must be created by using controlled sources and the frequency transfer of passive elements.[2]

The goal is to create the three noise sources shown in Fig. 6.3 with the noise powers (including frequency dependence and correlation) as described by Eq. (6.3).

To simplify notation, we rewrite Eqs. (4.235) and (4.236) as

$$S_{\mathrm{ig}} = \frac{\boldsymbol{N}_{\mathbf{T}}}{m_{\mathrm{ig}}} \cdot |T|^2 \tag{6.5}$$

and

$$S_{\mathrm{igid}} = \frac{\boldsymbol{N}_{\mathbf{T}}}{m_{\mathrm{ig}}} \cdot m_{\mathrm{igid}} \cdot T, \tag{6.6}$$

where

$$T = \frac{j \cdot \omega \cdot \tau}{1 + j \cdot \omega \cdot \tau}, \tag{6.7}$$

$\tau = m_{\mathrm{ig}} \cdot C_{\mathrm{Geff}}$ and ω is the operating frequency.

Correlation between noise sources in verilog-A can be created by making linear combinations of independent sources. Therefore, we start with two *independent* white noise sources with current noise spectral densities S_1 and S_2 and noise currents i_1 and i_2. If we set

$$\begin{aligned} i_{\mathrm{gs}} = i_{\mathrm{gd}} &= \frac{1}{2} \cdot \alpha_1 \cdot i_1 && (6.8)\\ i_{\mathrm{ds}} &= \beta_1 \cdot i_1 + \beta_2 \cdot i_2, && (6.9) \end{aligned}$$

where α_1, β_1, and β_2 are certain (complex) coefficients, we get

$$\begin{aligned} S_{\mathrm{ig}} &= 4 \cdot \langle i_{\mathrm{gd}} \cdot i_{\mathrm{gd}}^* \rangle = |\alpha_1|^2 \cdot \langle i_1 \cdot i_1^* \rangle \\ &= |\alpha_1|^2 \cdot S_1 && (6.10)\\ S_{\mathrm{id}} &= \langle i_{\mathrm{ds}} \cdot i_{\mathrm{ds}}^* \rangle = |\beta_1|^2 \cdot \langle i_1 \cdot i_1^* \rangle + \beta_1 \cdot \beta_2^* \cdot \langle i_1 \cdot i_2^* \rangle + |\beta_2|^2 \cdot \langle i_2 \cdot i_2^* \rangle \\ &= |\beta_1|^2 \cdot S_1 + |\beta_2|^2 \cdot S_2 && (6.11)\\ S_{\mathrm{igid}} &= 2 \cdot \langle i_{\mathrm{gd}} \cdot i_{\mathrm{ds}}^* \rangle = \alpha_1 \cdot \beta_1^* \cdot \langle i_1 \cdot i_1^* \rangle + \alpha_1 \cdot \beta_2^* \cdot \langle i_1 \cdot i_2^* \rangle \\ &= \alpha_1 \cdot \beta_1^* \cdot S_1. && (6.12) \end{aligned}$$

Here we used that the noise currents i_1 and i_2 are independent, such that $\langle i_1 \cdot i_2^* \rangle = 0$. We need to choose proper values for the coefficients α_1, β_1 and β_2, as well as S_1 and S_2, such that S_{ig}, S_{id}, and S_{igid} get the correct value. There is some freedom in choosing the numbers; the values that are used in the verilog-A implementation of PSP are

$$\begin{aligned} \alpha_1 &= T && (6.13)\\ \beta_1 &= m_{\mathrm{igid}} && (6.14)\\ \beta_2 &= 1 && (6.15)\\ S_1 &= \boldsymbol{N}_{\mathbf{T}}/m_{\mathrm{ig}} && (6.16)\\ S_2 &= \boldsymbol{N}_{\mathbf{T}} \cdot (1 - C_{\mathrm{igid}}^2) \cdot m_{\mathrm{id}}, && (6.17) \end{aligned}$$

[2] Although this appears to be a limitation, it is in fact very helpful to ensure that the resulting noise model is consistent with time-domain simulations.

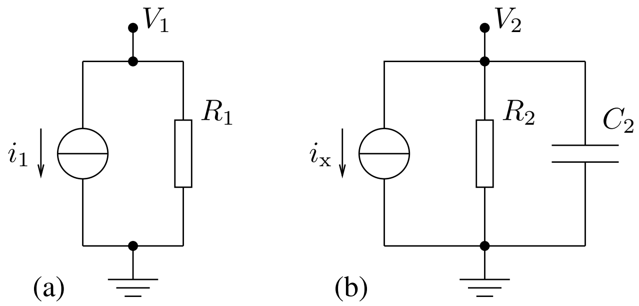

Figure 6.4: The two subcircuits used in PSP's Verilog-A implementation to model the correct frequency dependence of induced gate noise and its correlation with the channel thermal noise.

where

$$C_{\text{igid}} = \frac{m_{\text{igid}}}{\sqrt{m_{\text{ig}} \cdot m_{\text{id}}}}, \tag{6.18}$$

and m_{id}, m_{ig}, and m_{igid} are given by Eqs. (4.231), (4.232), and (4.233), respectively.

To achieve this, we make use of the subcircuits depicted in Fig. 6.4. The first subcircuit (a) contains a parallel connection of a white noise source with current small-signal noise current i_1 and a resistor R_1. The voltage over the elements is denoted by V_1. The second subcircuit (b) contains a voltage-controlled current source with current i_{x}, a resistor R_2, and a capacitor C_2. The nodal voltage is denoted by V_2.

The parameters of these components are given by

$$S_1 = \langle i_1 \cdot i_1^* \rangle = S_{\text{ig}}^0 \cdot s_{\text{f}}^2 \tag{6.19}$$
$$R_1 = 1\,\Omega \tag{6.20}$$
$$i_{\text{x}} = -V_1/s_{\text{f}} \tag{6.21}$$
$$R_2 = m_{\text{ig}} \tag{6.22}$$
$$C_2 = C_{\text{Geff}} \tag{6.23}$$

where the values of C_{Geff} is given by Eqs. (4.220) and

$$S_{\text{ig}}^0 = \frac{\boldsymbol{N_{\text{T}}}}{m_{\text{ig}}}. \tag{6.24}$$

Moreover, we introduce a scaling factor $s_{\text{f}} = \omega_0 \cdot m_{\text{ig}} \cdot C_{\text{Geff}}$ with $\omega_0 = 1$ MHz. Note that the value of s_{f} and ω_0 do not affect the final result, but help to give the noise power of V_1 a reasonable value.

Choosing the elements in this way, creates a frequency dependent current i_C through the capacitor C_2 given by

$$i_C = T \cdot i_{\text{x}}. \tag{6.25}$$

The two noise sources connected to the gate in Fig. 6.3 are now realized as two current-controlled current sources with

$$i_{\text{gd}} = i_{\text{gs}} = \frac{1}{2} \cdot i_C. \tag{6.26}$$

The third source in Fig. 6.3 (between source and drain) is realized by putting two elements in parallel:

- A voltage controlled current source with value $(m_{\text{igid}}/s_{\text{f}}) \cdot V_1$ and
- A white noise source with current power spectral density $S_2 = \boldsymbol{N_{\text{T}}} \cdot (1 - C_{\text{igid}}^2) \cdot m_{\text{id}}$.

To complete the model, we remark that from Fig. 6.3 it is clear that source-drain interchange only affects the sign of i_{ds}.

In summary, the relevant portion of the verilog-A implementation is given by (mult-scaling and labels are not included for clarity):

```
electrical NOI;
electrical NOI2;

branch (NOI) NOII;
branch (NOI) NOIR;
branch (NOI) NOIC;

// subcircuit (a)
I(NOI2)   <+  V(NOI2);
I(NOI2)   <+  white_noise(sqig * sqig * sf * sf);

// subcircuit (b)
I(NOII)   <+  -V(NOI2) / sf;
I(NOIR)   <+  V(NOIR) / mig;
I(NOIC)   <+  ddt(CGeff * V(NOIC));

// noise sources ids, igs, and igd
I(DI,SI)  <+  white_noise(sqid * sqid * (1.0 - c_igid * c_igid));
I(DI,SI)  <+  sigVds * migid * V(NOI2) / sf;
I(GP,SI)  <+  ddt(0.5 * CGeff * V(NOIC));
I(GP,DI)  <+  ddt(0.5 * CGeff * V(NOIC));
```

It is straightforward to verify that this implementation of PSP's noise model in Verilog-A naturally yields the desired correlations and frequency dependence. However, it requires two additional internal nodes.

SiMKit C-code

Contrary to the limitation of Verilog-A language, most circuit simulators are able to directly deal with correlated and frequency dependent noise—without the use of additional internal nodes. In order to minimize the simulation time of the model, C-implementations should therefore avoid the use of such internal nodes whenever possible.

In SiMKit, the frequency dependence and correlation of the noise sources indicated in Fig. 6.3 are implemented directly according to Eq. (6.3). The result is therefore equivalent to the verilog-A implementation.

In summary, even though the SiMKit-implementation of the noise model in PSP is different from that in verilog-A (as it does not make use of additional internal nodes) the result of noise noise simulations will be identical.

6.5.4 Clip warnings

From SiMKit 3.7 onwards, it is possible to set the level of clip-warning information through the value of the parameter **PARAMCHK**. This functionality is available for most SiMKit models. It is *not* available in the verilog-A version of PSP.

If the value of **PARAMCHK** is

- < 0 All clip warnings are suppressed.
- ≥ 0 (default) Clip warnings for instance parameters.
- ≥ 1 Clip warnings for model parameters.
- ≥ 2 Clip warnings for internally computed local parameters during model initialization.
- ≥ 3 Clip warnings for internally computed local parameters during model evaluation.

This works in an accumulative manner: if a higher value of **PARAMCHK** is used, the warnings associated with lower levels are still included. Note that the highest level is of interest only for self heating models, where electrical parameters may change dependent on temperature. Hence, it is currently not applicable to PSP. Also note that the default value (0) results in less clip warnings than in earlier versions of the model.

Section 7

Parameter extraction

The parameter extraction strategy for PSP consists of four main steps:

1. Measurements
2. Extraction of local parameters at room temperature
3. Extraction of temperature scaling parameters
4. Extraction of geometry scaling (global) parameters

The above steps will be briefly described in the following sections. Note that the description of the extraction procedure is not ‘complete’ in the sense that only the most important parameters are discussed and in cases at hand it may be advantageous (or even necessary) to use an adapted procedure.

Throughout this section, bias and current conditions are given for an n-channel transistor only; for a p-channel transistor, all voltages and currents should be multiplied by -1.

As explained in the introduction, the hierarchical setup of PSP (local and global level) allows for the two-step parameter extraction procedure described in this section; this is the recommended method of operation. Nevertheless, it is possible to skip the first steps and start extracting global parameters directly. This procedure is not described here, but the directions below may still be useful.

7.1 Measurements

The parameter extraction routine consists of six different DC-measurements (two of which are optional) and two capacitance measurements.[1] Measurement V and VI are only used for extraction of gate-current, avalanche, and GIDL/GISL parameters.

- **Measurement I** (“idvg”): $I_{\rm D}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 25$ or 50 mV
  $V_{\rm BS} = 0 \ldots -V_{\rm sup}$ (3 or more values)

- **Measurement II** (“idvgh”): $I_{\rm D}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = V_{\rm sup}$
  $V_{\rm BS} = 0 \ldots -V_{\rm sup}$ (3 or more values)

[1] The bias conditions to be used for the measurements are dependent on the supply voltage of the process. Of course it is advisable to restrict the range of voltages to this supply voltage $V_{\rm sup}$. Otherwise physical effects atypical for normal transistor operation—and therefore less well described by PSP—may dominate the characteristics.

- **Measurement III** ("idvd"): I_D vs. V_DS
  $V_\mathrm{GS} = 0 \ldots V_\mathrm{sup}$ (3 or more values)
  $V_\mathrm{DS} = 0 \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{BS} = 0$ V

- **Measurement IV** ("idvdh", optional):I_D vs. V_DS
  $V_\mathrm{GS} = 0 \ldots V_\mathrm{sup}$ (3 or more values)
  $V_\mathrm{DS} = 0 \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{BS} = -V_\mathrm{sup}$

- **Measurement V** ("igvg"): I_G and I_B vs. V_GS
  $V_\mathrm{GS} = -V_\mathrm{sup} \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{DS} = 0 \ldots V_\mathrm{sup}$ (3 or more values)
  $V_\mathrm{BS} = 0$ V

- **Measurement VI** ("igvgh", optional): I_G and I_B vs. V_GS
  $V_\mathrm{GS} = -V_\mathrm{sup} \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{DS} = 0 \ldots V_\mathrm{sup}$ (3 or more values)
  $V_\mathrm{BS} = -V_\mathrm{sup}$

- **Measurement VII** ("cggvg"): C_GG vs. V_GS
  $V_\mathrm{GS} = -V_\mathrm{sup} \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{DS} = 0$ V
  $V_\mathrm{BS} = 0$ V

- **Measurement VIII** ("ccgvg"): C_CG vs. V_GS
  $V_\mathrm{GS} = -V_\mathrm{sup} \ldots V_\mathrm{sup}$ (with steps of maximum 50 mV).
  $V_\mathrm{DS} = 0$ V
  $V_\mathrm{BS} = 0$ V

For the extraction procedure, the transconductance g_m (for Measurement I and II) and the output conductance g_DS (for Measurement III and IV) are obtained by numerical differentiation of the measured I-V-curves. Furthermore, I_min is the smallest current which can reliably measured by the system (noise limit) and I_T is defined as 10% of the largest measured value of $|I_\mathrm{D}|$ in Measurement I. The latter will be used to make a rough distinction between the subthreshold and superthreshold region.

The channel-to-gate capacitance C_CG in Measurement VIII is the summation of the drain-to-gate capacitance C_DG and the source-to-gate capacitance C_SG (i.e., source and drain are short-circuited); it is needed to extract overlap capacitance parameters.

The local parameter extraction measurements I through VI have to be performed at room temperature for every device. In addition, capacitance measurements VII and VIII need to be performed for at least a long/wide and a short/wide (i.e., $L = L_\mathrm{min}$) transistor (at room temperature). Furthermore, for the extraction of temperature scaling parameters measurements I, III, and V have to be performed at different temperatures (at least two extra, typically $-40\,^\circ$C and $125\,^\circ$C) for at least a long wide and a short wide transistor.

7.2 Extraction of local parameters at room temperature

General remarks

The simultaneous determination of *all* local parameters for a specific device is not advisable, because the value of some parameters can be wrong due to correlation and suboptimization. Therefore it is more practical to split the parameters into several small groups, where each parameter group can be determined using specific measurements. In this section, such a procedure will be outlined.

The extraction of local parameters is performed for every device. In order to ensure that the temperature scaling relations do not affect the behavior at room temperature, the reference temperature **TR** should be set equal to room temperature.

Before starting the parameter extraction procedure, one should make sure that **SWIGATE**, **SWIMPACT**, **SWGIDL**, **SWJUNCAP**, and **TYPE** are set to the desired value. Moreover, **QMC** should be set to 1, in order to include quantum mechanical corrections in the simulations.

It is not the case that all local parameters are extracted for every device. Several parameters are only extracted for one or a few devices, while they are kept fixed for all other devices. Moreover, a number of parameters can generally be kept fixed at their default values and need only occasionally be used for fine-tuning in the optimization procedure. Details are given later in this section.

As a special case, it is generally not necessary to extract values for **AX**. In stead, they can be calculated from Eq. (3.57), using **AXO** ~ 18 and **AXL** ~ 0.25. It may be necessary to tune the latter value such that the value of **AX** is between 2 and 3 for the shortest channel in the technology under study.

It is recommended to start the extraction procedure with the long(est) wide(st) device, then the shortest device with the same width, followed by all remaining devices of the same width in order of decreasing length. Then the next widest-channel devices are extracted, where the various lengths are handled in the same order. In this way, one works ones way down to the narrowest channel devices.

AC-parameters

Some parameters (such as **TOX** and **NP**) that do affect the DC-behavior of a MOSFET can only be extracted accurately from C-V-measurements.[2] This should be done before the actual parameter extraction from DC-measurements is started. In Tables 7.1 and 7.2 the extraction procedure for the AC-parameters is given.

Table 7.1: AC-parameter extraction procedure for a long channel MOSFET.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**VFB**,**NEFF**, **DPHIB**, **NP**, **COX**	VII: C_{GG}	Relative	–
2	Repeat Step 1			

Table 7.2: AC-parameter extraction procedure for a short channel MOSFET. The values of **VFB** and **NP** are taken from the long-channel case.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **DPHIB**, **COX**	VII: C_{GG}	Relative	–
2	**CGOV**, **NOV**	VIII: C_{CG}	Relative	$V_{\text{GS}} < 0$
3	Repeat Steps 1 and 2			

Starting from the default parameter set and setting **TOX** to a reasonable value (as known from technology), **VFB**, **NEFF**, **DPHIB**, **COX**, and **NP** can be extracted from C_{GG} in Measurement VII for a long, wide device.

Next, **NOV** and **CGOV** can be extracted from C_{CG} in Measurement VIII for a short, wide device (see also Table 7.1), where **VFB** and **NP** are taken from the long channel case. In general, one can assume **TOXOV** $=$ **TOX**.

The value of **TOX** can be determined from **COX** $= \epsilon_{\text{ox}} \cdot L \cdot W/$**TOX**. If the device is sufficiently long and wide, drawn length and width can be used in this formula. Even better, if Measurement VII is available for a

[2]Although parameter **NOV** *can* be determined from overlap gate current, it is nonetheless more accurately determined from Measurement VIII.

Table 7.3: Initial values for local parameter extraction for a *long*-channel device. For parameters which are not listed in this table, the default value (as given in Section 2.5.7) can be used as initial value.

Parameter	Initial value
BETN	$0.03 \cdot W/L$
RS	0
THESAT	0.1
AX	12
A1	0

few short/wide devices of different lengths, one can extract **TOX** and ΔL from a series of extracted values of **COX** vs. L_{draw}.

Some remarks:

- If C-V-measurements are not available, one could revert to values known from the fabrication process. Note that **TOX** and **TOXOV** are *physical* oxide thicknesses; poly-depletion and quantum-mechanical effects are taken care of by the model. If the gate dielectric is not pure SiO_2, one should manually compensate for the deviating dielectric constant.
- In general, **VFB** and **NP** can be assumed independent of channel length and width (so, the long/wide-channel values can be used for all other devices as well). Only if no satisfactory fits are obtained, one could allow for a length dependence (for **NP**) or length *and* width dependence (for **VFB**). Then, one should proceed by extracting **VFB** and/or **NP** from capacitance measurements for various channel geometries, fit Eq. (3.12) / Eq. (3.27) to the result and use interpolated values in the DC parameter extraction procedure.
- The value of parameter **TOX** profoundly influences both the DC- and AC-behavior of the PSP-model and thus the values of many other parameters. It is therefore very important that this parameter is determined (as described above) and *fixed* before the rest of the extraction procedure is started.

If desired (e.g., for RF-characterization), parameters for several parasitic capacitances (gate-bulk overlap, fringe capacitance, etc.) can be extracted as well (**CGBOV** and **CFR**). However, this requires additional capacitance measurements.

The obtained values of **VFB**, **TOX**, **TOXOV**, **NP**, and **NOV** can now be used in the DC-parameter extraction procedure. The above values of **NEFF** and **DPHIB** can be disregarded; they will be determined more accurately from the DC-measurements.

DC-parameters

Before the optimization is started a reasonably good starting value has to be determined, both for the parameters to be extracted and for the parameters which remain constant. For most parameters to be extracted for a *long* channel device, the default values from Section 2.5.7 can be taken as initial values. Exceptions are given in Table 7.3. Starting from these values, the optimization procedure following the scheme below is performed. This method yields a proper set of parameters after the repetition indicated as the final step in the scheme. Experiments with transistors of several processes show that repeating those steps more than once is generally not necessary.

For an accurate extraction of parameter values, the parameter set for a long-channel transistor has to be determined first. In the long-channel case most of the mobility related parameters (i.e. **MUE** and **THEMU**) and the gate tunneling parameters (**GCO**, **GC2**, and **GC3**) are determined and subsequently fixed for the shorter-channel devices.

Table 7.4: DC-parameter extraction procedure for a long-channel MOSFET. The parameters **VFB**, **TOX**, **TOXOV**, **NP**, and **NOV** must be taken from C-V-measurements. The optimization is either performed on the absolute or relative deviation between model and measurements, as shown in the table.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **BETN**, **MUE**, **THEMU**[a]	I: I_{D}	Absolute	–
2	**NEFF**, **DPHIB**, **CT**	I: I_{D}	Relative	$I_{\mathrm{min}} < I_{\mathrm{D}} < I_{\mathrm{T}}$
3	**MUE**, **THEMU**[a], **CS**, **XCOR**, **BETN**	I: I_{D}, g_{m}	Absolute	–
4	**THESAT**	III: I_{D}	Absolute	–
5	**ALP**, **ALP1**, **ALP2**, **VP**[a], (**AX**)	III: g_{DS}	Relative	–
6	**THESAT**	II: I_{D}	Absolute	–
7	**IGINV**, **GC2**[a], **GC3**[a]	V: I_{G}	Relative	$I_{\mathrm{G}} > I_{\mathrm{min}}$
8	**IGOV**, (**GCO**[a])	V: I_{G}	Relative	$V_{\mathrm{GS}} < 0$ V, $I_{\mathrm{G}} < -I_{\mathrm{min}}$
9	**A1**, **A2**[a], **A3**	V: I_{B}	Relative	$V_{\mathrm{GS}} > 0$ V, $I_{\mathrm{B}} < -I_{\mathrm{min}}$
10	**A4**	VI: I_{B}	Relative	$V_{\mathrm{GS}} > 0$ V, $I_{\mathrm{B}} < -I_{\mathrm{min}}$
11	**AGIDL**, **BGIDL**[a]	V: I_{B}	Relative	$V_{\mathrm{GS}} < 0$ V, $I_{\mathrm{B}} < -I_{\mathrm{min}}$
12	**CGIDL**[a]	VI: I_{B}	Relative	$V_{\mathrm{GS}} < 0$ V, $I_{\mathrm{B}} < -I_{\mathrm{min}}$
13	Repeat Steps 2 – 12			

[a]Only extracted for the *widest* long channel device and fixed for all other geometries.

In Table 7.4 the complete DC extraction procedure for long-channel transistors is given. The magnitude of the simulated I_{D} and the overall shape of the simulated I_{D}-V_{GS}-curve is roughly set in Step 1. Next the parameters **NEFF**, **DPHIB**, and **CT**—which are important for the subthreshold behavior—are optimized in Step 2, neglecting short-channel effects such as drain-induced barrier-lowering (DIBL). After that, the mobility parameters are optimized in Step 3, neglecting the influence of series-resistance. In Step 4 a preliminary value of the velocity saturation parameter is obtained, and subsequently the conductance parameters **ALP**, **ALP1**, **ALP2**, and **VP** are determined in Step 5. A more accurate value of **THESAT** can now be obtained using Step 6. The gate current parameters are determined in Steps 7 and 8, where it should be noted that **GCO** should only be extracted if the influence of gate-to-bulk tunneling is visible in the measurements. This is usually the case if $V_{\mathrm{sup}} \gtrsim |\mathbf{VFB}|$. This is followed by the weak-avalanche parameters in Step 9 and (optionally) 10, and finally, the gate-induced leakage current parameters are optimized in Step 11 and (optionally) 12.

After completion of the extraction for the long-channel device, it is recommended to first extract parameters for the shortest-channel device (of the same width). The mobility-reduction parameters (**MUE**, **THEMU**) and the gate tunneling probability factors (**GCO**, **GC2**, **GC3**) found from the corresponding long-channel device should be used. The extraction procedure as given in Table 7.5 should be used.

Once the value for **RS** has been found from the shortest device, it should be copied into the long-channel parameter set and steps 2–3 (Table 7.4) should be repeated, possibly leading to some readjustment of **MUE** and **THEMU**. If necessary, this procedure must be repeated. Similarly—once the value of **THESATG** and **THESATB** have been determined from the shortest widest channel device—steps 4, 5, and 6 of the long-channel extraction procedure (Table 7.4) must be repeated to obtain updated values for **THESAT**, **ALP**, **ALP1**, and **ALP2**.

If consistent parametersets have been found for the longest and shortest channel device, the extraction procedure as given in Table 7.5 can be executed for all intermediate channel lengths. The extracted parameter values of the next-longer device can be used as initial values.

Table 7.5: DC-parameter extraction procedure for a short-channel MOSFET. Parameters **MUE**, **THEMU**, **VP**, **GCO**, **GC2**, **GC3**, **A2**, **A4**, **BGIDL**, and **CGIDL** are taken from the corresponding long-channel case. The optimization is either performed on the absolute or relative deviation between model and measurements, as indicated in the table.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **DPHIB**, **BETN**, **RS**[a]	I: $I_{\rm D}$	Absolute	–
2	**NEFF**, **DPHIB**, **CT**	I: $I_{\rm D}$	Relative	$I_{\rm min} < I_{\rm D} < I_{\rm T}$
3	**BETN**, **RS**[a], **XCOR**	I: $I_{\rm D}$, $g_{\rm m}$	Absolute	–
4	**THESAT**	III: $I_{\rm D}$	Absolute	–
5	**ALP**, **ALP1**, **ALP2**, **CF**, (**AX**)	III: $g_{\rm DS}$	Relative	–
6	**CFB**[b]	IV: $g_{\rm DS}$	Relative	–
7	**THESAT**, **THESATG**[b], **THESATB**[b]	II: $I_{\rm D}$, $g_{\rm m}$	Absolute	–
8	**IGINV**, **IGOV**	V: $I_{\rm G}$	Relative	$\lvert I_{\rm G}\rvert > I_{\rm min}$
9	**A1**, **A3**	V: $I_{\rm B}$	Relative	$V_{\rm GS} > 0$ V, $I_{\rm B} < -I_{\rm min}$
10	**AGIDL**	V: $I_{\rm B}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm B} < -I_{\rm min}$
11	Repeat Steps 2 – 10			

[a]Only extracted for the *shortest* channel of each width and fixed for all other geometries.
[b]Only extracted for the *shortest widest* device and fixed for all other geometries.

Table 7.6: Temperature scaling parameter extraction procedure for a long wide channel MOSFET. This scheme only makes sense if measurements have been performed at one or (preferably) more temperatures which differ from room temperature.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**STVFB**[a]	I: $I_{\rm D}$	Relative	$I_{\rm D} < I_{\rm T}$
2	**STBETN**[a], **STMUE**, **STTHEMU**, **STCS**, **STXCOR**	I: $I_{\rm D}$	Absolute	–
3	**STTHESAT**[a]	II: $I_{\rm D}$	Absolute	–
4	**STIG**	V: $I_{\rm G}$	Relative	$\lvert I_{\rm G}\rvert > I_{\rm min}$
5	**STA2**	V: $I_{\rm B}$	Relative	$V_{\rm GS} > 0$ V, $I_{\rm B} < -I_{\rm min}$
6	**STBGIDL**	V: $I_{\rm B}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm B} < -I_{\rm min}$

[a]Also extracted for one or more long *narrow* devices.

7.3 Extraction of Temperature Scaling Parameters

For a specific device, the temperature scaling parameters can be extracted after determination of the local parameters at room temperature. In order to do so, measurements I, II and IV need to be performed at various temperature values (at least two values different from room temperature, typically $-40\,^{\circ}$C and $125\,^{\circ}$C), at least for a long wide device and a short wide device. If the reference temperature **TR** has been chosen equal to room temperature (as recommended in Section 7.2), the modeled behavior at room temperature is insensitive to the value of the temperature scaling parameters. As a first-order estimate of the temperature scaling parameter values, the default values as given in Section 2.5.7 can be used. Again the parameter extraction scheme is slightly different for the long-channel and for the short-channel case.

For an accurate extraction, the temperature scaling parameters for a long-wide-channel device have to be de-

Table 7.7: Temperature scaling parameter extraction procedure for short-channel MOSFETs (both wide and narrow). This scheme only makes sense if measurements have been performed at one or (preferably) more temperatures which differ from room temperature.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**STVFB**	I: I_{D}	Relative	$V_{\mathrm{GS}} < V_{\mathrm{T}}$
2	**STBETN**, **STRS**[a]	I: I_{D}	Absolute	$V_{\mathrm{GS}} > V_{\mathrm{T}}$
3	**STTHESAT**	II: I_{D}	Absolute	–

[a]Only extracted for a short *narrow* device and fixed for all other geometries.

termined first. In the long-wide-channel case the carrier mobility parameters can be determined, and they are subsequently fixed for all other devices. In Table 7.6 the appropriate extraction procedure is given. In Step 1 the subthreshold temperature dependence is optimized, followed by the optimization of mobility reduction parameters in Step 2. Next the temperature dependence of velocity saturation is optimized in Step 3. In the subsequent steps, parameters for the temperature dependence of the gate current, the impact ionization current and gate-induced drain leakage are determined. The determined values of the mobility reduction temperature scaling parameters (i.e., **STMUE**, **STTHEMU**, **STCS**, and **STXCOR**) are copied to all other devices and kept fixed during the remainder of the temperature-scaling parameter extraction procedure. Step 1 and 2 could then be performed on one or more long narrow devices as well (for **STVFB**, **STBETN**, and **STTHESAT** only).

Next the extraction procedure as given in Table 7.7 is carried out for several short devices of different widths. Preferably, the extraction is done first for a short narrow device, such that the determined value of **STRS** can be used during the extraction of the wider devices.

7.4 Extraction of Geometry Scaling Parameters

The aim of the complete extraction procedure is the determination of the geometry scaling parameters (global parameters), i.e., a single set of parameters (see Section 2.5.3) which gives a good description of the MOSFET-behavior over the full geometry range of a CMOS technology.

Determination of ΔL and ΔW

An extremely important part of the geometry scaling extraction scheme is an accurate determination of ΔL and ΔW, see Eqs. (3.6) and (3.7).[3] Since it affects the DC-, the AC- as well as the noise model and, moreover, it can heavily influence the quality of the resulting global parameter set, it is very important that this step is carried out with care.

Traditionally, ΔW can be determined from the extrapolated zero-crossing in **BETN** versus mask width W. In a similar way ΔL can be determined from $1/$**BETN** versus mask length L. For modern MOS devices with pocket implants, however, it has been found that the above ΔL extraction method is no longer valid [13, 14]. Another, more accurate method is to measure the gate-to-bulk capacitance C_{GB} in accumulation for different channel lengths [14, 15]. In this case the extrapolated zero-crossing in the C_{GB} versus mask length L curve will give ΔL. Similarly, the extracted values for **COX** (from the procedure in Table 7.1 and 7.2) vs. mask length L may be used for this purpose. Unfortunately for CMOS technologies in which gate current is non-negligible, capacitance measurements may be hampered by gate current [16]. In this case gate current parameter **IGINV** plotted as a function of channel length L may be used to extract ΔL [16]. If possible, ΔL extraction from C-V-measurements is the preferred method.

Finally, **LOV** can be obtained from (a series of) extracted values of **CGOV** from one or more short devices.

[3]Note that ΔL_{PS} and ΔW_{OD} are expected to be known from the fabrication process. So, in fact, only **LAP** and **WOT** are extracted from the electrical measurements.

From local to global

First of all, the global parameters **TYPE**, **QMC**, and the 'switch'-parameters should be set to the appropriate value. Next, parameters for which no geometrical scaling rules exist must be taken directly from the local set (this applies to **TR**, **TOXO**, **VNSUBO**, **NSLPO**, **DNSUBO**, **TOXOVO**, **NOVO**, **CFBO**, **STMUEO**, **THEMUO**, **STTHEMUO**, **STCSO**, **STXCORO**, **FETAO**, **STRSO**, **RSBO**, **RSGO**, **THESATBO**, **THESATGO**, **VPO**, **A2O**, **STA2O**, **GCOO**, **STIGO**, **GC2O**, **GC3O**, **CHIBO**, **BGIDLO**, **STBGIDLO**, **CGIDLO**, and **DTA**). Generally, these parameters have been left at their default values or they have been extracted for one device only and subsequently fixed for all other devices. The parameters **LVARO**, **LVARL**, **LVARW**, **WVARO**, **WVARL**, and **WVARW** should be known from technology.

Once the values of ΔL and ΔW are firmly established (as described above), **LAP** and **WOT** can be set and the actual extraction procedure of the geometry scaling parameters can be started. It consists of several *independent* sub-steps (which can be carried out in random order), one for each geometry dependent local parameter.

To illustrate such a sub-step, the local parameter **CT** is taken as an example. The relevant geometry scaling equation from Section 3.2 is Eq. (3.28), from which it can be seen that **CTO**, **CTL**, **CTLEXP**, and **CTW** are the global parameters which determine the value of **CT** as a function of L and W. First, the extracted **CT** of each device in a length-series of measured (preferably wide) devices are considered as a function of L. In this context **CTO**, **CTL**, and **CTLEXP** are optimized such that the fit of Eq. (3.28) to the extracted **CT**-values is as good as possible, while keeping **CTW** fixed at 0. Then **CTW** is determined by considering the extracted **CT**-values from a length-series of measured narrow devices. Finally, the four global parameters may be fine-tuned by optimizing all four parameters to all extracted **CT**-values simultaneously. The default values given in Section 2.5.3 are good initial values for the optimization procedure.

All other parameters can be extracted in a similar manner. The local parameters **BETN** and **NEFF** have quite complicated scaling rules, particularly due to the non-uniform doping profiles employed in modern CMOS technologies. Therefore, a few additional guidelines are in place.

- The optimization procedure for **BETN** is facilitated if not **BETN**, but $\mathbf{BETN}_{\mathrm{sq}} \stackrel{\mathrm{def}}{=} \mathbf{BETN} \cdot L_{\mathrm{E}}/W_{\mathrm{E}}$ is considered.
- Starting from the default values, first **UO**, **FBET1**, **LP1**, **FBET2**, and **LP2** should be determined from a length-series of wide devices. Then **BETW1**, **BETW2**, and **WBET** should be determined from a width-series of long devices. Finally, **FBET1W** and **LP1W** can be found by considering some short narrow devices.
- Starting from the default values, first extract **FOL1**, **FOL2**, **NSUBO**, **NPCK**, and **LPCK** from a length-series of wide devices. Here, **NSUBO** determines the long-channel value of **NEFF**. Moreover, **NPCK** and **LPCK** determine the increase of **NEFF** for shorter channels (reverse short channel effect), while **FOL1** and **FOL2** are used to describe the decrease of **NEFF** for very short channels (short channel effect).
- Then **NSUBW** and **WSEG** can be determined form a width-series of long devices. Finally, **NPCKW**, **LPCKW** and **WEGP** are determined from a width-series of short devices.
- Especially for **BETN** and **NEFF** it is advisable—after completing the procedure described above—to fine tune the global parameters found by considering all extracted values of **BETN** (or **NEFF**) simultaneously.

Note that in many cases it may not be necessary to use the full flexibility of PSP's parameter scaling, e.g., for many technologies **NP** and **VFB** may be considered as independent of geometry. If such a geometry-independence is anticipated, the corresponding local parameter should be fixed during local parameter extraction. Only if the resulting global parameter set is not satisfactory, the parameter should be allowed to vary during a subsequent optimization round.

Fine tuning

Once the complete set of global parameters is found, the global model should give an accurate description of the measured I-V-curves and capacitance measurements. Either for fine tuning or to facilitate the extraction of global parameters for which the geometry scaling of the corresponding extracted local parameters is not well-behaved, there are two more things that can be done.

- Local parameters for which the fitting of global parameters was completed satisfactorily could be replaced by the values calculated from the geometrical scaling rules and fixed. Then one could redo (parts of) the local parameter extraction procedure for the remaining local parameters, making them less sensitive for cross-correlations.
- Small groups of global parameters may be fitted directly to the measurements of a well-chosen series of devices, using the global model.

7.5 Summary – Geometrical scaling

Summarizing, for the determination of a full parameter set, the following procedure is recommended.

1. Determine local parameter sets (**VFB**, **NEFF**, . . .) for all measured devices, as explained in Section 7.2 and 7.3.
2. Find ΔL and ΔW.
3. Determine the global parameters by fitting the appropriate geometry scaling rules to the extracted local parameters.
4. Finally, the resulting global can be fine-tuned, by fitting the result of the scaling rules and current equations to the measured currents of all devices simultaneously.

7.6 Extraction of Binning Parameters

In this section, expressions will be given for the parameters in the binning scaling rules, **POYYY**, **PLYYY**, **PWYYY**, and **PLWYYY**, as given in Section 3.3. These coefficients will be expressed in terms of parameter values at the corners of bin (see Fig. 7.1). These expressions can be easily found by substituting the parameter values at the bin corners into the binning scaling rules and inverting the resulting four equations. Note once

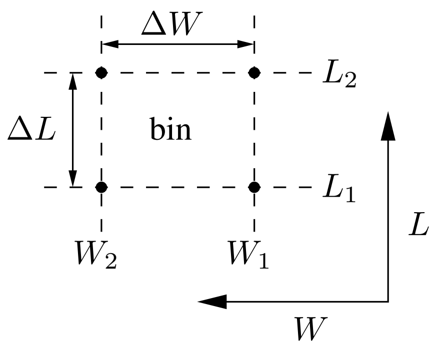

Figure 7.1: Schematic view of a bin, showing the coordinates of the four corners. Note that L_1, L_2, W_1, and W_2 denote the *effective* length and width (L_E and W_E) at the bin corners.

more that this results in a *separate parameter set for each bin*.

In the expression below, the value of parameter **YYY** at bin corner (L_i, W_j) is denoted by Y_{ij} ($i = 1, 2$, $j = 1, 2$). Moreover, $\Delta L = L_2 - L_1$, $\Delta W = W_2 - W_1$, $A = 1/(\Delta L \cdot \Delta W)$.

1. Coefficients for type I scaling

$$\mathbf{POYYY} = A \cdot (L_1 \cdot W_1 \cdot Y_{11} - L_1 \cdot W_2 \cdot Y_{12} - L_2 \cdot W_1 \cdot Y_{21} + L_2 \cdot W_2 \cdot Y_{22}) \tag{7.1}$$

$$\mathbf{PLYYY} = A \cdot \frac{L_1 \cdot L_2}{L_{\mathrm{EN}}} \cdot (-W_1 \cdot Y_{11} + W_2 \cdot Y_{12} + W_1 \cdot Y_{21} - W_2 \cdot Y_{22}) \tag{7.2}$$

$$\mathbf{PWYYY} = A \cdot \frac{W_1 \cdot W_2}{W_{\mathrm{EN}}} \cdot (-L_1 \cdot Y_{11} + L_1 \cdot Y_{12} + L_2 \cdot Y_{21} - L_2 \cdot Y_{22}) \tag{7.3}$$

$$\mathbf{PLWYYY} = A \cdot \frac{L_1 \cdot L_2 \cdot W_1 \cdot W_2}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \cdot (Y_{11} - Y_{12} - Y_{21} + Y_{22}) \tag{7.4}$$

2. Coefficients for type II scaling

$$\mathbf{POYYY} = A \cdot (L_2 \cdot W_2 \cdot Y_{11} - L_2 \cdot W_1 \cdot Y_{12} - L_1 \cdot W_2 \cdot Y_{21} + L_1 \cdot W_1 \cdot Y_{22}) \tag{7.5}$$

$$\mathbf{PLYYY} = A \cdot L_{\mathrm{EN}} \cdot (-W_2 \cdot Y_{11} + W_1 \cdot Y_{12} + W_2 \cdot Y_{21} - W_1 \cdot Y_{22}) \tag{7.6}$$

$$\mathbf{PWYYY} = A \cdot W_{\mathrm{EN}} \cdot (-L_2 \cdot Y_{11} + L_2 \cdot Y_{12} + L_1 \cdot Y_{21} - L_1 \cdot Y_{22}) \tag{7.7}$$

$$\mathbf{PLWYYY} = A \cdot L_{\mathrm{EN}} \cdot W_{\mathrm{EN}} \cdot (Y_{11} - Y_{12} - Y_{21} + Y_{22}) \tag{7.8}$$

3. Coefficients for type III scaling

$$\mathbf{POYYY} = A \cdot (-L_1 \cdot W_2 \cdot Y_{11} + L_1 \cdot W_1 \cdot Y_{12} + L_2 \cdot W_2 \cdot Y_{21} - L_2 \cdot W_1 \cdot Y_{22}) \tag{7.9}$$

$$\mathbf{PLYYY} = A \cdot \frac{L_1 \cdot L_2}{L_{\mathrm{EN}}} \cdot (W_2 \cdot Y_{11} - W_1 \cdot Y_{12} - W_2 \cdot Y_{21} + W_1 \cdot Y_{22}) \tag{7.10}$$

$$\mathbf{PWYYY} = A \cdot W_{\mathrm{EN}} \cdot (L_1 \cdot Y_{11} - L_1 \cdot Y_{12} - L_2 \cdot Y_{21} + L_2 \cdot Y_{22}) \tag{7.11}$$

$$\mathbf{PLWYYY} = A \cdot \frac{L_1 \cdot L_2 \cdot W_{\mathrm{EN}}}{L_{\mathrm{EN}}} \cdot (-Y_{11} + Y_{12} + Y_{21} - Y_{22}) \tag{7.12}$$

Note: For L_1, L_2, W_1, and W_2 in the formulas above one must take the *effective* length and width (L_{E} and W_{E}) as defined in Section 3.2.

Section 8

DC Operating Point Output

The DC operating point output facility gives information on the state of a device at its operation point. Beside terminal currents and voltages, the magnitudes of linearized internal elements are given. In some cases meaningful quantities can be derived which are then also given (e.g., $f_{\rm T}$). The objective of the DC operating point facility is twofold:

- Calculate small-signal equivalent circuit element values
- Open a window on the internal bias conditions of the device and its basic capabilities.

All accessible quantities are described in the table below. The symbols in the 'value' column are defined in Section 4. Besides, the following notation is used: $P_{\rm D} = 1 + \boldsymbol{k_p} \cdot G/4$, where $\boldsymbol{k_p}$ is defined in Eq. (4.16).

Important note: For *all* operating point output the signs are such as if the device is an NMOS. Moreover, whenever there is a reference to the 'drain', this is always the terminal which is acting as drain for the actual bias conditions. This is even true for variables such as **vds** (which is therefore always nonnegative) and the junction-related variables. The output variable **sdint** shows whether or not this 'drain' is the same as the terminal which was named 'drain' in the simulator.

No.	Name	Unit	Value	Description
0	**ctype**	–	1 for NMOS, -1 for PMOS	Flag for channel-type
1	**sdint**	–	1 if $V'_{\rm DS} \geq 0, \ -1$ otherwise	Flag for source-drain interchange
			Current components	
2	**ise**	A	$I_{\rm S} - I_{\rm JS}$	Total source current
3	**ige**	A	$I_{\rm G}$	Total gate current
4	**ide**	A	$I_{\rm D} - I_{\rm JD}$	Total drain current
5	**ibe**	A	$I_{\rm B} + I_{\rm JS} + I_{\rm JD}$	Total bulk current
6	**ids**	A	$I_{\rm DS}$	Drain current, excl. avalanche and tunnel currents
7	**idb**	A	$I_{\rm avl} + I_{\rm gidl} - I_{\rm JD}$	Drain-to-bulk current
8	**isb**	A	$I_{\rm gisl} - I_{\rm JS}$	Source-to-bulk current
9	**igs**	A	$I_{\rm GCS} + I_{\rm GSov}$	Gate-source tunneling current
10	**igd**	A	$I_{\rm GCD} + I_{\rm GDov}$	Gate-drain tunneling current
11	**igb**	A	$I_{\rm GB}$	Gate-bulk tunneling current
12	**igcs**	A	$I_{\rm GCS}$	Gate-channel tunneling current (source component)

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No.	Name	Unit	Value	Description
13	**igcd**	A	I_{GCD}	Gate-channel tunneling current (drain component)
14	**iavl**	A	I_{avl}	Substrate current due to weak-avalanche
15	**igisl**	A	I_{gisl}	Gate-induced source leakage current
16	**igidl**	A	I_{gidl}	Gate-induced drain leakage current
			Junction currents	
17	**ijs**	A	I_{JS}	Total source junction current
18	**ijsbot**	A	$I_{\mathrm{JS,bot}}$	Source junction current, bottom component
19	**ijsgat**	A	$I_{\mathrm{JS,gat}}$	Source junction current, gate-edge component
20	**ijssti**	A	$I_{\mathrm{JS,sti}}$	Source junction current, STI-edge component
21	**ijd**	A	I_{JD}	Total drain junction current
22	**ijdbot**	A	$I_{\mathrm{JD,bot}}$	Drain junction current, bottom component
23	**ijdgat**	A	$I_{\mathrm{JD,gat}}$	Drain junction current, gate-edge component
24	**ijdsti**	A	$I_{\mathrm{JD,sti}}$	Drain junction current, STI-edge component
			Voltages	
25	**vds**	V	V_{DS}	Drain-source voltage
26	**vgs**	V	V_{GS}	Gate-source voltage
27	**vsb**	V	V_{SB}	Source-bulk voltage
28	**vto**	V	$\mathbf{VFB} + P_{\mathrm{D}} \cdot (\boldsymbol{\phi}_{\mathbf{B}} + 2 \cdot \boldsymbol{\phi}^*_{\mathbf{T}}) + G \cdot \sqrt{\boldsymbol{\phi}^*_{\mathbf{T}} \cdot (\boldsymbol{\phi}_{\mathbf{B}} + 2 \cdot \boldsymbol{\phi}^*_{\mathbf{T}})}$	Zero-bias threshold voltage
29	**vts**	V	$\mathbf{VFB} + P_{\mathrm{D}} \cdot (V^*_{\mathrm{SB}} + \boldsymbol{\phi}_{\mathbf{B}} + 2 \cdot \boldsymbol{\phi}^*_{\mathbf{T}}) - V^*_{\mathrm{SB}} + G \cdot \sqrt{\boldsymbol{\phi}^*_{\mathbf{T}} \cdot (V^*_{\mathrm{SB}} + \boldsymbol{\phi}_{\mathbf{B}} + 2 \cdot \boldsymbol{\phi}^*_{\mathbf{T}})}$	Threshold voltage including back-bias effects
30	**vth**	V	$\mathbf{vts} - \Delta V_{\mathrm{G}}$	Threshold voltage including back-bias and drain-bias effects
31	**vgt**	V	$\mathbf{vgs} - \mathbf{vth}$	Effective gate drive voltage including drain- and back-bias effects
32	**vdss**	V	V_{dsat}	Drain saturation voltage at actual bias
33	**vsat**	V	$V_{\mathrm{DS}} - V_{\mathrm{dsat}}$	Saturation limit
			(Trans-)conductances	
34	**gm**	A/V	$\partial\mathbf{ide}/\partial V_{\mathrm{GS}}$	Transconductance
35	**gmb**	A/V	$-\partial\mathbf{ide}/\partial V_{\mathrm{SB}}$	Substrate-transconductance
36	**gds**	A/V	$\partial\mathbf{ide}/\partial V_{\mathrm{DS}}$	Output conductance
37	**gjs**	A/V	$-\partial\mathbf{ijs}/\partial V_{\mathrm{SB}}$	Source junction conductance

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No.	Name	Unit	Value	Description
38	**gjd**	A/V	$-(\partial\mathbf{ijd}/\partial V_{\mathrm{DS}} + \partial\mathbf{ijd}/\partial V_{\mathrm{SB}})$	Drain junction conductance
			Capacitances	
39	**cdd**	F	$\partial Q_{\mathrm{D}}^{(i)}/\partial V_{\mathrm{DS}}$	Drain capacitance
40	**cdg**	F	$-\partial Q_{\mathrm{D}}^{(i)}/\partial V_{\mathrm{GS}}$	Drain-gate capacitance
41	**cds**	F	$\mathbf{cdd} - \mathbf{cdg} - \mathbf{cdb}$	Drain-source capacitance
42	**cdb**	F	$\partial Q_{\mathrm{D}}^{(i)}/\partial V_{\mathrm{SB}}$	Drain-bulk capacitance
43	**cgd**	F	$-\partial Q_{\mathrm{G}}^{(i)}/\partial V_{\mathrm{DS}}$	Gate-drain capacitance
44	**cgg**	F	$\partial Q_{\mathrm{G}}^{(i)}/\partial V_{\mathrm{GS}}$	Gate capacitance
45	**cgs**	F	$\mathbf{cgg} - \mathbf{cgd} - \mathbf{cgb}$	Gate-source capacitance
46	**cgb**	F	$\partial Q_{\mathrm{G}}^{(i)}/\partial V_{\mathrm{SB}}$	Gate-bulk capacitance
47	**csd**	F	$-\partial Q_{\mathrm{S}}^{(i)}/\partial V_{\mathrm{DS}}$	Source-drain capacitance
48	**csg**	F	$-\partial Q_{\mathrm{S}}^{(i)}/\partial V_{\mathrm{GS}}$	Source-gate capacitance
49	**css**	F	$\mathbf{csg} + \mathbf{csd} + \mathbf{csb}$	Source capacitance
50	**csb**	F	$\partial Q_{\mathrm{S}}^{(i)}/\partial V_{\mathrm{SB}}$	Source-bulk capacitance
51	**cbd**	F	$-\partial Q_{\mathrm{B}}^{(i)}/\partial V_{\mathrm{DS}}$	Bulk-drain capacitance
52	**cbg**	F	$-\partial Q_{\mathrm{B}}^{(i)}/\partial V_{\mathrm{GS}}$	Bulk-gate capacitance
53	**cbs**	F	$\mathbf{cbb} - \mathbf{cbd} - \mathbf{cbg}$	Bulk-source capacitance
54	**cbb**	F	$-\partial Q_{\mathrm{B}}^{(i)}/\partial V_{\mathrm{SB}}$	Bulk capacitance
55	**cgsol**	F	$\partial(Q_{\mathrm{sov}} + Q_{\mathrm{ofs}})/\partial V_{\mathrm{GS}}$	Total gate-source overlap capacitance
56	**cgdol**	F	$\partial(Q_{\mathrm{dov}} + Q_{\mathrm{ofd}})/\partial V_{\mathrm{DS}}$	Total gate-drain overlap capacitance
			Junction capacitances	
57	**cjs**	F	C_{JS}	Total source junction capacitance
58	**cjsbot**	F	$C_{\mathrm{JS,bot}}$	Source junction capacitance, bottom component
59	**cjsgat**	F	$C_{\mathrm{JS,gat}}$	Source junction capacitance, gate-edge component
60	**cjssti**	F	$C_{\mathrm{JS,sti}}$	Source junction capacitance, STI-edge component
61	**cjd**	F	C_{JD}	Total drain junction capacitance
62	**cjdbot**	F	$C_{\mathrm{JD,bot}}$	Drain junction capacitance, bottom component
63	**cjdgat**	F	$C_{\mathrm{JD,gat}}$	Drain junction capacitance, gate-edge component
64	**cjdsti**	F	$C_{\mathrm{JD,sti}}$	Drain junction capacitance, STI-edge component
			Miscellaneous	
65	**weff**	m	W_{E}	Effective channel width for geometrical models
66	**leff**	m	L_{E}	Effective channel length for geometrical models
67	**u**	-	$\mathbf{gm}/\mathbf{gds}$	Transistor gain

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No.	Name	Unit	Value	Description
68	**rout**	Ω	$1/\mathbf{gds}$	Small-signal output resistance
69	**vearly**	V	$\lvert\mathbf{ide}\rvert/\mathbf{gds}$	Equivalent Early voltage
70	**beff**	A/V^2	$2 \cdot \lvert\mathbf{ide}\rvert/\mathbf{vgt}^2$	Gain factor
71	**fug**	Hz	$\mathbf{gm}/[2 \cdot \pi \cdot (\mathbf{cgg} + \mathbf{cgsol} + \mathbf{cgdol})]$	Unity gain frequency at actual bias
72	**rg**	Ω	**RG**	Gate resistance
			Noise	
73	**sfl**	A^2/Hz	$S_{\mathrm{fl}}(1\ \mathrm{Hz})$	Flicker noise current spectral density at 1 Hz
74	**sqrtsff**	V/$\sqrt{\mathrm{Hz}}$	$\sqrt{S_{\mathrm{fl}}(1\ \mathrm{kHz})}/\mathbf{gm}$	Input-referred RMS white noise voltage spectral density at 1 kHz
75	**sqrtsfw**	V/$\sqrt{\mathrm{Hz}}$	$\sqrt{S_{\mathrm{id}}}/\mathbf{gm}$	Input-referred RMS white noise voltage spectral density
76	**sid**	A^2/Hz	S_{id}	Channel thermal noise current spectral density
77	**sig**	A^2/Hz	$S_{\mathrm{ig}}(1\ \mathrm{kHz})$	Induced gate noise current spectral density at 1 kHz
78	**cigid**	–	$\dfrac{m_{\mathrm{igid}}}{\sqrt{m_{\mathrm{ig}} \cdot m_{\mathrm{id}}}}$	Imaginary part of correlation coefficient between S_{ig} and S_{id}
79	**fknee**	Hz	$1\mathrm{Hz} \cdot S_{\mathrm{fl}}(1\mathrm{Hz})/S_{\mathrm{id}}$	Cross-over frequency above which white noise is dominant
80	**sigs**	A^2/Hz	S_{igs}	Gate-source current noise spectral density
81	**sigd**	A^2/Hz	S_{igd}	Gate-drain current noise spectral density
82	**siavl**	A^2/Hz	S_{avl}	Impact ionization current noise spectral density
83	**ssi**	A^2/Hz	$S_{\mathrm{S,I}}$	Total source junction current noise spectral density
84	**sdi**	A^2/Hz	$S_{\mathrm{D,I}}$	Total drain junction current noise spectral density

From PSP 102.4 onwards, the values of local parameters are provided in the operating point output. They are listed in the table below.

No.	Name	Unit	Description
			Process Parameters
0	**lp_vfb**	V	Local parameter **VFB** after T-scaling and clipping
1	**lp_stvfb**	V/K	Local parameter **STVFB** after clipping
2	**lp_tox**	m	Local parameter **TOX** after clipping
3	**lp_epsrox**	–	Local parameter **EPSROX** after clipping
4	**lp_neff**	m^{-3}	Local parameter **NEFF** after clipping
5	**lp_vnsub**	V	Local parameter **VNSUB** after clipping
6	**lp_nslp**	V	Local parameter **NSLP** after clipping
7	**lp_dnsub**	V^{-1}	Local parameter **DNSUB** after clipping
8	**lp_dphib**	V	Local parameter **DPHIB** after clipping
9	**lp_np**	m^{-3}	Local parameter **NP** after clipping
10	**lp_ct**	–	Local parameter **CT** after clipping
11	**lp_toxov**	m	Local parameter **TOXOV** after clipping
12	**lp_toxovd**	m	Local parameter **TOXOVD** after clipping
13	**lp_nov**	m^{-3}	Local parameter **NOV** after clipping
14	**lp_novd**	m^{-3}	Local parameter **NOVD** after clipping
			DIBL Parameters
15	**lp_cf**	–	Local parameter **CF** after clipping
16	**lp_cfb**	V^{-1}	Local parameter **CFB** after clipping
			Mobility Parameters
17	**lp_betn**	$m^2/V/s$	Local parameter **BETN** after T-scaling and clipping
18	**lp_stbet**	–	Local parameter **STBET** after clipping
19	**lp_mue**	m/V	Local parameter **MUE** after T-scaling and clipping
20	**lp_stmue**	–	Local parameter **STMUE** after clipping
21	**lp_themu**	–	Local parameter **THEMU** after T-scaling and clipping
22	**lp_stthemu**	–	Local parameter **STTHEMU** after clipping
23	**lp_cs**	–	Local parameter **CS** after T-scaling and clipping
24	**lp_stcs**	–	Local parameter **STCS** after clipping
25	**lp_xcor**	V^{-1}	Local parameter **XCOR** after T-scaling and clipping
26	**lp_stxcor**	–	Local parameter **STXCOR** after clipping
27	**lp_feta**	–	Local parameter **FETA** after clipping
			Series Resistance Parameters
28	**lp_rs**	Ω	Local parameter **RS** after T-scaling and clipping
29	**lp_strs**	–	Local parameter **STRS** after clipping
30	**lp_rsb**	V^{-1}	Local parameter **RSB** after clipping
31	**lp_rsg**	V^{-1}	Local parameter **RSG** after clipping
			Velocity Saturation Parameters
32	**lp_thesat**	V^{-1}	Local parameter **THESAT** after T-scaling and clipping

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No.	Name	Unit	Description
33	**lp_stthesat**	–	Local parameter **STTHESAT** after clipping
34	**lp_thesatb**	V^{-1}	Local parameter **THESATB** after clipping
35	**lp_thesatg**	V^{-1}	Local parameter **THESATG** after clipping
			Saturation Voltage Parameters
36	**lp_ax**	–	Local parameter **AX** after clipping
			Channel Length Modulation (CLM) Parameters
37	**lp_alp**	–	Local parameter **ALP** after clipping
38	**lp_alp1**	V	Local parameter **ALP1** after clipping
39	**lp_alp2**	V^{-1}	Local parameter **ALP2** after clipping
40	**lp_vp**	V	Local parameter **VP** after clipping
			Impact Ionization (II) Parameters
41	**lp_a1**	–	Local parameter **A1** after clipping
42	**lp_a2**	V	Local parameter **A2** after T-scaling and clipping
43	**lp_sta2**	–	Local parameter **STA2** after clipping
44	**lp_a3**	–	Local parameter **A3** after clipping
45	**lp_a4**	$1/\sqrt{V}$	Local parameter **A4** after clipping
			Gate Current Parameters
46	**lp_gco**	–	Local parameter **GCO** after clipping
47	**lp_iginv**	A	Local parameter **IGINV** after T-scaling and clipping
48	**lp_igov**	A	Local parameter **IGOV** after T-scaling and clipping
49	**lp_igovd**	A	Local parameter **IGOVD** after T-scaling and clipping
50	**lp_stig**	–	Local parameter **STIG** after clipping
51	**lp_gc2**	–	Local parameter **GC2** after clipping
52	**lp_gc3**	–	Local parameter **GC3** after clipping
53	**lp_chib**	V	Local parameter **CHIB** after clipping
			Gate-Induced Drain Leakage Parameters
54	**lp_agidl**	A/V^3	Local parameter **AGIDL** after clipping
55	**lp_agidld**	A/V^3	Local parameter **AGIDLD** after clipping
56	**lp_bgidl**	V	Local parameter **BGIDL** after T-scaling and clipping
57	**lp_bgidld**	V	Local parameter **BGIDLD** after T-scaling and clipping
58	**lp_stbgidl**	V/K	Local parameter **STBGIDL** after clipping
59	**lp_stbgidld**	V/K	Local parameter **STBGIDLD** after clipping
60	**lp_cgidl**	–	Local parameter **CGIDL** after clipping
61	**lp_cgidld**	–	Local parameter **CGIDLD** after clipping
			Charge Model Parameters
62	**lp_cox**	F	Local parameter **COX** after clipping
63	**lp_cgov**	F	Local parameter **CGOV** after clipping
64	**lp_cgovd**	F	Local parameter **CGOVD** after clipping
65	**lp_cgbov**	F	Local parameter **CGBOV** after clipping

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No.	Name	Unit	Description
66	**lp_cfr**	F	Local parameter **CFR** after clipping
67	**lp_cfrd**	F	Local parameter **CFRD** after clipping
			Noise Model Parameters
68	**lp_fnt**	–	Local parameter **FNT** after clipping
69	**lp_fntexc**	–	Local parameter **FNTEXC** after clipping
70	**lp_nfa**	$1/\mathrm{V/m}^4$	Local parameter **NFA** after clipping
71	**lp_nfb**	$1/\mathrm{V/m}^2$	Local parameter **NFB** after clipping
72	**lp_nfc**	V^{-1}	Local parameter **NFC** after clipping
73	**lp_ef**	–	Local parameter **EF** after clipping
			Parasitic Resistance Parameters
74	**lp_rg**	Ω	Local parameter **RG** after clipping
75	**lp_rbulk**	Ω	Local parameter **RBULK** after clipping
76	**lp_rwell**	Ω	Local parameter **RWELL** after clipping
77	**lp_rjuns**	Ω	Local parameter **RJUNS** after clipping
78	**lp_rjund**	Ω	Local parameter **RJUND** after clipping
			Junction Parameters
79	**cjosbot**	F	Bottom component of total zero-bias source junction capacitance at device temperature
80	**cjossti**	F	STI-edge component of total zero-bias source junction capacitance at device temperature
81	**cjosgat**	F	Gate-edge component of total zero-bias source junction capacitance at device temperature
82	**vbisbot**	V	Built-in voltage of source-side bottom junction at device temperature
83	**vbissti**	V	Built-in voltage of source-side STI-edge junction at device temperature
84	**vbisgat**	V	Built-in voltage of source-side gate-edge junction at device temperature
85	**idsatsbot**	A	Total source-side bottom junction saturation current
86	**idsatssti**	A	Total source-side STI-edge junction saturation current
87	**idsatsgat**	A	Total source-side gate-edge junction saturation current
88	**cjosbotd**	F	Bottom component of total zero-bias drain junction capacitance at device temperature
89	**cjosstid**	F	STI-edge component of total zero-bias drain junction capacitance at device temperature
90	**cjosgatd**	F	Gate-edge component of total zero-bias drain junction capacitance at device temperature
91	**vbisbotd**	V	Built-in voltage of drain-side bottom junction at device temperature
92	**vbisstid**	V	Built-in voltage of drain-side STI-edge junction at device temperature
93	**vbisgatd**	V	Built-in voltage of drain-side gate-edge junction at device temperature

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No.	Name	Unit	Description
94	**idsatsbotd**	A	Total drain-side bottom junction saturation current
95	**idsatsstid**	A	Total drain-side STI-edge junction saturation current
96	**idsatsgatd**	A	Total drain-side gate-edge junction saturation current

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Appendix A

Auxiliary Equations

In this Appendix, some auxiliary functions which are used in the model equations are defined.

The MINA-smoothing function:

$$\text{MINA}\left(x,\, y,\, a\right) = \frac{1}{2} \cdot \left[x + y - \sqrt{\left(x-y\right)^2 + a}\right] \tag{A.1}$$

The MAXA-smoothing function:

$$\text{MAXA}\left(x,\, y,\, a\right) = \frac{1}{2} \cdot \left[x + y + \sqrt{\left(x-y\right)^2 + a}\right] \tag{A.2}$$

The functions $\chi(y)$, its derivatives, σ_1, and σ_2, which are used in the explicit approximation of surface potential:

$$\chi(y) = \frac{y^2}{2+y^2} \tag{A.3}$$

$$\chi'(y) = \frac{4y}{(2+y^2)^2} \tag{A.4}$$

$$\chi''(y) = \frac{8-12y^2}{(2+y^2)^3} \tag{A.5}$$

$$\nu = a + c \tag{A.6}$$

$$\mu_1 = \frac{v^2}{\tau} + \frac{c^2}{2} - a \tag{A.7}$$

$$\sigma_1\left(a,\, c,\, \tau,\, \eta\right) = \frac{a \cdot \nu}{\mu_1 + (c^2/3 - a) \cdot c \cdot \nu/\mu_1} + \eta \tag{A.8}$$

$$\mu_2 = \frac{v^2}{\tau} + \frac{c^2}{2} - a \cdot b \tag{A.9}$$

$$\sigma_2\left(a,\, b,\, c,\, \tau,\, \eta\right) = \frac{a \cdot \nu}{\mu_2 + (c^2/3 - a \cdot b) \cdot c \cdot \nu/\mu_2} + \eta \tag{A.10}$$

Appendix B

Layout parameter calculation

In post-layout simulations, various PSP instance parameters should be supplied either manually or by a layout extraction tool. In this appendix, it is shown how these parameters should be calculated.

Note: These equations are *not* part of the PSP model.

B.1 Stress parameters

B.1.1 Layout effects for irregular shapes

For irregular shapes the following effective values for **SA** and **SB** are to be used (see Fig B.1).

$$\frac{1}{\mathbf{SA}_{\text{eff}} + 0.5 \cdot L} = \sum_{i=1}^{n} \frac{\mathbf{SW}_i}{W} \cdot \frac{1}{\mathbf{SA}_i + 0.5 \cdot L} \tag{B.1}$$

$$\frac{1}{\mathbf{SB}_{\text{eff}} + 0.5 \cdot L} = \sum_{i=1}^{n} \frac{\mathbf{SW}_i}{W} \cdot \frac{1}{\mathbf{SB}_i + 0.5 \cdot L} \tag{B.2}$$

B.2 Well proximity effect parameters

The values of the instance parameters **SCA**, **SCB** and **SCC** can be calculated from layout parameters using the equations below.

$$f_{\text{A}}(u) = \frac{\mathbf{SCREF}^2}{u^2} \tag{B.3}$$

$$f_{\text{B}}(u) = \frac{u}{\mathbf{SCREF}} \cdot \exp\left(-10 \cdot \frac{u}{\mathbf{SCREF}}\right) \tag{B.4}$$

$$f_{\text{C}}(u) = \frac{u}{\mathbf{SCREF}} \cdot \exp\left(-20 \cdot \frac{u}{\mathbf{SCREF}}\right) \tag{B.5}$$

$$A_{\text{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\text{SCX}_i+\text{SCY}_i}^{\text{SCX}_i+\text{SCY}_i+W} f_{\text{A}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\text{SCX}_i+\text{SCY}_i}^{\text{SCX}_i+\text{SCY}_i+L} f_{\text{A}}(u)\,\mathrm{d}u \right) \tag{B.6}$$

$$B_{\mathrm{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+W} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+L} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) \tag{B.7}$$

$$C_{\mathrm{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+W} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+L} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) \tag{B.8}$$

$$\mathbf{SCA} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{A}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{A}}(u)\,\mathrm{d}u \right) + A_{\mathrm{corner}} \right] \tag{B.9}$$

$$\mathbf{SCB} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + B_{\mathrm{corner}} \right] \tag{B.10}$$

$$\mathbf{SCC} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + C_{\mathrm{corner}} \right] \tag{B.11}$$

Here, m and n are the number of projections of the well edge along the length and width of the devices, respectively. Moreover, k is the number of corners selected to account for the ‘corner’ effects.

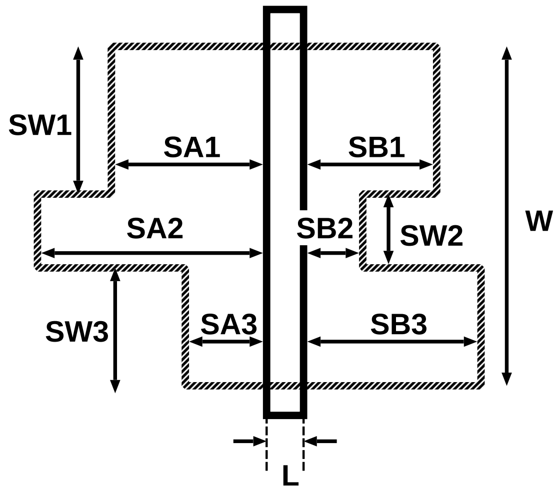

Figure B.1: A typical layout of MOS devices with more instance parameters ($\mathbf{SW}_i$, $\mathbf{SA}_i$ and $\mathbf{SB}_i$) in addition to the traditional L and W.

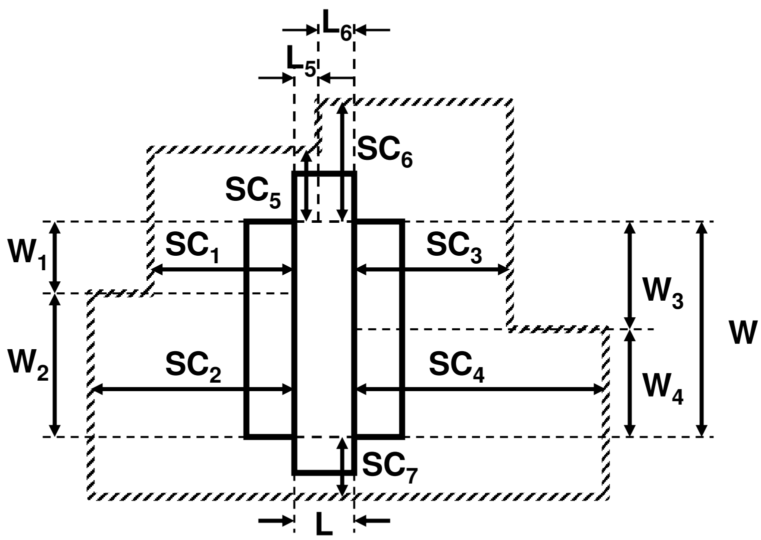

Figure B.2: A typical layout of MOS devices with **WPE** instance parameters

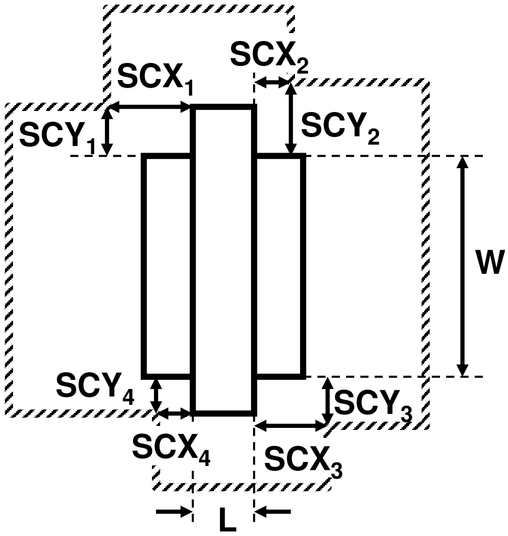

Figure B.3: A layout of MOS devices for corner terms calculation

